Optical Property Studies and Metalorganic Chemical Vapor Deposition
of Ferroelectric Thin Films

by

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(ABSTRACT)

Ferroelectric lead zirconate titanate thin films, Pb(ZrxTi1-x)O3 or PZT, have aroused considerable interest in recent years for the application in nonvolatile electronic memories because of their excellent ferroelectric properties. In this research, PZT thin films were studied from two aspects: the scientific aspect and the technical aspect.

The optical properties of PZT solid solutions and the structure development in PZT films were extensively investigated in the scientific aspect. The PZT films used in this part of study were prepared by metalorganic decomposition (MOD) process. The envelope method, with consideration of light intensity loss from the back surface of the substrate, was demonstrated to be a simple and convenient tool for obtaining the optical properties of the PZT films in the medium and weak absorption regions. In the near optical band gap region, both the transmission and reflection spectra were used to successfully calculate the optical constants of the films. The film thickness derived from the envelope method was cross checked by a computer simulation method and was found to have an accuracy better than 2%. An effective, versatile, and nondestructive optical method was developed for the study of the structure development in MOD PZT films. Also, the models for the structure development
were proposed and were verified by this optical method. Using this method, the
characteristic temperatures (i.e., the initiation and completion temperatures) of each
phase can be easily identified. In addition, the volume fraction of the perovskite
phase in the pyrochlore–perovskite phase transformation region was obtained from
this optical method.

From the technical point of view, ferroelectric PZT films were successfully and
reproducibly deposited for the first time by hot–wall metalorganic chemical vapor
deposition (MOCVD). One of the problems associated with the MOCVD technique
is the availability of the precursors. After intensive studies searching for the most
suitable precursors for MOCVD PZT thin films, the safe and stable precursors,
namely lead tetramethylheptadione [Pb(thd)$_2$], zirconium tetramethylheptadione
[Zr(thd)$_4$], and titanium ethoxide [Ti(OEt)$_4$] were chosen. The films were deposited
at temperatures as low as 550°C and had pure perovskite phase in the as–deposited
state. Also, the films were smooth, specular, crack–free, uniform, and adhered well
on the substrates. The stoichiometry of the films can be easily controlled either by
varying the individual precursor temperature and/or the flow rate of the carrier gas.
Auger electron spectroscopic (AES) depth profile showed good uniformity through
the thickness of the films. The AES spectra also showed no carbon contamination in
the bulk of the films. As–deposited films were dense and showed uniform and fine
grains. The film (Pb/Zr/Ti = 50/41/9) annealed at 600°C showed a spontaneous
polarization of 23.3 μC/cm$^2$ and a coercive field of 64.5 kV/cm.
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Table of Contents

Chapter 1 Introduction ................................................................. 1
  1.1 Ferroelectric Materials ...................................................... 2
  1.2 Properties and Applications of Ferroelectric Materials .......... 3
    1.2.1 Ferroelectric Properties and Applications .................... 3
    1.2.2 Pyroelectric Properties and Applications ..................... 6
    1.2.3 Piezoelectric Properties and Applications ................... 8
    1.2.4 Electro–optic Properties and Applications ................... 9
  1.3 Fabrication Techniques of Ferroelectric Thin Films ............. 10
  1.4 Objectives of Research ................................................... 14

Chapter 2 Experimental Procedure ............................................. 15
  2.1 Preparation of Precursor Solutions ................................. 15
  2.2 PZT Film Preparation ...................................................... 16
  2.3 Optical Transmission and Reflection Measurements .......... 18
  2.4 X–ray Diffraction and Scanning Electron Microscopy .......... 21
  2.5 Composition Determination .............................................. 21
  2.6 Auger Electron Spectroscopy ........................................... 22
  2.7 Ferroelectric Property Measurements ............................... 22

Chapter 3 Optical Properties of PZT Thin Films ......................... 24
  3.1 Introduction ................................................................. 24
  3.2 Theoretical Background .................................................. 25
    3.2.1 Thin Films Optics ................................................ 26
3.2.1.1 Multi-Layer Thin Film System ........................................ 27
3.2.1.2 Single Layer Film on a Transparent Substrate .................... 31
3.2.2 Envelope Method .......................................................... 34
3.2.3 Consideration of the Light Intensity Loss from the Back Surface
of the Substrate ................................................................. 38
3.2.4 Effective Medium Approximation ...................................... 44
3.2.5 Optical Constant at Near Band Gap .................................. 45
3.3 Optical Properties of Sapphire Substrate ................................ 46
3.4 X-ray Diffraction Study ..................................................... 48
3.5 Optical Constants and Film Thickness of PZT Solid Solutions .......... 51
3.6 Absorption Coefficients at Near Band Gap .............................. 70
3.7 Surface Morphology .......................................................... 73
3.8 Summary ............................................................................ 77

Chapter 4 Structure Development Study of PZT Thin Films
by an Optical Method ............................................................... 81
4.1 Introduction ......................................................................... 81
4.2 Models of Structure Development of PZT Thin Films .................. 83
4.3 Structure Development in MOD PZT Thin Films ....................... 88
  4.3.1 X-ray Diffraction Study .................................................. 88
  4.3.2 Optical Method ............................................................. 91
  4.3.3 Pyrochlore–Perovskite Phase Transformation ....................... 102
  4.3.4 Surface Morphology ...................................................... 103
4.4 Summary ............................................................................ 106
Chapter 5 Metalorganic Chemical Vapor Deposition of PZT Thin Films .......... 108

5.1 Introduction .................................................................................. 108
5.2 Selection of Precursors .................................................................. 112
  5.2.1 General Consideration ............................................................ 112
  5.2.2 Properties of Precursors ......................................................... 116
5.3 Experimental Procedure ............................................................... 121
5.4 Results and Discussion of MOCVD PZT Thin Films ...................... 127
  5.4.1 Effect of the Deposition Parameters on the Composition of the Film ................................................................................ 128
  5.4.2 X-ray Diffraction Study ........................................................... 131
  5.4.3 Surface Morphology ............................................................... 135
  5.4.4 Reproducibility ....................................................................... 137
  5.4.5 Optical Properties .................................................................... 141
  5.4.6 Interrelationship of Composition Uniformity and Ferroelectric Properties ............................................................................. 141
5.5 Cold-Wall MOCVD PZT Thin Films ............................................. 149
5.6 Summary ....................................................................................... 153

Chapter 6 Summary ............................................................................ 158

Chapter 7 Suggestions for Future Research ..................................... 162

Appendix A Preparation of PZT Precursor Solutions .......................... 165
Appendix B Supplemental Figures for Chapter 3 ................................. 167
Appendix C Computer Programs ......................................................... 198
List of Figures

Figure 1.1  Unit cell of the perovskite structure
Figure 1.2  Hysteresis loop of a ferroelectric material
Figure 1.3  Phase diagram of PbTiO$_3$ – PbZrO$_3$ solid solution [7]
Figure 1.4  Ferroelectric random access memory (FRAM) cell [9]
Figure 2.1  A flow chart for the preparation of PZT precursor solutions
Figure 2.2  A flow chart for the preparation of PZT films by MOD process
Figure 3.1  A schematic diagram of the transmitted and reflected light in a m-layer thin film system
Figure 3.2  A schematic diagram of a weakly absorbing thin film on a completely transparent semi-infinite substrate
Figure 3.3  A schematic diagram for the calculation of the transmittance and the reflectance of an uncoated substrate
Figure 3.4  Comparison of the experimental and the calculated transmission spectra of sapphire
Figure 3.5  XRD patterns of MOD Pb(Zr$_x$Ti$_{1-x}$)O$_3$ films on sapphire substrates. The samples were annealed at 650°C for 1 hour.
Figure 3.6  Optical transmission spectrum of Pb(Zr$_{0.5}$Ti$_{0.4}$)O$_3$ film on sapphire with that of the uncoated substrate. The envelope curves are shown as the dashed curve.
Figure 3.7  The reflection spectra of Pb(Zr$_{0.6}$Ti$_{0.4}$)O$_3$ film on sapphire in the wavelength range of 300 nm to 2000 nm. The dashed curve is the spectrum with the black paint on the back surface of the substrate.
Figure 3.8  The reflection spectra of Pb(Zr$_{0.6}$Ti$_{0.4}$)O$_3$ film on sapphire in the wavelength range of 300 nm to 500 nm. The dashed curve is the spectrum with the black paint on the back surface of the substrate.
Figure 3.9  The reflectance and the transmittance and their sum of Pb(Zr$_{0.6}$Ti$_{0.4}$)O$_3$ film on sapphire in the wavelength range of 300 nm to 2000 nm. The reflection spectrum was measured without the black paint on the back surface of the substrate.
Figure 3.10  The refractive index as a function of wavelength and the dispersion
Variation of the refractive index at $\lambda = 632.8$ nm with the $x$ value in Pb(Zr$_x$Ti$_{1-x}$)O$_3$ films. Filled circles and the dashed line are values from reference 54.

Adjusted refractive index as a function of wavelength and the dispersion curve of PbTiO$_3$ film

The extinction coefficient as a function of wavelength of Pb(Zr$_{0.6}$Ti$_{0.4}$)O$_3$ film in the wavelength of 300 nm to 2000 nm

The experimental and simulated transmission spectra of Pb(Zr$_{0.6}$Ti$_{0.4}$)O$_3$ film

The absorption coefficients as a function of incident photon energy in the near band gap region for Pb(Zr$_x$Ti$_{1-x}$)O$_3$

The incident photon energy as a function of composition at three different absorption coefficients

SEM micrographs of the surface morphology of MOD Pb(Zr$_x$Ti$_{1-x}$)O$_3$ films. The samples were annealed at 650°C for 1 hour.

Average grain size of the Pb(Zr$_x$Ti$_{1-x}$)O$_3$ films as a function of composition. The samples were annealed at 650°C for 1 hour.

A flow chart for calculation the optical constants and the film thickness of a single layer film on a transparent substrate

Model A: the simplest hypothetical model for the structure development in MOD PZT thin films

Model B: the most complicated hypothetical model for the structure development in MOD PZT thin films

Model C: an example of the hypothetical models between model A and model B for the structure development in MOD PZT thin films

XRD patterns of the MOD Pb(Zr$_{0.5}$Ti$_{0.5}$)O$_3$ film for the annealing temperatures ranging from 460°C to 620°C

Initiation and completion temperature of the perovskite phase as a function of composition in the Pb(Zr$_x$Ti$_{1-x}$)O$_3$ films

Refractive index (at $\lambda = 632.8$ nm) and film thickness as a function of annealing temperature for MOD PbTiO$_3$ film

Refractive index (at $\lambda = 632.8$ nm) and film thickness as a function of annealing temperature for MOD Pb(Zr$_{0.2}$Ti$_{0.8}$)O$_3$ film
Figure 4.8  Refractive index (at $\lambda = 632.8$ nm) and film thickness as a function of annealing temperature for MOD Pb(Zr$_{0.4}$Ti$_{0.6}$)O$_3$ film

Figure 4.9  Refractive index (at $\lambda = 632.8$ nm) and film thickness as a function of annealing temperature for MOD Pb(Zr$_{0.5}$Ti$_{0.5}$)O$_3$ film

Figure 4.10  Refractive index (at $\lambda = 632.8$ nm) and film thickness as a function of annealing temperature for MOD Pb(Zr$_{0.6}$Ti$_{0.4}$)O$_3$ film

Figure 4.11  Refractive index (at $\lambda = 632.8$ nm) and film thickness as a function of annealing temperature for MOD Pb(Zr$_{0.8}$Ti$_{0.2}$)O$_3$ film

Figure 4.12  Refractive index (at $\lambda = 632.8$ nm) and film thickness as a function of annealing temperature for MOD PbZrO$_3$ film

Figure 4.13  The volume fraction of the perovskite phase as a function of annealing temperature in MOD Pb(Zr$_x$Ti$_{1-x}$)O$_3$ films, which was derived from the refractive index by using the effective medium approximation

Figure 4.14  SEM micrographs of the surface morphology of MOD Pb(Zr$_x$Ti$_{1-x}$)O$_3$ films which had suffered through 23 heat treatments in the temperature range from 150°C to 700°C for 30 min at each annealing temperature

Figure 4.15  Average grain size of the Pb(Zr$_x$Ti$_{1-x}$)O$_3$ films as a function of composition. The samples had suffered through 23 heat treatments in the temperature range from 150°C to 700°C for 30 min at each annealing temperature

Figure 5.1  Schematic diagram of MOCVD apparatus for PZT films

Figure 5.2  Temperature Profile of the deposition zone of MOCVD apparatus

Figure 5.3  Variation of (Zr,Ti) composition with the bubbler temperature of Zr and Ti precursors

Figure 5.4  Sample—to—sample composition uniformity

Figure 5.5  XRD patterns of as—deposited PZT films on sapphire substrates

Figure 5.6  XRD patterns of as—deposited PZT films on Pt/Ti/SiO$_2$/Si substrates

Figure 5.7  XRD patterns of as—deposited PZT films on RuO$_x$/SiO$_2$/Si substrates

Figure 5.8  SEM micrographs of MOCVD Pb(Zr$_x$Ti$_{1-x}$)O$_3$ films: (a) as—deposited film on sapphire substrate with $x = 0.4$, (b) as—deposited film on Pt/Ti/SiO$_2$/Si substrate with $x = 0.6$, (c) as—deposited film on RuO$_x$/SiO$_2$/Si substrate with $x = 0.8$, and (d) 650°C/30 min annealed film on RuO$_x$/SiO$_2$/Si substrate with $x = 0.8$.

Figure 5.9  SEM micrograph of highly [100] oriented MOCVD PZT film on
Reproducibility of composition and deposition rate for four consecutive runs with the same deposition condition. The films were on sapphire substrates.

Reproducibility of surface morphology for four consecutive runs with the same deposition condition. The films were on RuO$_x$/SiO$_2$/Si substrate.

Optical transmission spectrum of as-deposited MOCVD Pb(Zr$_{0.6}$Ti$_{0.4}$)O$_3$ film on sapphire substrate. Dashed line shows the transmittance of the uncoated sapphire substrate.

Variation of optical constants with wavelength for as-deposited MOCVD Pb(Zr$_{0.6}$Ti$_{0.4}$)O$_3$ film

AES study of MOCVD PZT film with the composition of Pb/Zr/Ti = 50/41/9: (a) depth profile, (b) AES spectrum on the sample surface, and (c) AES spectrum after 3 min Ar sputtering

AES study of MOCVD PZT film with the composition of Pb/Zr/Ti = 52/26/22: (a) depth profile, (b) AES spectrum on the sample surface, and (c) AES spectrum after 3 min Ar sputtering

D–E hysteresis loop of 600°C/30 min annealed MOCVD PZT film whose composition profile is shown in Figure 5.14

D–E hysteresis loop of 600°C/30 min annealed MOCVD PZT film whose composition profile is shown in Figure 5.15

Schematic diagram of hot–wall MOCVD apparatus with bypass line

AES depth profiles of MOCVD PZT films on Ru$_x$/SiO$_2$/Si: (a) without bypass line and (b) with bypass line

Schematic diagram of cold–wall MOCVD apparatus with bypass line

XRD patterns of MOCVD PZT films deposited by cold–wall reactor at 600°C: (a) on RuO$_x$/SiO$_2$/Si, (b) on Pt/Ti/SiO$_2$/Si, and (c) on sapphire

SEM micrographs of cold–wall MOCVD PZT film on Pt/Ti/SiO$_2$/Si

The reflectance and the transmittance and their sum of PbTiO$_3$ film on sapphire in the wavelength range of 300 nm to 2000 nm. The reflection spectrum was measured without the black paint on the back surface of the substrate.

The reflectance and the transmittance and their sum of Pb(Zr$_{0.2}$Ti$_{0.8}$)O$_3$ film on sapphire in the wavelength range of 300 nm
to 2000 nm. The reflection spectrum was measured without the black paint on the back surface of the substrate.

Figure B.3 The reflectance and the transmittance and their sum of Pb(Zr_{0.4}Ti_{0.6})O_3 film on sapphire in the wavelength range of 300 nm to 2000 nm. The reflection spectrum was measured without the black paint on the back surface of the substrate.

Figure B.4 The reflectance and the transmittance and their sum of Pb(Zr_{0.5}Ti_{0.5})O_3 film on sapphire in the wavelength range of 300 nm to 2000 nm. The reflection spectrum was measured without the black paint on the back surface of the substrate.

Figure B.5 The reflectance and the transmittance and their sum of Pb(Zr_{0.6}Ti_{0.2})O_3 film on sapphire in the wavelength range of 300 nm to 2000 nm. The reflection spectrum was measured without the black paint on the back surface of the substrate.

Figure B.6 The reflectance and the transmittance and their sum of PbZrO_3 film on sapphire in the wavelength range of 300 nm to 2000 nm. The reflection spectrum was measured without the black paint on the back surface of the substrate.

Figure B.7 The refractive index as a function of wavelength and the dispersion curve of PbTiO_3 film

Figure B.8 The refractive index as a function of wavelength and the dispersion curve of Pb(Zr_{0.2}Ti_{0.8})O_3 film

Figure B.9 The refractive index as a function of wavelength and the dispersion curve of Pb(Zr_{0.4}Ti_{0.6})O_3 film

Figure B.10 The refractive index as a function of wavelength and the dispersion curve of Pb(Zr_{0.6}Ti_{0.4})O_3 film

Figure B.11 The refractive index as a function of wavelength and the dispersion curve of Pb(Zr_{0.8}Ti_{0.2})O_3 film

Figure B.12 The refractive index as a function of wavelength and the dispersion curve of PbZrO_3 film

Figure B.13 Adjusted refractive index as a function of wavelength and the dispersion curve of Pb(Zr_{0.2}Ti_{0.8})O_3 film

Figure B.14 Adjusted refractive index as a function of wavelength and the dispersion curve of Pb(Zr_{0.4}Ti_{0.6})O_3 film

Figure B.15 Adjusted refractive index as a function of wavelength and the dispersion curve of Pb(Zr_{0.6}Ti_{0.4})O_3 film

Figure B.16 Adjusted refractive index as a function of wavelength and the
dispersion curve of Pb(Zr$_{0.6}$Ti$_{0.4}$)O$_3$ film

Figure B.17  Adjusted refractive index as a function of wavelength and the dispersion curve of Pb(Zr$_{0.8}$Ti$_{0.2}$)O$_3$ film

Figure B.18  Adjusted refractive index as a function of wavelength and the dispersion curve of PbZrO$_3$ film

Figure B.19  The extinction coefficient as a function of wavelength of PbTiO$_3$ film

Figure B.20  The extinction coefficient as a function of wavelength of Pb(Zr$_{0.2}$Ti$_{0.8}$)O$_3$ film

Figure B.21  The extinction coefficient as a function of wavelength of Pb(Zr$_{0.4}$Ti$_{0.6}$)O$_3$ film

Figure B.22  The extinction coefficient as a function of wavelength of Pb(Zr$_{0.5}$Ti$_{0.5}$)O$_3$ film

Figure B.23  The extinction coefficient as a function of wavelength of Pb(Zr$_{0.8}$Ti$_{0.2}$)O$_3$ film

Figure B.24  The extinction coefficient as a function of wavelength of PbZrO$_3$ film

Figure B.25  The experimental and simulated transmission spectra of PbTiO$_3$ film

Figure B.26  The experimental and simulated transmission spectra of Pb(Zr$_{0.2}$Ti$_{0.8}$)O$_3$ film

Figure B.27  The experimental and simulated transmission spectra of Pb(Zr$_{0.4}$Ti$_{0.6}$)O$_3$ film

Figure B.28  The experimental and simulated transmission spectra of Pb(Zr$_{0.5}$Ti$_{0.5}$)O$_3$ film

Figure B.29  The experimental and simulated transmission spectra of Pb(Zr$_{0.8}$Ti$_{0.2}$)O$_3$ film

Figure B.30  The experimental and simulated transmission spectra of PbZrO$_3$ film
List of Tables

Table 1.1 History of ferroelectric thin films [18]
Table 3.1 Notation descriptions of thin film optics
Table 3.2 The range of subscript i in equations 3.11 – 3.14
Table 3.3 A comparison of the envelope method with and without the back surface of the substrate by using the following values: $T_{\text{max}} = 0.85$, $T_{\text{min}} = 0.70$, $d = 300 \text{ nm}$, $n_s = 1.76$, and $\lambda = 600 \text{ nm}$
Table 3.4 Packing densities of MOD Pb(Zr$_{x}$Ti$_{1-x}$)O$_3$ thin films
Table 3.5 Constants of the dispersion relations of Pb(Zr$_{x}$Ti$_{1-x}$)O$_3$ films. The dispersion relation is written as $n^2 = 1 + A_2/(\lambda^2 - B)$, where $\lambda$ is in $\mu\text{m}$
Table 3.6 Film thickness calculation of Pb(Zr$_x$Ti$_{1-x}$)O$_3$ thin films by envelope method and the equation $2nd = mA$. Both of $\lambda$ and $d$ are in nm.
Table 3.7 Comparison of the film thickness of Pb(Zr$_x$Ti$_{1-x}$)O$_3$ thin films obtained from the envelope method with that from the simulation
Table 4.1 The values of $T_c^{\text{Py}}$, $T_c^{\text{Pe}}$, and $T_c^{\text{Pe}}$ determined by the optical method for MOD Pb(Zr$_x$Ti$_{1-x}$)O$_3$ thin films
Table 5.1 Comparison of MOCVD PZT films prepared by different investigators
Table 5.2 Examples of lead $\beta$-diketonates [68]
Table 5.3 Possible selection of metalorganic precursors and their selected properties for PbO films
Table 5.4 Possible selection of metalorganic precursors and their selected properties for ZrO$_2$ films
Table 5.5 Possible selection of metalorganic precursors and their selected properties for TiO$_2$ films
Table 5.6 Typical deposition conditions for MOCVD PZT films
Table 5.7 Summary of deposition parameters of MOCVD PZT films from different investigators
Table A.1 The molecular weight and purity of PZT precursors

xvi
Chapter 1 Introduction

1.1 Ferroelectric Materials

Ferroelectric materials are a subgroup of the pyroelectric materials, which are in turn a subgroup of the piezoelectric materials. In other words, pyroelectric materials present piezoelectric properties as well as pyroelectric properties, and ferroelectric materials possess both pyroelectric properties and piezoelectric properties, in addition to their unique ferroelectric properties.

Most of the ferroelectric materials have the ABO$_3$ perovskite structure as shown in Figure 1.1. As can be seen in Figure 1.1, the A element (which is Pb in the case of Pb(Zr$_x$Ti$_{1-x}$)O$_3$) is a large cation situated at the corners of the unit cell and the B element (which is Zr or Ti in Pb(Zr$_x$Ti$_{1-x}$)O$_3$) is a smaller cation located at the body center. The oxygen atoms are positioned at the face centers. These materials exhibit a characteristic temperature, the Curie temperature, at which the material makes a structural phase change from a polar phase (ferroelectric phase) to a non-polar phase, typically called the paraelectric phase.

Triglycine sulphate (TGS) [1] and KNO$_3$ [2] are some of earlier ferroelectric materials studied, but they are very unstable in the presence of moisture. The perovskite titanate [3] and niobate [4] families have been studied since 1950s. Among these ferroelectric materials, BaTiO$_3$ [5] and Pb(Zr$_x$Ti$_{1-x}$)O$_3$ [6] have been
Figure 1.1 Unit cell of the perovskite structure.
extensively investigated because of their excellent ferroelectric and piezoelectric properties.

1.2 Properties and Applications of Ferroelectric Materials

1.2.1 Ferroelectric Properties and Applications

One of the well-known features of ferroelectric materials is the response of the polarization to the external electric field, which is often referred to as simply the hysteresis loop or hysteresis curve as shown in Figure 1.2. PZT is one of the best-known ferroelectric materials with the ABO\(_3\) perovskite structure. In the ferroelectric phase, i.e., at the temperatures below the Curie temperature, the crystal structure of the PZT can be one of three structural formations: tetragonal, orthorhombic, or rhombohedral, depending on the Zr/Ti ratio. Figure 1.3 shows the phase diagram of the PbZrO\(_3\) – PbTiO\(_3\) solid solution [7]. As can be seen in Figure 1.3, when x < 0.53 (x is defined by the Zr fraction), PZT displays a tetragonal structure, in the range of 0.53 to 0.92 PZT has a rhombohedral structure, while when x > 0.92 it exhibits a orthorhombic structure. In the tetragonal structure, the spontaneous polarization aligns itself parallel to the c-axis. In a rhombohedral structure, a cube is stretched along a body diagonal and the spontaneous polarization aligns in the direction of the stretched body diagonal. The orthorhombic structure is formed by stretching a cube along a face diagonal along which the spontaneous polarization aligns itself.

The most attractive application of the ferroelectric materials is for nonvolatile memory devices because of their characteristic polarization response to an electric
Figure 1.2 Hysteresis loop of a ferroelectric material.
Figure 1.3 Phase diagram of PbTiO₃—PbZrO₃ solid solution [7].
field [8]. As can be seen in Figure 1.2, there is a threshold electric field, also called coercive field $E_c$, above which the polarization switches. When the external electric field is removed, the polarization decreases to a remaining value: the remanent polarization, $P_r$. In other words, no applied field is required to maintain the stored charge. Therefore, ferroelectric materials can be modeled as bistable capacitors with two distinct polarization values and thus can be used as a true nonvolatile memory.

The goal of the use of ferroelectric memories is to integrate them into the existing semiconductor devices. Figure 1.4 shows a ferroelectric random access memory (FRAM) cell developed by Ramtron corporation [9]. As can be seen in Figure 1.4, a layer of PZT film with the top and bottom electrodes is superimposed on a metal–oxide–semiconductor (MOS) transistor. The polarization of the PZT film switches to the opposite polarity when the transistor is turned on. In order to sense the polarization state of the PZT film, the film is pulsed and monitored for a given current/time wave form envelope which is indicative of its polarization state.

1.2.2 Pyroelectric Properties and Applications

Ferroelectric materials also present pyroelectric properties. Pyroelectricity results from the temperature dependence of the spontaneous polarization, $P_s$ [10]. In other words, a change in temperature produces a change in polarization. A pyroelectric material is usually described by its pyroelectric coefficient which is defined by

$$\Delta P = p \Delta T$$  \hspace{1cm} (1.1)
Figure 1.4 Ferroelectric random access memory (FRAM) cell [9].
where $\Delta P$ is the change in the polarization, $\Delta T$ is the change in the temperature, and $p$ is the pyroelectric coefficient which has the unit of nC/(cm$^2$ °C). Because a change in polarization in a solid is accompanied by a change in surface charges, it can be detected by an induced current in an external circuit.

Pyroelectric materials respond to changes in the intensity of incident radiation and not to a temporally uniform intensity. Thus humans or animals moving across the field of view of a pyroelectric detector will produce a response as a result of the movement of their warm bodies which emit infrared radiation. On the other hand, to obtain a response from stationary objects requires the radiation from them to be periodically interrupted. This is usually achieved by a sector disc rotating in front of the detector and acting as a radiation chopper.

The pyroelectric properties have been used to design a wide range of devices. For example, a pyroelectric radiometer measures the surface temperature of an object. The radiation emitted from the object has to be chopped, and so the detector receives pulses of radiation from the source and the chopper alternately. Thus the temperature is measured relative to the temperature of the chopper surface. A particular commercial pyroelectric radiometer made from an LiTaO$_3$ single crystal can be used to measure the temperatures in a range of 0 to 600°C [11]. Many other pyroelectric devices have been commercially available such as the pollutant detector, the intruder alarm, and the pyroelectric vidicon [11].

1.2.3 Piezoelectric Properties and Applications

The piezoelectric effect occurs when the materials are strained by an applied stress, a polarization is developed in the materials, and vice versa, i.e., when a
polarization is developed in the materials, they are strained [12]. The piezoelectric materials are often characterized by the effective electromechanical coupling coefficient $\kappa_{\text{eff}}^2$ which is defined as follows:

$$\kappa_{\text{eff}}^2 = \frac{\text{mechanical energy converted to electrical energy}}{\text{input mechanical energy}}$$  \hspace{1cm} (1.2)

or

$$\kappa_{\text{eff}}^2 = \frac{\text{electrical energy converted to mechanical energy}}{\text{input electrical energy}}$$  \hspace{1cm} (1.3)

One of the most important applications of the piezoelectric materials is the actuator. For example, in the fabrication of semiconductor chips, circuit components have to be precisely positioned for the various processing steps. In optical equipment, lenses and mirrors require micropositioning. In autofocusing cameras, there are actuators capable of producing precise rotational displacements. Actuators are also required for ink-jet printers, for positioning videotape-recording heads, and for micromachining metals.

1.2.4 Electro–optic Properties and Applications

The electro–optic effect is the dependence of the refractive index on an external electric field. In other words, the refractive index of an electro–optic material can be changed by an applied electric field [13].

Transparent single crystal ferroelectronics, such as lithium niobate [4], potassium dihydrogen phosphate (KDP) [14] and BaTiO$_3$ [5] have been recognized as useful electro–optic materials. However, the use of single crystal is limited by the available size, cost, and, in case of KDP, susceptibility to moisture attack. The development of
highly transparent lanthanum doped PZT (PLZT) ceramics in the 1960s led to a variety of successful electro-optic devices [15]. Recently, PLZT have been successfully prepared into a thin film form by several deposition techniques [16,17], which further enlarged the applications of electro-optic devices.

One of the very successful devices may be the integrated optic total internal reflection switch (TIR) in which the laser light confined in a PLZT thin film can be redirected by an applied field [18].

1.3 Fabrication Techniques of Ferroelectric Thin Films

A variety of techniques have been used for the deposition of ferroelectric thin films. In general, the thin film deposition techniques can be divided into two major categories; i.e., (1) physical vapor deposition (PVD) and (2) chemical processes. Among the PVD techniques, the most common methods used for the deposition of ferroelectric thin films are electron beam evaporation [19], rf diode sputtering [20], rf magnetron sputtering [21–23], dc magnetron sputtering [24], ion beam sputtering [25], molecular beam epitaxy (MBE), and laser ablation [26–29]. The chemical processes can be further divided into two subgroups; i.e., the chemical vapor deposition (CVD) and the wet chemical process including sol-gel process and metalorganic decomposition (MOD).

A chronological history of the developments of ferroelectric thin films is given in Table 1.1 [18] with the bold letters for PZT thin films. As can be seen, focusing on the PZT film development, the first successful PZT films were produced by PVD techniques (e-beam evaporation [19] and rf diode sputtering [20]) in 1976, then followed by MOD process [30] and sol-gel technique [31–32] in mid 1980s. The laser
Table 1.1 History of ferroelectric thin films [18]

<table>
<thead>
<tr>
<th>Year</th>
<th>Developments</th>
</tr>
</thead>
<tbody>
<tr>
<td>1969</td>
<td>e–beam evaporated BaTiO$_3$</td>
</tr>
<tr>
<td>1971</td>
<td>radio–frequency (rf) sputtered BaTiO$_3$</td>
</tr>
<tr>
<td>1972</td>
<td>rf sputtered Bi$_4$Ti$<em>3$O$</em>{12}$</td>
</tr>
<tr>
<td>1974</td>
<td>rf sputtered LiNbO$_3$</td>
</tr>
<tr>
<td>1975</td>
<td>liquid phase epitaxial (LPE) grown PLZT and LiNbO$_3$</td>
</tr>
<tr>
<td>1976</td>
<td>e–beam evaporated PZT, rf diode sputtered PZT</td>
</tr>
<tr>
<td>1977</td>
<td>rf sputtered epitaxial PLZT, rf sputtered (Ba,Sr)Nb$_2$O$_6$</td>
</tr>
<tr>
<td>1980</td>
<td>ion beam sputtered PZT</td>
</tr>
<tr>
<td>1982</td>
<td>chemical vapor deposited (CVD) PT</td>
</tr>
<tr>
<td>1983</td>
<td>rf planar magnetron sputtered epitaxial PLZT, direct–current (dc) sputtered Pb$_5$Ge$<em>3$O$</em>{11}$</td>
</tr>
<tr>
<td>1984</td>
<td>Metalorganic decomposition (MOD) process for PLZT, LPE grown KNbO$_3$</td>
</tr>
<tr>
<td>1985</td>
<td>dc reactive sputtered PLZT with metal targets, sol–gel PT, PZ, PZT, and PLZT</td>
</tr>
<tr>
<td>1987</td>
<td>sol–gel and sputtered PZT and PLZT for random access memory (RAM), sol–gel LiNbO$_3$</td>
</tr>
<tr>
<td>1990</td>
<td>Laser ablation PZT</td>
</tr>
<tr>
<td></td>
<td>metalorganic CVD (MOCVD) PZT</td>
</tr>
</tbody>
</table>
ablation [26–29] and metalorganic chemical vapor deposition (MOCVD) [33–38] PZT films did not appear until the beginning of the 1990s.

The PVD techniques require a high vacuum, usually better than $10^{-5}$ torr, in order to obtain a sufficient flux of atoms or ions capable of depositing onto a substrate. The advantages of the PVD techniques are (1) dry processing, (2) high purity and cleanliness, and (3) compatibility with semiconductor integrated circuit processing. However, these are offset by disadvantages such as (1) low throughput, (2) low deposition rate, (3) difficult stoichiometry control, (4) high temperature post deposition annealing, and (5) high equipment cost.

Sputtering and e–beam evaporation are examples of well established and successful PVD techniques. Although they have the above mentioned advantages and disadvantages, there are still some significant issues for these techniques. For the complex oxide films, different sputtering yields from different metal targets and the oxidation of the metal targets are some of the problems associated with reactive sputtering. Sputtering of an oxide target may avoid these problems. However, in order to incorporate sputtering into the large scale applications, some of the technical issues still need to be solved, such as the inflexibility to modify or change the stoichiometry of the deposition film. In addition, since the sputtering and the e–beam evaporation are line–of–sight deposition processes, the step coverage is a significant issue for these deposition technique.

Laser ablation is a newly developed thin film deposition technique and the understanding of this process is in its infant period. Laser ablation has found some success in depositing high temperature superconducting films [29]. There are only a few reported works on laser deposition of PZT films [26–29]. The major problems of this technique are the composition and thickness nonuniformity of the deposited films.
over a large scale. The wet chemical processes including MOD and sol–gel process consist of the following steps: (1) preparation of metalorganic precursor solution, (2) hydrolysis (for sol–gel process), (3) deposition onto a substrate by spin or dip–coating technique, (4) removal of solvent and pyrolysis, and (5) crystallization of the films. The advantages of the wet chemical process are

(1) molecular homogeneity
(2) high deposition rate and high throughput
(3) excellent composition control
(4) easy introduction of dopants
(5) low capital cost; deposition can be done in ambient condition, no vacuum processing is needed.

The major problems due to this wet process are (1) film cracking during the post–annealing process and (2) possible contamination which results in a difficulty to incorporate this technique into the semiconductor processing. However, because it provides a fast and easy way to produce the complex oxide thin films, this wet chemical process acts a very important role in the investigation of the interrelationship among the processing, the microstructure, and the property of the films.

Of all the above mentioned techniques, the MOCVD technique appears to be the most promising because it offers advantages of simplified apparatus, excellent film uniformity, composition control, high film densities, high deposition rates, excellent step coverage, and amenability to the large scale processing. The excellent film step coverage that can be obtained by MOCVD cannot be equaled by any other technique. Purity, controllability, and precision that have been demonstrated by MOCVD are competitive with the MBE technique. More importantly, novel
structures can be grown easily and precisely. MOCVD is capable of producing materials for an entire class of devices which utilize either ultra-thin layers or atomically sharp interfaces. In addition, different compositions, for example Pb(Zr$_x$Ti$_{1-x}$)O$_3$, can be fabricated using the same sources.

1.4 Objectives of Research

The objectives of this research were as follows:

1. To obtain good quality ferroelectric PZT thin films by chemical methods, namely, the MOD process and the MOCVD technique.
2. To study the optical properties of PZT thin films.
3. To develop an optical method for studying the structure development in MOD PZT films.
4. To understand the structure development in MOD PZT films.
5. To interrelate process parameters, composition, structure, and properties of MOCVD ferroelectric PZT films.
Chapter 2 Experimental Procedure

This chapter describes the preparation of PZT thin films by the metalorganic decomposition (MOD) process and the film characterization methods. The metalorganic chemical vapor deposition (MOCVD) process for PZT thin films will be discussed in Chapter 5 separately.

Sections 2.1 and 2.2 describe the preparations of the PZT solutions and films, respectively. The transmission and reflection spectra measurements are given in Section 2.3. The phase identification and the microstructure of the films were carried out by an x-ray diffractometer and a scanning electron microscope, respectively, which are described in Section 2.4. Section 2.5 describes the composition analysis using energy dispersive spectroscopy (EDS). The method for obtaining the Auger electron spectroscopic depth profile is given in Section 2.6. Finally, a detailed description of the ferroelectric property measurements is given in Section 2.7.

2.1 Preparation of Precursor Solutions

Reagent grade chemicals were used in preparing the precursor solutions. The starting precursors, lead acetate \([\text{Pb(O}_2\text{C}_2\text{H}_3)\_2\cdot\text{3H}_2\text{O}]\), titanium isopropanoxide \([\text{Ti(OC}_3\text{H}_7)\_4]\), and zirconium n-propoxide \([\text{Zr(OC}_3\text{H}_7)\_4]\) were purchased from
Johnson Matthey. The solvent, methoxyethanol \((\text{C}_3\text{H}_7\text{O}_2)\), was obtained from Fisher Scientific.

The preparation process of the PZT precursor solutions was a modification of the process developed by Budd et al. \[30\]. The properties and the decomposition behavior of these precursors were discussed in Chang's M.S. Thesis \[39\]. Figure 2.1 shows the flow chart for the preparation of PZT precursor solutions. To prepare the PZT precursor solutions, lead titanate (PT) and lead zirconate (PZ) precursor solutions were first prepared separately. The PT solution was prepared by dissolving lead acetate and titanium isopropoxide in methoxyethanol; the PZ solution was prepared by dissolving lead acetate and zirconium n-propoxide in methoxyethanol. Lead acetate was first dissolved in methoxyethanol and distilled at around 120°C to boil off the water contained in the lead acetate before the appropriate metalorganic compound of either titanium or zirconium was added. A 10% excess of lead acetate was added in both PT and PZ solutions to compensate for the PbO loss expected to take place during later high temperature post-annealings. After the solutions were cooled to room temperature, a proper amount of methoxyethanol was added to adjust their molar concentration. PZT solutions of different \(\text{Zr}/\text{Ti} \) ratio were prepared by mixing the desired volume fractions of PT and PZ solutions. The final concentration of the solutions was fixed at 0.5 molarity. A detailed step-by-step procedure for preparing the PZT precursor solutions can be found in Appendix A.

2.2 PZT Film Preparation

PZT thin films were made by placing a few drops of the precursor solution on a
Figure 2.1 A flow chart for the preparation of PZT precursor solutions.
1 inch diameter sapphire disk mounted on a Headway Research Photo–Resist Spinner and spinning at 2000 rpm for 30 seconds. The sapphire substrates were obtained from Swiss Jewel Company and had a surface orientation within a 30° cone of the [100] direction. After spin coating, the specimens were dried on a hot plate at 150°C for 5 minutes. The drying process removed the solvents in the films. In order to obtain a thick enough film for optical measurements, the above coating–drying cycle was repeated three times. Each coating resulted in a film approximately 100 nm thick. The desired film thickness can be achieved by adjusting the concentration of the precursor, the spin speed, or the number of the coating–drying cycles. Seven different Pb(Zr\textsubscript{x}Ti\textsubscript{1-x})O\textsubscript{3} compositions, i.e., x = 0.0, 0.2, 0.4, 0.5, 0.6, 0.8, and 1.0 were prepared.

Two different post–annealing treatment routes were used. For the specimens used in the optical property study (Chapter 3), after three coating–drying cycles, they were directly annealed at 650°C for 1 hour. For the specimens used in the structure development study (Chapter 4), they were heat treated at 150°C, 250°C, and 300°C and at successively higher temperatures with 20°C increments, i.e., 150°C, 250°C, 300°C, 320°C, 340°C, etc., up to 700°C for 30 min for each heat treatment. The heating rate was 10°C/min for both heat treatment routes. All the heat treatments were performed in air. Note that the same specimen was used through the entire heat treatment sequence for the structure development study. The specimens were characterized using both UV–VIS–NIR spectrophotometry and x–ray diffraction after every heat treatment. A flow chart for the preparation of PZT films by the MOD process is shown in Figure 2.2.

2.3 Optical Transmission and Reflection Spectra Measurements
Figure 2.2 A flow chart for the preparation of PZT films by MOD process.
The transmission and reflection spectra measurements were performed using a Shimadzu UV-3101PC double-beam UV-VIS-NIR scanning spectrophotometer. The transmission spectra of the samples were measured using air as a reference at a wavelength ranging from 200 nm to 2000 nm, a slit width of 3 nm, a scan speed of 200 nm/min, and a sampling interval of 1 nm. Because of its hexagonal crystalline structure, the sapphire substrate exhibits anisotropy in many optical and physical properties. The optical properties of sapphire depend on the orientation of the optic axis, or c-axis, relative to its surface. Sapphire exhibits birefringence, which is a difference in index of refraction in orthogonal directions.

The reflection spectra were measured using an aluminum mirror as a reference at a wavelength ranging from 300 nm to 2000 nm. The reflection spectrum of the aluminum mirror was pre-measured at Shimadzu by using an absolute reflectance measurement attachment. Therefore, the "real" reflection spectra of the samples were obtained by multiplying the measured spectra by the spectrum of the aluminum mirror, i.e.,

\[ R_s = R_m \left( \frac{I_s}{I_m} \right) \]  

(2.1)

where \( R_s \) and \( R_m \) are reflectances of the sample and the mirror, respectively, and \( I_s \) and \( I_m \) are the intensities measured from the sample and the mirror, respectively.

Two reflection spectra were measured for each sample; one was from the sample without the black paint on the back surface of the substrate, the other was from the sample with the black paint on the back of the substrate. The incident light is not expected to be reflected from the back surface of the sample with the black paint. The purpose of doing these two measurements is to determine the wavelength at
which the light is completely absorbed by the sample.

2.4 X-ray Diffraction and Scanning Electron Microscopy

The phase identification of the PZT films was carried out by x-ray diffraction (XRD) using a Philips PW–1792 diffractometer with Cu–Kα radiation. The specimens (deposited films on substrates) were directly characterized by the XRD. No further specimen preparation was required. The typical measurement conditions were as follows: 2θ ranged from 20° to 60°, speed was 0.1°/sec, time constant was 1 sec, slit was 0.2 mm, and intensity ranged from 1000 counts to 5000 counts. In addition, the diffractometer was operated at 30 mA and 40 kV.

The surface morphologies of the films were investigated by an ISI–SX–40 scanning electron microscope (SEM). Prior to loading the specimens into the SEM chamber, they were coated with a thin layer of gold (approximately 100 A thick) for the purpose of electric conduction. The SEM was operated at 20 kV.

2.5 Composition Determination

The composition of the films was investigated using energy dispersive spectroscopy (EDS). In the EDS measurements, the specimen was tilted 30° to the direction of the electron beam. The acceleration voltage was 20 kV. The Kα line at 4.51 eV was used for titanium, the Lα line at 2.042 eV was used for zirconium, and the Mα line at 2.34 eV was used for lead. The composition of the films observed by EDS were compared to those obtained by the electron probe microanalysis (EPMA) and were found to be in good agreement. Quantitative analysis of Pb, Zr, and Ti
ions was performed using a 8 kV, 50 mA source. Ten measurements were made at different areas of each specimen and averaged to obtain the final data point.

2.6 Auger Electron Spectroscopy

A Perkin–Elmer PHI 610 scanning Auger microprobe was used to examine the carbon contamination and to study the composition depth profile of the films. For the carbon contamination examination, the carbon KLL peak at 271 eV was used. The detection limit was better than 1 atomic percent. For the composition depth profile study, the detection windows and peaks for the elements studied were chosen as follow:

- Pb: 79 – 104 eV, MNN (94 eV)
- Zr: 132 – 157 eV, MNN (147 eV)
- Ti: 372 – 397 eV, LMM (387 eV)
- O: 495 – 515 eV, KLL (503 eV)
- Ru: 258 – 283 eV, MNN (273 eV)

The operation voltage and beam current for the electron beam were 3 kV and 0.05 μA, respectively. The operation voltage and beam current for the Ar beam were 4 kV and 5 μA, respectively. The sputtering rate was approximately 10 nm/min.

2.7 Ferroelectric Property Measurements

For the ferroelectric property measurements, the PZT films were deposited either on Pt/Ti/SiO₂/Si wafers or on RuOₓ/SiO₂/Si wafers. A simple parallel–plate capacitor configuration was used for the ferroelectric property measurements.
Either a 400 nm thick sputtered Pt layer or a 500 nm thick sputtered RuO$_x$ layer was used as a bottom electrode, depending on the substrate used. Room temperature electron beam evaporation was used for the deposition of the palladium (Pd) top electrode. Circular Pd top electrodes (300 – 400 nm thick, 0.016 cm in diameter, and 2.2 x 10$^{-4}$ cm$^2$ in area) were pattern-deposited on top of the PZT films using a mask. No post-annealing was made after the Pd top electrode deposition. The ferroelectric properties of the PZT films were determined by hysteresis loop measurements using a modified Sawyer–Tower circuit [8] at 60 Hz. In this study, a commercially available ferroelectric test system (Radiant Technology RT66A) controlled by a personal computer was used to determine ferroelectric properties. The applied voltage used was 5 volts.
3.1 Introduction

Nature of phases (i.e., composition and structure), thickness, packing density, and surface roughness are important structural parameters for thin films, because these parameters control the properties, for example, electrical, optical, and mechanical properties. X-ray diffraction is a convenient method for the phase identification of crystalline materials, although in some cases diffraction peaks from the film interfere with those of the substrate. The thickness and surface roughness of the film can be easily obtained using a profilometer [40]. However, this requires forming a sharp step between the film and the substrate. Scanning electron microscopy is a powerful tool for examining the surface morphology of the film, but it requires a metal coating on the top of electrically insulating specimens. Furthermore, none of the above mentioned techniques can be used to determine the packing density of the film.

Film packing density can be quite easily estimated from the optical properties (i.e., the refractive index) of the film [41]. In addition to providing packing density, optical property characterization of PZT films is quite valuable for the fabrication of both optical and electro-optic devices.

In this chapter, the thin film optics is first discussed in detail. Based on the
thin film optics, the envelope method with the consideration of the light intensity loss from the back surface of the substrate is then derived. The original envelope method was proposed without the consideration of the light intensity loss from the back surface of the substrate by Manifacier in 1976 [42]. Although Swanepoel [43] took the back surface of the substrate into consideration in 1983 and improved the accuracy of the extinction coefficient, he still derived the same equation for the calculation of the refractive index as Manifacier had. The mistake they made will be pointed out in this study.

In this study, the thickness measurement from the interference fringes of the transmission spectrum is cross checked by a computer simulation procedure. The accuracy in the thickness measurement is found to be better than 2%. The optical properties were measured not only in the medium and weak absorption regions by the envelope method but also in the strong absorption region by both the transmission and the reflection spectra.

Optical properties of perovskite PZT films, fabricated by the MOD process, were investigated using both transmission and reflection spectra in the wavelength range from 200 nm to 2000 nm. The refractive index, extinction coefficient, and the thickness of the film were calculated from the transmission spectra. The packing density of each film was derived from its refractive index. The refractive indices were fit to a Sellmeier type dispersion equation [44]. The surface roughness of each film was qualitatively estimated from the extinction coefficient. Also, the absorption coefficient and the near band gap energy of each film was calculated from its extinction coefficient.

3.2 Theoretical Background
3.2.1 Thin Film Optics

A starting point from which to derive the equations for thin film optics is Maxwell’s equations. For an isotropic medium, Maxwell’s equations are

\[ \text{div } D = \varepsilon \text{ div } E = 4\pi \rho \]  
\[ (3.1) \]

\[ \text{div } D = \mu \text{ div } H = 0 \]  
\[ (3.2) \]

\[ \text{curl } E = -\frac{\mu}{c} \frac{\partial H}{\partial t} \]  
\[ (3.3) \]

\[ \text{curl } H = \frac{4\pi \sigma E}{c} + \frac{\varepsilon}{c} \frac{\partial E}{\partial t} \]  
\[ (3.4) \]

where the symbols have their usual meanings. For a non-conducting medium (\( \sigma = 0 \)) in which there is no space-charge, these relations reduce to the well-known simple form of wave equations, which show that the wave propagates with velocity \( c/\sqrt{\varepsilon \mu} \).

\[ \frac{\varepsilon \mu}{c^2} \frac{\partial^2 E}{\partial t^2} = \nabla^2 E \]  
\[ (3.5) \]

\[ \frac{\varepsilon \mu}{c^2} \frac{\partial^2 H}{\partial t^2} = \nabla^2 H \]  
\[ (3.6) \]

Because the value of \( \mu \) for all materials is insensibly different from unity at optical frequencies, the velocity of propagation is \( c/\sqrt{\varepsilon} \) where \( \varepsilon \) is the dielectric constant at the frequency of the light wave. From the definition of refractive index, the
well-known result, \( n = \sqrt{\epsilon} \) is obtained. The problem of determining the fraction of light reflected and transmitted at a boundary separating two media is dealt with by applying boundary conditions to the solutions of wave equations, i.e. equations 3.5 and 3.6 in the present case.

For the convenience and to avoid any confusion, the notations of thin film optics used hereafter are described in Table 3.1.

3.2.1.1 Multi-layer Thin Film System

Figure 3.1 schematically illustrates the transmittance and reflectance of a multi-layer thin film system. The system consists of an \( m \)-layer thin film with the complex refractive index of each layer given by \( N_i \) and the corresponding film thickness by \( d_i \) and a semi-infinite substrate with the complex refractive index \( N_{m+1} \). The angle between the incident light and the surface normal is given by \( \varphi_0 \). The intensity of the incident light is denoted by \( I_0 \), that of the reflected light by \( I_r \), and that of the transmitted light by \( I_t \). The transmittance \( (T) \) and reflectance \( (R) \) are then defined by:

\[
T = \frac{I_t}{I_0} \quad (3.7)
\]

and

\[
R = \frac{I_r}{I_0} \quad (3.8)
\]

\( T \) and \( R \) are experimentally measurable quantities and may also be defined in terms of a function of \( N_i \) and \( d_i \) for a given \( \lambda \) and \( \varphi_0 \). Thus if \( N_i \) and \( d_i \) are known, \( T \) and \( R \) can be mathematically calculated for a given \( \lambda \) and \( \varphi_0 \). The equations for
Table 3.1 Notation descriptions of thin film optics

<table>
<thead>
<tr>
<th>Notation</th>
<th>Description</th>
</tr>
</thead>
<tbody>
<tr>
<td>$T_m$</td>
<td>Transmittance of $m$-layer thin films on a finite substrate</td>
</tr>
<tr>
<td>$R_m$</td>
<td>Reflectance of $m$-layer thin films on a finite substrate</td>
</tr>
<tr>
<td>$T_m'$</td>
<td>Transmittance of $m$-layer thin films on a semi-infinite substrate</td>
</tr>
<tr>
<td>$R_m'$</td>
<td>Reflectance of $m$-layer thin films on a semi-infinite substrate</td>
</tr>
<tr>
<td>$r_i$</td>
<td>Reflectance at the $i^{th}$ interface</td>
</tr>
<tr>
<td>$d_i$</td>
<td>Thickness of the $i^{th}$ layer thin film</td>
</tr>
<tr>
<td>$N_i$</td>
<td>Complex index of refraction of the $i^{th}$ layer thin film</td>
</tr>
<tr>
<td>$n_i$</td>
<td>Refractive index of the $i^{th}$ layer thin film</td>
</tr>
<tr>
<td>$k_i$</td>
<td>Extinction coefficient of the $i^{th}$ layer thin film</td>
</tr>
<tr>
<td>$\alpha_i$</td>
<td>Absorption coefficient of the $i^{th}$ layer thin film</td>
</tr>
</tbody>
</table>
Figure 3.1 A schematic diagram of the transmitted and reflected light in a m-layer thin film system.
calculating $T$ and $R$ from $N_j$ and $t_i$ can be found in two excellent books, Heavens [45] and Azzam and Bashara [46].

If the direction of the incident light is normal to the surface of the system, i.e. $\varphi_0 = 0$, the calculation of $T$ and $R$ can be dramatically simplified. A comprehensive recurrence relation method provided by Heavens [45] is adopted in this study for the purpose of easy computer programming. In Heavens method, $T_m'$ and $R_m'$, below, taking note that the notations are different from his (see Table 3.1), are expressed as:

$$T_m' = \frac{m+1}{n_0} \frac{\prod_{i=1}^{m+1} [1 + g_i^2 + h_i^2]}{(p_{1,m+1}^2 + q_{1,m+1}^2)} (3.9)$$

$$R_m' = \frac{t_{1,m+1}^2 + u_{1,m+1}^2}{(p_{1,m+1}^2 + q_{1,m+1}^2)} (3.10)$$

where

$$p_{1,i+1} = p_{1,i} p_{i+1} - q_{1,i} q_{i+1} + r_{1,i} t_{i+1} - s_{1,i} u_{i+1} (3.11a)$$

$$q_{1,i+1} = q_{1,i} p_{i+1} + p_{1,i} q_{i+1} + s_{1,i} t_{i+1} + r_{1,i} u_{i+1} (3.11b)$$

$$t_{1,i+1} = t_{1,i} p_{i+1} - u_{1,i} q_{i+1} + v_{1,i} t_{i+1} - w_{1,i} u_{i+1} (3.11c)$$

$$u_{1,i+1} = u_{1,i} p_{i+1} + t_{1,i} q_{i+1} + w_{1,i} t_{i+1} + v_{1,i} u_{i+1} (3.11d)$$

$$r_{1,i+1} = p_{1,i} r_{i+1} - q_{1,i} s_{i+1} + r_{1,i} v_{i+1} - s_{1,i} w_{i+1} (3.11e)$$

$$s_{1,i+1} = q_{1,i} r_{i+1} + p_{1,i} s_{i+1} + s_{1,i} v_{i+1} + r_{1,i} w_{i+1} (3.11f)$$

$$v_{1,i+1} = t_{1,i} r_{i+1} - u_{1,i} s_{i+1} + v_{1,i} v_{i+1} - w_{1,i} w_{i+1} (3.11g)$$

$$w_{1,i+1} = u_{1,i} r_{i+1} + t_{1,i} s_{i+1} + w_{1,i} v_{i+1} + v_{1,i} w_{i+1} (3.11h)$$

$$p_i = \exp(a_i d_{i-1}/2) \cos(\gamma_i d_{i-1}/2) (3.12a)$$
\[ q_i = \exp(\alpha_i d_{i-1}/2) \sin(\gamma_i d_{i-1}/2) \] (3.12b)

\[ t_i = \exp(-\alpha_i d_{i-1}/2) \left[ g_i \cos(\gamma_i d_{i-1}/2) + h_i \sin(\gamma_i d_{i-1}/2) \right] \] (3.12c)

\[ u_i = \exp(-\alpha_i d_{i-1}/2) \left[ h_i \cos(\gamma_i d_{i-1}/2) - g_i \sin(\gamma_i d_{i-1}/2) \right] \] (3.12d)

\[ r_i = \exp(\alpha_i d_{i-1}/2) \left[ g_i \cos(\gamma_i d_{i-1}/2) - h_i \sin(\gamma_i d_{i-1}/2) \right] \] (3.12e)

\[ s_i = \exp(\alpha_i d_{i-1}/2) \left[ h_i \cos(\gamma_i d_{i-1}/2) + g_i \sin(\gamma_i d_{i-1}/2) \right] \] (3.12f)

\[ v_i = \exp(-\alpha_i d_{i-1}/2) \cos(\gamma_i d_{i-1}/2) \] (3.12g)

\[ w_i = -\exp(-\alpha_i d_{i-1}/2) \sin(\gamma_i d_{i-1}/2) \] (3.12h)

\[ \alpha_i = \frac{4\pi k_i}{\lambda} \] (3.13a)

\[ \gamma_i = \frac{4\pi n_i}{\lambda} \] (3.13b)

\[ g_i = \frac{n_{i-1}^2 + k_{i-1}^2 - n_i^2 - k_i^2}{(n_{i-1} + n_i)^2 + (k_{i-1} + k_i)^2} \] (3.14a)

\[ h_i = \frac{2(n_i - k_i) - n_i k_i}{(n_{i-1} + n_i)^2 + (k_{i-1} + k_i)^2} \] (3.14b)

with the initial values of \( p_{11} = 1, q_{11} = 0, t_{11} = g_{11}, u_{11} = h_{11}, r_{11} = g_{11}, s_{11} = h_{11}, v_{11} = 1, \) and \( w_{11} = 0. \) In addition, the range of the subscript \( i \) is different for the above equations, and is listed in Table 3.2. Equations 3.9 and 3.10 are valid only if the film is homogeneous and the thickness of the film is uniform.

### 3.2.1.2 Single Layer Film on a Transparent Substrate

For a system of a single layer absorbing film on a transparent substrate, equation 3.9 becomes:
Table 3.2 The range of subscript $i$ in equations 3.11–3.14

<table>
<thead>
<tr>
<th>Equations</th>
<th>running range of $i$</th>
</tr>
</thead>
<tbody>
<tr>
<td>3.11a – 3.11d</td>
<td>$1 \leq i \leq m$</td>
</tr>
<tr>
<td>3.11e – 3.11h</td>
<td>$1 \leq i \leq m-1$</td>
</tr>
<tr>
<td>3.12a – 3.12d</td>
<td>$2 \leq i \leq m+1$</td>
</tr>
<tr>
<td>3.12e – 3.12h</td>
<td>$2 \leq i \leq m$</td>
</tr>
<tr>
<td>3.13a – 3.13b</td>
<td>$1 \leq i \leq m$</td>
</tr>
<tr>
<td>3.14a – 3.14b</td>
<td>$1 \leq i \leq m+1$</td>
</tr>
</tbody>
</table>
\[ T_1' = \frac{n_2}{n_0} \frac{[(1+g_1)^2 + h_1^2]}{p_1,2} \frac{[(1+g_2)^2 + h_2^2]}{q_1,2} \]  

(3.15)

Recall that \( T_1' \) represents the transmittance of a single film on a semi-infinite substrate and \( n_2 \) is the refractive index of the substrate. By using equations 3.11–3.14, \( T_1' \) can be explicitly expressed in terms of the optical constants of the film and the substrate, the film thickness, and the wavelength \( \lambda \):

\[ T_1' = \frac{Ax}{B - Cx - Dx^2} \]  

(3.16)

where

\[ x = \exp(-\alpha_1 d_1) \]

\[ A = 16 \frac{n_0 n_2 (n_1^2 + k_1^2)}{n_2} \]

\[ B = \left[(n_0 + n_1)^2 + k_1^2\right] \left[(n_1 + n_2)^2 + k_1^2\right] \]

\[ C = 2 \left[(n_1^2 - n_0^2 + k_1^2)(n_1^2 - n_2^2 + k_1^2) - 4k_1^2n_2\right] \cos(\gamma) - 2\left[2k_1n_2(n_1^2 - n_0^2 + k_1^2) + 2k_1(n_1^2 - n_2^2 + k_1^2)\right] \sin(\gamma) \]

\[ D = \left[(n_1 - n_0)^2 + k_1^2\right] \left[(n_1 - n_2)^2 + k_1^2\right] \]

and \( \alpha_1 \) is the absorption coefficient which is equal to \( 4\pi k_1/\lambda \), \( \gamma \) is equal to \( 4\pi n_1 d_1/\lambda \), \( d_1 \) is the film thickness, \( k_1 \) is the extinction coefficient, and \( n_0, n_1, \) and \( n_2 \) are the refractive indices of the ambient (air), film, and substrate, respectively. In addition to the assumptions made in section 3.2.1.1, equation 3.16 assumes that the substrate is completely transparent, i.e., \( k_2 = 0 \).
3.2.2 Envelope Method

In a multi-layer thin film system, if the complex refractive index and the thickness of each thin film layer are known, the reflectance and transmittance can be calculated exactly no matter how many layers are in the system or what the incident angle of the light is. All these quantities except the film thickness are wavelength dependent. However, in practice, a reverse calculation is needed, i.e., the optical constants and thickness of the film need to be calculated from the measured reflection and transmission spectra. There are only two measurable quantities T and R, but 3m+2 unknowns (three unknowns n, k, and d for each layer and two unknowns n and k for the substrate) at a given wavelength and incident angle. For a simple thin film system consisting of a single film on substrate, there are still three unknowns for the film but two measured T and R for a given wavelength and incident angle, assuming the optical constants of the substrate are known. The difficulty of calculating the optical constants and the thickness of the film from T and R is not only that the number of unknowns is larger than the number of quantities one can measure, but also that the optical constants cannot be explicitly expressed in terms of T and R.

Fortunately, for a single layer weakly absorbing film on a transparent substrate, the refractive index and extinction coefficient as a function of wavelength, and film thickness can be obtained from the transmission spectra alone. This method, which is referred to as the "envelope method" hereafter, was first presented by Manifacier [42]. This is a very useful approach to study the optical properties of insulating films since most of them are weakly absorbing materials.

Before starting to derive the equations for describing the envelope method,
some subscripts used in section 3.2.1.2 are dropped for the sake of simplicity. Figure 3.2 shows the schematic diagram of a weakly absorbing thin film on a completely transparent substrate. The refractive index of the ambient is $n_0$; $n_s$ is the refractive index of the substrate; $n$, $k$, and $d$ denote the refractive index, extinction coefficient, and the thickness of the film, respectively.

The transmittance of a single film on a transparent substrate has been described in equation 3.16 of section 3.2.1.2. The equations describing the envelope method can be derived from equation 3.16 with the further assumptions that:

1. The substrate is completely transparent, i.e. $k_s = 0$;
2. the square of the refractive index of the film is much greater than that of the extinction of the film, i.e. $n^2 >> k^2$;
3. the square of the refractive index difference between the film and air and the film and substrate is much greater than that of the extinction coefficient of the film, i.e. $(n-1)^2 >> k^2$ and $(n-n_s)^2 >> k^2$.

The first assumption will be verified in section 3.3. The second assumption leads to $A = 16 n_0 n^2 n_s$ and $B = (n_0 + n)^2 (n + n_s)^2$ (equation 3.16). The third assumption leads to $C = 2 [(n^2 - n_0^2)(n^2 - n_s^2)] \cos(\gamma)$ and $D = (n-n_0)^2(n-n_s)^2$ in equation 3.16. The most critical assumption of these is $(n-n_s)^2 >> k^2$. For the present study, the films are PZT solid solutions having a refractive index greater than 2.1 and the substrate is sapphire having the refractive index around 1.76. Therefore, if $k^2/(n-n_s)^2 \leq 0.01$ and if $n = 2.1$ and $n_s = 1.76$, $k$ must be smaller than 0.034.

With the above assumptions, equation 3.16 becomes

$$T'_{1'} = \frac{16 n_s n^2 x}{(1+n)^2(n+n_s)^2 - 2x[(n^2-1)(n^2-n_s^2)]\cos(\gamma) + (n-1)^2(n-n_s)^2x^2} \quad (3.17)$$
Figure 3.2 A schematic diagram of a weakly absorbing thin film on a completely transparent semi-infinite substrate.
here 1 is used to replace \( n_0 \) which is the refractive index of air and \( \gamma = 4\pi nd/\lambda \). It is identical to the formula derived by Manifacier [42]. The cosine function in the denominator oscillates between +1 and −1, which results in the well-known equation for the interference fringes in the transmission spectrum:

\[
2\pi d = m\lambda \quad (3.18)
\]

where the order number \( m \) is an integer for maxima and a half integer for minima. Equation 3.17 gives the top envelope equation for \( \cos(\gamma) = 1 \) as

\[
T_{\text{max}'} = \frac{16 \, n_s^2 \, n^2 \, x}{[(1+n)(n+n_s) - (n-1)(n-n_s)x]^2} \quad (3.19)
\]

whereas, for \( \cos(\gamma) = -1 \), the bottom envelope equation becomes

\[
T_{\text{min}'} = \frac{16 \, n_s^2 \, n^2 \, x}{[(1+n)(n+n_s) + (n-1)(n-n_s)x]^2} \quad (3.20)
\]

Equations 3.19 and 3.20 can be solved for \( n \) and \( x \) giving

\[
x = \frac{(n+1)(n+n_s)/[(T_{\text{max}'}/T_{\text{min}'})(0.5-1)]}{(n-1)(n-n_s)/[(T_{\text{max}'}/T_{\text{min}'})(0.5+1)]} \quad (3.21)
\]

\[
n = [N' + (N' 2n_s^2)^{0.5}]^{0.5} \quad (3.22)
\]

where \( N' = \frac{1}{2} (1+n_s^2) + 2n_s \frac{T_{\text{max}'} - T_{\text{min}'}'}{T_{\text{max}'}/T_{\text{min}'}'}. \) Once \( T_{\text{max}'} \) and \( T_{\text{min}'} \) are obtained from the measured transmission spectrum and the refractive index of the substrate is known, the refractive index of the film can be calculated as a function of
wavelength using equation 3.22. If \( n(\lambda_1) \) and \( n(\lambda_2) \) are the refractive indices at two adjacent maxima (or minima), at \( \lambda_1 \) and \( \lambda_2 \), it follows that the film thickness is given by the expression

\[
d = \frac{\lambda_1 \lambda_2}{2 \left[ n(\lambda_1) \lambda_2 - n(\lambda_2) \lambda_1 \right]}
\]

(3.23)

Also, the extinction coefficient \((k)\) and absorption coefficient \((\alpha)\) of the film can be calculated by equation 3.21 and the relation \( \alpha = 4\pi k/\lambda \).

3.2.3 Consideration of Light Intensity Loss from the Back Surface of the Substrate

In all of the equations derived in sections 3.2.1 and 3.2.2 for calculating transmittance and reflectance it was assumed that the substrate is semi-infinite. In other words, for the transmittance measurement, the specimen could have to be a free standing film or else the detector could have to be installed "inside" the substrate in order for these equations to be valid. Therefore, if the specimen consists of a film on a thick substrate and if the detector has to be installed "outside" the substrate, the light intensity loss from the back surface of the substrate must be taken into account.

To take the back surface of the substrate into account, we start from the basic equations for Fresnel reflection coefficients. Consider the reflection and transmission of light at the planar interface between two semi-infinite homogeneous and optically isotropic media denoted by 0 and 1 with complex indices of refraction \( N_0 \) and \( N_1 \), respectively. The Fresnel reflection coefficients for the parallel polarization \((r_p)\) and perpendicular polarization \((r_s)\) can be expressed as
\[ r_p = \frac{N_0 \cos \varphi_1 - N_1 \cos \varphi_0}{N_1 \cos \varphi_0 + N_0 \cos \varphi_1} \]  
\[ (3.24) \]

\[ r_s = \frac{N_0 \cos \varphi_0 - N_1 \cos \varphi_1}{N_0 \cos \varphi_0 + N_1 \cos \varphi_1} \]  
\[ (3.25) \]

where \( \varphi_0 \) is the angle of incidence and \( \varphi_1 \) is the angle of refraction. The reflectances \( r_p \) and \( r_s \), defined by the fraction of the total intensity that appears in the reflected wave for the \( p \) and \( s \) polarizations, are the amplitudes of the Fresnel reflection coefficients, i.e. \( r_p = r_p r_p^* \) and \( r_s = r_s r_s^* \). For the case of normal incidence, \( \varphi_0 = \varphi_1 = 0 \), if the complex refractive index is written in terms of the refractive index and the extinction coefficient, i.e. \( N = n - i k \), the reflectance may be written:

\[ r = r_p = r_s = \frac{(n_1 - n_0)^2 + (k_1 - k_0)^2}{(n_1 + n_0)^2 + (k_1 + k_0)^2} \]  
\[ (3.26) \]

To modify the equations in sections 3.2.1.1 and 3.2.1.2 by adding the back surface of the substrate, the simplest example of a "thick" substrate is used. The term "thick" is emphasized because the interference fringes disappear if the sampling interval \( \Delta \lambda \) is several times larger than \( \lambda^2 / 4 \eta d \) [47]. Also, for the purpose of this study, the extinction coefficient of this "thick" substrate is assumed to be zero and the case of the normal incidence is considered. Figure 3.3 schematically shows how the transmittance and reflectance of an uncoated substrate are calculated. Summation of the intensities from the multi-reflection and transmission at each interface gives the total transmittance and reflectance as

\[ T_0 = \frac{1 - r}{1 + r} \]  
\[ (3.27) \]

39
Figure 3.3 A schematic diagram for the calculation of the transmittance and the reflectance of an uncoated substrate.
where \( r \) is the reflectance at each interface; it may be expressed as given in equation 3.26. Recall that \( T_0 \) and \( R_0 \) are the transmittance and reflectance of 0 layer film on a finite substrate, i.e., an uncoated finite substrate. Following the same procedure, for a sample consisting of \( m \) layers "thick" transparent films on a transparent substrate, the transmittance becomes

\[
T_m = \frac{m+2}{\prod_{i=1}^{m+1} (1-r_i)}
\]

where \( r_1, r_2, \ldots, r_{m+2} \) are the reflectances at the first interface, which is the air/first film interface to the last interface, which is the substrate/air interface; \( r_i \) is given by equation 3.26. Therefore, the transmittance of a thin film consisting of \( m \) layers on a substrate, with the consideration of the back surface of the substrate, can be approximately treated as

\[
T_m = T_m' \frac{1-r_{m+2}}{1-r_{m+1}r_{m+2}}
\]

where \( T_m' \) is the transmittance of a thin film consisting of \( m \) layers on a semi–infinite substrate (see equation 3.9). The reflectance can be approximated as

\[
R_m = R_m' + (T_m' - T_m)(R_m' + T_m')
\]

where \( R_m' \) is the reflectance of a thin film consisting of \( m \) layers on a semi–infinite substrate.
substrate (see equation 3.10).

Since $r_m r_{m+2} << 1$, which can be easily verified, equation 3.30 can be further approximated by neglecting $r_m r_{m+2}$. Applying this approximation to equation 3.30 and combining it with equation 3.17, it follows that

$$T = 16 \frac{n_s n^2 x (1-r_3)}{(1+n)^2(n+n_s)^2 - 2x[(n^2-1)(n^2-n_s^2)]\cos(\gamma) + (n-1)^2(n-n_s)^2x^2} \tag{3.32}$$

where $r_3$ is the reflectance at the interface of air–back substrate surface, which is equal to $(n_s-1)^2/(n_s+1)^2$. Equation 3.32 differs from equation 3.17 by a factor of $1-r_3$. Starting from equation 3.32 and following the same procedure in section 3.2.2, the solutions for $x$ and $n$ are found to have the exact same forms as equations 3.21 and 3.22, respectively. The only difference appears in $N'$ (see equation 3.22), due to the extra factor of $(1-r_3)$, which becomes

$$N = \frac{1}{2} (1+n_s^2) + \frac{8n_s^2}{(n_s+1)^2} \frac{T_{\text{max}} - T_{\text{min}}}{T_{\text{max}} T_{\text{min}}} \tag{3.33}$$

To demonstrate the significant difference between the calculations with and without regard to the back surface of the substrate, an example is used. We take $T_{\text{max}} = 0.85$, $T_{\text{min}} = 0.70$, $d = 300$ nm, $n_s = 1.76$, and $\lambda = 600$ nm; a comparison of these two cases is listed in Table 3.3. Although the difference in the refractive index $n$ is only 1.5%, a surprising difference in the extinction coefficient $k$, of as large as 17 times was observed. This huge difference in $k$ can be easily understood by checking the reflection loss on a bare substrate. Taking the above example, for a semi–infinite substrate with $n_s = 1.76$, $R_0' = 0.076$ at the interface (equation 3.26);
Table 3.3  A comparison of the envelope method with and without the back surface of the substrate by using the following values: $T_{\text{max}} = 0.85$, $T_{\text{min}} = 0.70$, $d = 300\text{nm}$, $n_s = 1.76$, and $\lambda = 600\text{nm}$.

<table>
<thead>
<tr>
<th></th>
<th>$N$</th>
<th>$n$</th>
<th>$x$</th>
<th>$a(\text{cm}^{-1})$</th>
<th>$k$</th>
</tr>
</thead>
<tbody>
<tr>
<td>Manifacier$^1$</td>
<td>2.9362</td>
<td>2.2992</td>
<td>0.9272</td>
<td>2521</td>
<td>0.0120</td>
</tr>
<tr>
<td>Swanepoel$^2$</td>
<td>2.9362</td>
<td>2.2992</td>
<td>0.9907</td>
<td>313</td>
<td>0.0015</td>
</tr>
<tr>
<td>This study</td>
<td>2.8689</td>
<td>2.2659</td>
<td>0.9956</td>
<td>146</td>
<td>0.0007</td>
</tr>
</tbody>
</table>

$^1$Reference 42

$^2$Reference 43
hence, \( T_0' = 0.924 \). For a real substrate (finite thickness), \( R_0 = 0.141 \) and \( T_0 = 0.859 \) (see equations 3.27 and 3.28). Consequently, it becomes clear that the small \( k \) (0.0007) is expected from the difference between \( T_{\text{max}} \) and \( T_0 \), while the huge \( k \) (0.0120) results from the big difference between \( T_{\text{max}} \) and \( T_0' \). This means that if the formulae in section 3.2.2 are used to calculate \( n \) and \( k \) of the film, the reflection loss from the back surface of the substrate is counted into the extinction coefficient of the film.

To the best of my knowledge, equations 3.32 and 3.33 are being reported for the first time to calculate \( n \) and \( k \) of a weakly absorbing film on a transparent substrate. This is surprising because since the time Manifacier first derived the envelope method in 1976, many authors have used his equations without mentioning the importance of the back surface of the substrate.

3.2.4 Effective Medium Approximation

The dielectric response of a heterogeneous medium can be described in terms of the dielectric properties of its components [48]. The effective dielectric response of a heterogeneous medium can be described by the Bruggeman effective medium approximation (EMA) [49,50]. According to the effective medium approximation, the relationship of the effective dielectric function \( (\varepsilon) \) of a heterogeneous medium, the dielectric function \( (\varepsilon_i) \) of each component, and the volume fraction \( (f_i) \) of each component is given by

\[
\sum_{i=1}^{n} f_i \left( \frac{\varepsilon_i - \varepsilon}{\varepsilon_i + 2\varepsilon} \right) = 0
\]  

(3.34)
where \( n \) is the number of components in the heterogeneous medium.

In general, most methods produce films with packing densities less than one. Therefore, the porosity needs to be considered as a separate phase in the so-called "single phase" film. The EMA can consequently be applied to calculate the packing density of a single phase film. For most oxides, the extinction coefficient is much smaller than the refractive index at a given wavelength. Thus the dielectric function at optical frequencies can be related to the refractive index \( n \) by \( \epsilon = n^2 \). For a single phase porous film, the EMA becomes

\[
f \frac{n_b^2 - n^2}{n_b^2 + 2n^2} + \left( 1 - f \right) \frac{1 - n^2}{1 + 2n^2} = 0 \quad (3.35)
\]

where \( f \) is the volume fraction or the packing density of the film, \( n_b \) is the refractive index of the bulk material, and \( n \) is the effective (or measured) refractive index.

### 3.2.5 Optical Constants at Near Band Gap

At near optical band gap region, for a single film on a transparent substrate, the transmittance of the specimen can be written as [51]

\[
T = \frac{(1-r_1)(1-r_2)(1-r_3)\exp(-\alpha d)}{(1-r_1 r_2) \left\{ 1 - \frac{r_1 r_2 + r_1 r_3 (1-r_2)^2}{1} \exp(-2\alpha d) \right\} } \quad (3.36)
\]

where \( \alpha \) is the absorption coefficient of the film, \( d \) is the film thickness, and \( r_1, r_2, \) and \( r_3 \) are the reflectance of air–film, film–substrate, and substrate–air interfaces, respectively. Since \( r_2 \ll 1 \) and \( \exp(-2\alpha d) \ll 1 \), equation 3.36 can be reduced to
On the other hand, because of the strong absorption of the film, light cannot reach the second (film-substrate) and the third (substrate-air) interfaces. Therefore, the reflectance of the specimen is approximately equal to the reflectance of the air-film interface, i.e.,

\[ R = r_1 \]  

(3.38)

Although the extinction coefficient (k) is large at wavelengths near the optical band gap, it is still negligible compared to the refractive index (n). Thus, the refractive index of the film can be related to the reflectance of the specimen by equations 3.26 and 3.38

\[ n = \frac{(1 + \sqrt{R})}{(1 - \sqrt{R})} \]  

(3.39)

Therefore, the absorption coefficient of the film can be obtained by rewriting equation 3.37

\[ \alpha = \frac{1}{d} \ln \left( \frac{1-R}{T} \right) \frac{[1-(n-n_s)^2]/(n+n_s)^2}{[1-(n_s-1)^2]/(n_s+1)^2} \]  

(3.40)

All the computer programs used in this study are collected in Appendix C.

3.3 Optical Properties of Sapphire Substrate
The substrate used in this study is sapphire (single crystal Al₂O₃). Optical grade sapphire disks 1 inch in diameter and 1 mm thick were obtained from Swiss Jewel Company and had a surface orientation within a 30° cone of the [100] direction. Sapphire is in many ways an excellent window material. Because of its extreme surface hardness, sapphire can be scratched by only a few substances (such as diamond or boron nitride) other than itself. Chemically inert and insoluble in almost everything at room temperature, sapphire can be cleaned with impunity; even hydrogen fluoride fails to attack sapphire at temperatures below 300°C. Because of its excellent hardness and inertness to chemicals, sapphire can be reused many times. A solution of hydrogen fluoride, nitric acid, and water (1:1:1 in volume) can be utilized to remove the film at room temperature without damaging the sapphire.

A dispersion relation for the ordinary ray in sapphire has been determined by Malitson [52]:

$$n^2 = 1 + \frac{A\lambda^2}{\lambda^2 - \lambda_1^2} + \frac{B\lambda^2}{\lambda^2 - \lambda_2^2} + \frac{C\lambda^2}{\lambda^2 - \lambda_3^2}$$  (3.41)

where

$$A = 1.023798$$
$$B = 1.058264$$
$$C = 5.280792$$
$$\lambda_1 = 0.00377588$$
$$\lambda_2 = 0.0122544$$
$$\lambda_3 = 321.3616$$
The unit of $\lambda$ is in $\mu$m.

By using the above dispersion relation for the refractive index and assuming the extinction coefficient to be zero, the transmittance of sapphire substrate can be calculated. Figure 2.4 shows the experimental transmission spectrum and the calculated spectrum of sapphire. As can be seen from Figure 2.4, these two spectra agree with each other very well. Therefore, equation 3.41 and the assumption of $k = 0$ can be applied for all the optical property calculations in this study.

3.4 X-ray Diffraction Study

Before the optical measurements, the films were insured of having the perovskite structure by X-ray diffraction (XRD). The XRD patterns of the specimens are shown in Figure 2.5. Figure 2.5 shows that the formation of the perovskite phase was completed for all compositions at an annealing temperature of 650°C for 1 hour. As can be seen from the splitting of the \{100\}, \{110\}, \{200\}, and \{211\} peaks, the films with compositions between $x = 0.0$ and 0.4 showed a tetragonal structure while those with composition $x = 0.5$ were on the porphotropic phase boundary. On the other hand, films with compositions $x = 0.6$ and 0.8 were rhombohedral, while those with composition $x = 1.0$ showed orthorhombic structure. From the position of the x-ray diffraction peaks it can be seen that the lattice parameters also showed the expected systematic variation with the Zr/Ti ratio [32].
Figure 3.4 Comparison of the experimental and the calculated transmission spectra of sapphire.
Figure 3.5 XRD patterns of MOD Pb(Zr$_x$Ti$_{1-x}$)O$_3$ films on sapphire substrates. The samples were annealed at 650°C for 1 hour.
3.5 Optical Constants and Film Thickness of PZT Solid Solutions

Figure 3.6 shows an example of the transmission spectrum of a weakly absorbing Pb(Zr$_{0.6}$Ti$_{0.4}$)O$_3$ film on a completely transparent substrate (sapphire). The top solid curve is the transmittance of the uncoated sapphire. The fringes are a result of the interference between two interfaces: the air–film and the film–substrate. The transmittance $T(\lambda)$ of the sample is enveloped by two dashed curves, $T_{\text{max}}$ and $T_{\text{min}}$, which are the curves drawn through the maxima and minima of $T(\lambda)$. The "gap" between the transmission spectrum of the substrate and $T_{\text{max}}$ is indicative of the light loss due to the scattering and/or absorption. Based on the strength of the absorption, the transmission spectrum can be roughly divided into three regions: weak, medium, and strong absorption regions. In this study, the region at the transmittance values higher than 0.6 will be considered as the weak absorption region, the values between 0.3 and 0.6 will be considered as the medium absorption region, and the values lower than 0.3 will be considered as the strong absorption region. For the given example (Figure 3.6), the region at the wavelength longer than 450 nm is assigned to be the weak absorption region, from 350 nm to 450 nm is the medium absorption region, and at wavelengths shorter than 350 nm is the strong absorption region.

Once $T_{\text{max}}$ and $T_{\text{min}}$ are obtained, the refractive index of the film can be easily calculated by using equations 3.22 and 3.33 as a function of wavelength. It seems to be quite straightforward to calculate the optical constants using the envelope method. The questions are how to determine the envelope curves and where the wavelength limit of the envelope method is.

For the first question, although a computer program called ENVELOPE was
Figure 3.6 Optical transmission spectrum of $\text{Pb(Zr}_{0.6}\text{Ti}_{0.4})\text{O}_3$ film on sapphire with that of the uncoated substrate. The envelope curves are shown as the dashed curves.
obtained from National Institute of Standards and Technology [53] to help the
determination of the envelope curves (T_{max} and T_{min}), it does not work in our case.
The reason may be that the films are too thin for this computer program. For a
film having a thickness of about 300 nm, the number of the maxima or minima of
the interference fringes is three or four, as can be seen in Figure 3.6. Therefore, in
many cases, an unsatisfactory curve generated by a computer program from only
three points is understandable. In addition, we tried to write a computer program
to solve this problem by using B-spline interpolation. It also does not work well.
Therefore, the envelope curves were manually determined. A quite accurate curve
can be obtained by hand in the weak absorption region as can be seen in Figure 3.6.

For the second question, in theory, the envelope method is valid as long as the
sample meets the assumptions discussed in section 3.2.2. However, even though
these assumptions may be met at the medium absorption region, the envelope
curves are not easy to be accurately determined. This can be understood by the
very steep drop in the transmittance occurring in a small wavelength range. Thus a
small error in the determination of the envelope curves can result in a significant
error in the refractive index. In short, the envelope method is good in the weak
absorption region (\lambda > 450 nm for the given example), is questionable in the
medium absorption region (450 nm > \lambda > 350 nm), and is invalid in the strong
absorption region (\lambda < 350 nm).

In the strong absorption region, both the refractive index and extinction
coefficient of the film region can be calculated from the transmission and reflection
spectra. The reflection spectrum of Pb(Zro.6Ti0.4)O3 film on sapphire is shown in
Figure 3.7. The solid curve is the reflectance of the sample without black paint on
the back surface of the substrate, while the dashed curve is that with black paint on
Figure 3.7 The reflection spectra of Pb(Zr_{0.6}Ti_{0.4})O_3 film on sapphire in the wavelength range of 300 nm to 2000 nm. The dashed curve is the spectrum with the black paint on the back surface of the substrate.
the back surface of the substrate. The reflectance of the sample with black paint shows lower values than that without black paint because the black paint eliminates most of the reflection from the back surface of the substrate. One very interesting observation is that these two reflection spectra merge together at the strong absorption region, as shown in Figure 3.8. This means that almost no light can reach the back surface to be eliminated by the black paint. In other words, the incident light is either reflected or absorbed by the film. In addition, it can be clearly seen that the interference effect starts at the point where the two reflection spectra merge together. The interference fringes of the reflection spectrum show the opposite behavior as those in the transmission spectrum. That is, the maxima of the interference fringes in the reflection spectrum are the minima in the transmission spectrum, as shown in Figure 3.9 for the case of Pb(Zr_{0.6}Ti_{0.4})O_3 film. The reflection spectrum in Figure 3.9 was measured without the black paint on the back surface of the substrate. The top curve in Figure 3.9 is the sum of the transmittance and the reflectance which indicates how much light intensity was absorbed and/or scattered by the sample. The reflection and the transmission spectra for the rest of the compositions are shown in Figures B.1 – B.6 in Appendix B.

Figure 3.10 shows the refractive index of Pb(Zr_{0.6}Ti_{0.4})O_3 film as a function of wavelength. For the rest of the compositions, the refractive indices as a function of wavelength are shown in Figures B.7 – B.12. The open circles are data calculated from the envelope method and the filled circles are data calculated from equation 3.39.

As can be seen in Figure 3.10, the refractive index has a value of 2.16 in the near infrared region, and gradually increases to a value of 2.42 at a wavelength
Figure 3.8  The reflection spectra of Pb(Zr$_{0.6}$Ti$_{0.4}$)O$_3$ film on sapphire in the wavelength range of 300 nm to 2000 nm. The dashed curve is the spectrum with the black paint on the back surface of the substrate.
Figure 3.9  The reflectance, transmittance, and their sum of the Pb(Zr$_{0.6}$Ti$_{0.4}$)O$_3$ film on sapphire in the wavelength range of 300 nm to 2000 nm. The reflection spectrum was measured without the back paint on the back surface of the substrate.
Figure 3.10 The refractive index as a function of wavelength and the dispersion curve of Pb(Zr$_{0.6}$Ti$_{0.4}$)O$_3$ film.
around 450 nm; it then rises abruptly in the ultraviolet region to a value of 3.15 at 340 nm and finally flattens out at a wavelength of 300 nm with a value of 3.2. In addition, the data obtained from the envelope method at a wavelength range from 400 nm to 2000 nm "relate" very well with those from the reflectance measurement at a wavelength range from 300 nm to 340 nm. The "gap" between 340 nm and 400 nm can be interpolated by a dispersion relation which will be discussed later.

Since most refractive index data were presented at $\lambda = 632.8$ nm which is the wavelength of a He–Ne laser, a summary of the refractive index at this wavelength for the entire PZT solid solutions is given in Figure 3.11. The refractive index of the film decreases linearly for an increase in $x$, i.e. with increasing zirconium content. For example, PbTiO$_3$ ($x = 0.0$) has an $n$ value of 2.481, whereas PbZrO$_3$ ($x = 1.0$) shows an $n$ value of 2.125. Compared to the refractive indices of the bulk materials [54], which are 2.668 for PbTiO$_3$ and 2.420 for PbZrO$_3$, the films showing lower indices were possibly due to the porosity and/or the stress in the films [55].

If the lower indices are only due to the porosity in the films, the packing densities of the films can be calculated by using the effective medium approximation as discussed in section 3.2.4. Table 3.4 summaries the packing densities of Pb(ZrxTi$_{1-x}$)O$_3$ films made by MOD in this study. The packing densities display a higher value for the titanium–rich side, while a lower value for the PbZrO$_3$ film. This may be due to the fact that the completion temperature of the perovskite phase for the titanium–rich side is much lower than that for the zirconium–rich side. The structure development of MOD PZT films will be discussed in detail in Chapter 4.

Coming back to Figure 3.10, the refractive index data as a function of wavelength can be fitted to a Sellmeier type dispersion relation [44]. For pure
Figure 3.11 Variation of the refractive index at $\lambda = 632.8$ nm with $x$ value in Pb($Zr_xTi_{1-x}$)O$_3$ films. Filled circles and the dashed line are data from reference 54.
### Table 3.4 Packing density of MOD Pb(Zr$_x$Ti$_{1-x}$)O$_3$ thin films

<table>
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<th>Composition, $x$</th>
<th>0.0</th>
<th>0.2</th>
<th>0.4</th>
<th>0.5</th>
<th>0.6</th>
<th>0.8</th>
<th>1.0</th>
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<td>.871</td>
<td>.847</td>
<td>.844</td>
<td>.849</td>
<td>.796</td>
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</tbody>
</table>
substances, the wavelength dependence of the optical constants may be described by the classical treatment of Lorentz. This theory assumes that the solid is composed of a series of independent oscillators, which are set into forced vibrations by the incident radiation. For both insulating and semiconducting materials, the well-known Sellmeier type equation, neglecting absorption, follows [44]

\[ n^2 = 1 + \frac{A \lambda^2}{(\lambda^2 - B)} \]  

(3.42)

where A and B are constants to be determined and \( \lambda \) is the wavelength in \( \mu m \).

By fitting the refractive index data (Figure 3.10) to equation 3.42, the dispersion relation constants were found to be 3.5811 for A and 0.0573 for B. As can be seen in Figure 3.10, the dispersion curve fits very well to the experimental data for wavelengths longer than 450 nm. The first two data points (at a wavelength around 400 nm) obtained from the envelope method deviate considerably from the dispersion curve because of the large error of the envelope method in this region. On the other hand, the dispersion curve also has its wavelength limit. This can be understood from the fact that the experimental data "flattens" out at 300 nm, while the dispersion curve continuously increases. It is also clear that if \( \lambda^2 = 0.0573 \) or \( \lambda = 0.240 \mu m = 240 \) nm, the \( n \) value is infinite.

Combining these two sets of experimental data and the curve fitting result, it is concluded that the dispersion curve is valid from 350 nm to 2000 nm.

As discussed earlier, if the reduction in the index of the film from its bulk value is only due to porosity in the film and if the effective medium approximation is valid in the wavelength range of this study, the indices of the films can be "adjusted" to those of the bulk materials for the study of the dispersion relations of
the bulk materials. For example, for PbTiO$_3$, the $n$ value at $\lambda = 632.8$ nm is 2.668 for the bulk material and 2.481 for the film. Therefore, 0.187 is added to the indices of the film in the wavelength range studied to find the indices of the corresponding bulk materials. By applying equation 3.42 to the adjusted data, the fitting constants were 5.3617 for the A and 0.0527 for the B, as shown in Figure 3.12. Singh et al [56] also studied the dispersion relation of the single crystal PbTiO$_3$ by using the same Sellmeier-type equation. They reported a value of 5.3636 for the A and 0.05027 for the B. The fitting results of the original refractive indices and the adjusted refractive indices are listed in Table 3.5. As can be seen in Table 3.5, the A values decreased linearly from 4.4556 for PbTiO$_3$ to 2.9500 for PbZrO$_3$ for the MOD films of this study and from 5.3617 for PbTiO$_3$ to 4.2033 for PbZrO$_3$ for the "bulk" materials. For the B values, they were in the range from 0.05011 to 0.06070, which correspond to the wavelengths 0.224 and 0.246 $\mu$m, respectively, and were independent of the composition. The figures for the rest of compositions which are not presented in this chapter are collected in Appendix B (Figures B.13 – B.18).

One of the most direct applications of the interference fringes of the transmission spectrum is the estimation of the film thickness. If the refractive indices at two adjacent maxima (or minima) are known, the film thickness can be determined using equation 3.23. The wavelength at each peak and valley of the interference fringes, corresponding $n$ values which were calculated from the envelope method, and the thickness calculated from each pair of peaks or valleys are listed in Table 3.6 for all PZT compositions in this study. The average thickness $d^\tau$ can now be used, along with $n$, to calculate the order number $m^\tau$ for the different extremes using equation 3.18. As can be seen in Table 3.6, the values of $m^\tau$ are not exact integers or half integers. The accuracy in thickness can now be significantly
Figure 3.12  Adjusted refractive index as a function of wavelength and the dispersion curve of PbTiO$_3$ film.
Table 3.5 Constants of the dispersion relations for Pb(ZrₓTi₁₋ₓ)O₃ thin films. The dispersion relation is written as $n^2 = 1 + A \lambda^2 / (\lambda^2 - B)$, where $\lambda$ is in $\mu$m.

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<th>For the adjusted data†</th>
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†The original refractive indices were adjusted to those of the bulk materials according to the effective medium approximation.
Table 3.6 Film thickness calculation of Pb(Zr\(_x\)Ti\(_{1-x}\))O\(_3\) thin films by envelope method and equation 2nd = m\(\lambda\). Both of \(\lambda\) and \(d\) are in nm.

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<th>(d)</th>
<th>(\bar{d})</th>
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<th>(m')</th>
<th>(m'')</th>
<th>(d)</th>
<th>(\bar{d})</th>
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<td></td>
<td></td>
</tr>
<tr>
<td>1362 (p)</td>
<td>2.009</td>
<td>313</td>
<td>0.92</td>
<td>1</td>
<td>339</td>
<td>331</td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>426 (v)</td>
<td>2.332</td>
<td>293</td>
<td>3.42</td>
<td>3.5</td>
<td>320</td>
<td></td>
<td></td>
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<tr>
<td>571 (v)</td>
<td>2.152</td>
<td>323</td>
<td>2.36</td>
<td>2.5</td>
<td>332</td>
<td></td>
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<tr>
<td>922 (v)</td>
<td>2.047</td>
<td></td>
<td>1.39</td>
<td>1.5</td>
<td>338</td>
<td></td>
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<td></td>
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</tr>
</tbody>
</table>

p = wavelength at peak position of interference fringes
v = wavelength at valley position of interference fringes
increased by rounding the value of m to the nearest exact integer or half integer value of m associated with each extreme point and deriving a new thickness d from equation 3.18. For example, the standard deviation for d' was found to be 17 nm which corresponds to an error of 6.5%, whereas that of d was 4.8 nm which corresponds to an error of 1.8% for the film with composition x = 0.2.

The thicknesses of the films derived from the above method are 267, 271, 277, 296, 290, 296, and 331 nm corresponding to the compositions of x = 0.0, 0.2, 0.4, 0.5, 0.6, 0.8, and 1.0, respectively. These thickness values were used to calculate the extinction coefficients of PZT films as a function of wavelength using equations 3.16 and 3.21, as shown in Figure 3.13 for Pb(Zr0.6Ti0.4)O3 and Figures B.19 — B.24 for the rest of the compositions. In order to reveal these values in the visible and the near infrared region, the ordinate was broken into two different scales. The extinction coefficients of MOD PZT films were in the range of 10^{-2} to 10^{-3}, in the visible and the infrared region, which are one order of magnitude higher than that of MOCVD PZT films (the optical properties of MOCVD PZT films will be discussed in Chapter 5). These higher values may be due to the scattering of the incident light from the sample surface.

An alternative but more tedious method, in which the film thickness is simulated from the the optical constants obtained from the envelope method, was used to cross check the validity of the above thickness calculation method. This thickness simulation method is considered to be more accurate than the envelope method because the only assumptions for this method are that the film is homogeneous and the thickness of the film is uniform. In addition, this simulation process has only one unknown, namely, film thickness, that needs to be determined. The simulation process is as follows:
Figure 3.13 The extinction coefficient as a function of wavelength of Pb(Zr$_{0.5}$Ti$_{0.5}$)$_3$O$_3$ film in the wavelength range of 300 nm to 2000 nm.
(1) use the known optical constants \((n \text{ and } k)\) of the film

(2) give an initial guess of the film thickness

(3) use equations 3.9 and 3.30 to calculate the transmission spectrum and compare to the experimental transmission spectrum which will generate a fitting error, \(\chi^2\), defined as

\[
\chi^2 = \frac{1}{n} \sum_{i=1}^{n} (T_i^c - T_i^e)^2
\]

where \(n\) is the number of data points, \(T_i^c\) is the calculated transmittance, and \(T_i^e\) is the experimental transmittance.

(4) add a small increment of thickness (0.1 nm in the present study) and continue step (3) until the smallest \(\chi^2\) is met.

Figure 3.14 shows the fitting result of the \(\text{Pb(}Zr_{0.6}Ti_{0.4}\text{)}O_3\) film whose \(n\) and \(k\) values were shown in Figures 3.10 and 3.13, respectively. The fitted thickness is 295 nm which is in reasonable agreement with the result of 290 nm obtained from the envelope method. As can be seen in Figure 3.14, the simulated curve fits well to the experimental data in the visible, near infrared, and near the absorption edge range. However, a considerable deviation was found in the neighborhood of wavelength around 400 nm. As discussed earlier, the refractive indices at around wavelength 400 nm also deviate from the dispersion curve. The fitting results along with the results obtained from the envelope method are listed in Table 3.7 for the entire PZT solid solutions. The figures for the rest of compositions are presented in Appendix B as Figures B.25 – B.30.

3.6 Absorption Coefficients at Near Band Gap
Figure 3.14 The experimental and simulated transmission spectra of Pb(Zr$_{0.6}$Ti$_{0.4}$)O$_3$ film.
Table 3.7 Comparison of the film thickness of Pb(ZrxTi1-x)O3 thin films obtained from the envelope method with that from the simulation. The optical constants obtained from envelope method were used for film thickness simulation. The wavelength range of simulation is from 450 nm to 2000 nm. The least square fit error \( \chi^2 \) is defined in equation 3.43.

<table>
<thead>
<tr>
<th>Composition, x</th>
<th>0.0</th>
<th>0.2</th>
<th>0.4</th>
<th>0.5</th>
<th>0.6</th>
<th>0.8</th>
<th>1.0</th>
</tr>
</thead>
<tbody>
<tr>
<td>Thickness, t (nm)</td>
<td>267</td>
<td>271</td>
<td>277</td>
<td>296</td>
<td>290</td>
<td>296</td>
<td>331</td>
</tr>
</tbody>
</table>

(Envelope Method)

| Thickness, t (nm) | 268 | 272 | 280 | 300 | 295 | 301 | 331 |

(Simulated)

| \( \chi^2 (10^{-2}) \) | 7.96 | 3.22 | 2.71 | 2.62 | 6.21 | 11.8 | 24.6 |

(Least square error)
Since the envelope method is invalid in the strong absorption region, the calculation of the absorption coefficients of the film needs both the transmission and reflection spectra. Figure 3.15 shows the absorption coefficients, calculated using equation 3.40, as a function of incident photon energy for the entire PZT solid solution range. As can be seen in Figure 3.15, at a given photon energy of the incident light, the absorption coefficient decreased with increasing zirconium content of the PZT film. The photon energy of the incident light as a function of composition is shown in Figure 3.16 at three different absorption coefficients, namely, $\alpha = 1.5 \times 10^5, 1 \times 10^5, \text{and } 5 \times 10^4 \text{ cm}^{-1}$. For a given $\alpha$, the photon energy increased with increasing zirconium content of the PZT film. For example, for $\alpha = 1.5 \times 10^5 \text{ cm}^{-1}$, the value of the photo energy for PbTiO$_3$ was 3.7 eV, whereas PbZrO$_3$ had a value of 4.3 eV. In addition, these three curves were approximately parallel. Zametin [57] reported the band gap energies ($E_g$) for bulk PbTiO$_3$ and PbZrO$_3$ ceramics as 3.6 eV and 3.93 eV, respectively. The reported values ($E_g$) are very close to the present values which were 3.59 eV and 3.88 eV for $\alpha = 1 \times 10^5 \text{ cm}^{-1}$ for PbTiO$_3$ and PbZrO$_3$, respectively. The $E_g$ values for PZT ceramics have not been reported to the best of my knowledge.

3.7 Surface Morphology

The SEM micrographs of the surface morphology of MOD PZT films are shown in Figure 3.17. The surface morphologies of the films at the zirconium–rich side are very different from those of the films at the titanium–rich side. Very large (diameters ranging from 5 $\mu$m to 35 $\mu$m) spheroidal grains with very fine grains occupying the space between the large grains were seen for the films at the
Figure 3.15 The absorption coefficients as a function of incident photon energy in the near band gap region for Pb(Zr$_x$Ti$_{1-x}$)O$_3$. 
Figure 3.16 The incident photon energy as a function of composition at three different absorption coefficients.
Figure 3.17 SEM micrographs of the surface morphology of MOD Pb(ZrxTi1-x)O3 films. The samples were annealed at 650°C for 1 hour.
zirconium–rich side. These very large grains are believed to be the pure perovskite phase, while the fine grains may be the residual pyrochlore phase [39,58]. On the other hand, the grains of the films at the titanium–rich side were well developed with the sizes ranging from 0.1 to 2 μm. The surface morphology and the average grain size of the films with x = 0.0 and 0.2 are very similar to those from the sputtering [59] and MOCVD [38] PZT films. The average grain size increased with increasing zirconium content in the film, as can be seen in Figure 3.18.

This observation of the microstructure dependence on the composition of the PZT film may indicate that the nucleation barrier for the film at the titanium–rich side is lower than that at the zirconium–rich side.

3.8 Summary

The optical properties (the refractive index, the extinction coefficient, and the absorption coefficient near the band gap) and the thickness of the PZT thin films were studied. The envelope method, accompanied with the consideration of the light intensity loss from the back surface of the substrate, was shown to be a simple and convenient tool for obtaining the optical properties and the film thickness of the PZT films by using the transmission spectra alone in the medium and weak absorption regions. In the near optical band gap region, both the transmission and the reflection spectra were used to successfully calculate the optical constants of the films. The film thickness derived from the envelope method was cross checked by a computer simulation method. In addition, the refractive indices were fitted to a simple Sellmeier type equation for determining the dispersion constants for both porous PZT films and bulk PZT materials. The valid wavelength range of these
Figure 3.18  Average grain size of Pb(\(Zr_xTi_{1-x}\))O\(_3\) films as a function of composition.

The samples were annealed at 650°C for 1 hour.
dispersion relations was from 350 nm to 2000 nm. A flow chart for the entire calculation procedure for this study is illustrated in Figure 3.19.
In Medium and Weak Absorption Regions

- Measure transmission spectrum

Obtain \(T_{\text{max}}\) and \(T_{\text{min}}\) from transmission spectrum

- Calculate \(n\) using equ. 3.22 & 3.33

- Calculate \(d\) using equ. 3.18 & 3.23

- Calculate \(k\) using equ. 3.16 & 3.21

In Strong Absorption Region

- Measure both transmission and reflection spectrum

- Calculate \(n\) using equ. 3.39

- Calculate absorption coefficient using equ. 3.40

Figure 3.19 A flow chart for calculation the optical constants and the film thickness of a single layer film on a transparent substrate.
Chapter 4 Structure Development Study of PZT Thin Films by an Optical Method

4.1 Introduction

Reaction mechanisms of PZT bulk materials, prepared by sintering the mixed oxide powders, have been extensively studied [60–63]. PbTiO$_3$ forms first from the PbO–ZrO$_2$–TiO$_2$ system in the temperature range of 450°C to 600°C [63]. Single phase PZT was observed at temperatures around 785°C but no PbZrO$_3$ phase was observed [62]. Therefore, Chandratrey et al [62] concluded that PbTiO$_3$ was formed at lower temperatures which subsequently reacted with ZrO$_2$ to form PZT bulk material. However, in the case of sputtered PZT thin films, amorphous PZT phase was reported to transform to a metastable pyrochlore phase at temperatures as low as 350°C and finally formed the perovskite phase at temperatures higher than 500°C [64]. It was anticipated that the results of the phase transformation study for PZT bulk materials would be very different from those for the PZT thin films. The difference may be due mainly to the short diffusion distance in the thin films compared to that of the bulk materials.

For a typical MOD process, an amorphous PZT phase is observed at temperatures around 300°C. As the annealing temperature is increased, the films transform from the amorphous phase to the pyrochlore phase and then finally to the
perovskite phase [65]. The pyrochlore phase has the chemical formula $A_2B_2O_6$ and has a cubic structure. However, the perovskite phase has the chemical formula $ABO_3$ and can exhibit tetragonal, rhombohedral, or orthorhombic structure depending on the Zr/Ti ratio. Both the amorphous phase and the pyrochlore phase do not display ferroelectric properties. In order to obtain the useful perovskite phase, most often, annealing temperatures above 550°C are required, again, depending on the Zr/Ti ratio.

Several device applications require processes which form the perovskite phase at low temperatures. Understanding the various aspects of structure development in MOD PZT films is the key for developing such low temperature processes. A nondestructive optical method for characterizing the various phase transformations in MOD PZT films is proposed. The effectiveness of this technique (1) in identifying various characteristic temperatures will be shown and (2) the kinetics of phase transformations in PZT films will be studied.

Even though the composition of the amorphous, pyrochlore and perovskite phase may be similar [58], they are expected to have different refractive indices since they have different structures. Therefore, by following the refractive index of the film as a function of annealing temperature one can obtain information on structure development. By noting the changes in the refractive index, the initiation and completion temperatures of a new phase from the existing one can be identified. In addition, by using the effective medium approximation (section 3.2.4), the concentration of each phase as a function of time or temperature (i.e., phase transformation kinetics) can also be obtained.

The sample preparations and the transmission spectrum measurements have been described in Chapter 2.
4.2 Models of Structure Development of PZT Thin Films

The structure development of MOD PZT films from the initial as-deposited state to the final perovskite phase involves phase transformations of four different phases, namely, metalorganic compounds (MO), the amorphous phase (A), the pyrochlore PZT phase (Py), and the perovskite PZT phase (Pe). There are many possible ways for the initial metalorganic compounds to transform into the final perovskite phase through the amorphous and the pyrochlore phases. Two extreme cases are presented in Figures 4.1 and 4.2 to illustrate the complexity of the structure development in MOD PZT films involving these four different phases. The simplest case which will be referred to as model A hereafter is shown in Figure 4.1, while the most complicated case which will be referred to as model B hereafter is presented in Figure 4.2. Also, one example of the possible cases which are in between the model A and model B is given in Figure 4.3 and this case will be referred to as model C.

In model A, the film is assumed to have four single phase regions at four certain annealing temperature intervals and three two phases mixtures in between. In other words, no more than two phases can exist at any temperature. After the solvent removal, the film can be represented by one or a mixture of metalorganic compounds. As the temperature is increased at $T_1^A$, the amorphous PZT phase is formed. At the temperature $T_c^A$ the MO is completely converted into amorphous phase. In other words, the formation of amorphous phase is completed at $T_c^A$. Similarly, $T_1^P_y$ and $T_1^P_e$ represent, respectively, the temperatures at which the pyrochlore and the perovskite formation is initiated. Likewise, $T_c^P_y$ and $T_c^P_e$ are the temperature at which the formation of pyrochlore and perovskite is completed.
Figure 4.1 Model A: the simplest hypothetical model for the structure development in MOD PZT thin films.
Figure 4.2 Model B: the most complicated hypothetical model for the structure development in MOD PZT thin films.
Figure 4.3 Model C: an example of the hypothetical models between model A and model B for the structure development in MOD PZT thin film.
respectively.

According to this simple model, two phase mixtures of MO/A, A/Py, and Py/Pe are presented in the temperature intervals $T_1^A$ to $T_c^A$, $T_1^Py$ to $T_c^Py$, and $T_1^Pe$ to $T_c^Pe$, respectively. In other words, it should be possible to identify these six characteristic temperatures. In this simple model, not only can the characteristic temperatures be identified, but also information on the phase transformation kinetics of each two phase mixture can be obtained.

For model B, a maximum of four phases can exist in a certain temperature range. Similar to the early development stage of model A, the film is represented by a mixture of metalorganic compounds after the solvent removal and the amorphous phase is formed as the temperature is increased at $T_1^A$. However, unlike model A, before the metalorganic compounds are completely converted into the amorphous phase, the pyrochlore phase has started forming at temperature $T_1^Py$. In other words, it is not possible to define the $T_c^A$. Similarly, the perovskite phase is initiated at the temperature $T_1^Pe$ before the metalorganic compounds are completely decomposed. As the temperature is increased, the metalorganic compounds and the amorphous phase completely disappear at temperatures $T_1$ and $T_2$, respectively. The temperatures $T_1$ and $T_2$ are used only for the purpose of convenience and have no meaningful definitions. Finally, the perovskite phase is completely formed at the temperature $T_c^Pe$.

Based on model B, only two single phases, i.e. metalorganic compounds and perovskite phase, can exist in a certain temperature interval during the whole structure developments. Two phase mixtures of MO/A and Py/Pe are present in the temperature intervals $T_1^A$ to $T_1^Py$ and $T_2$ to $T_c^Pe$, respectively. Three phase mixtures of MO/A/Py and A/Py/Pe are present in the temperature intervals $T_1^Py$
to $T_1^{Pe}$ and $T_1$ to $T_2$, respectively, and a four phase mixture of MO/A/Py/Pe is present in the temperature interval $T_1^{Pe}$ to $T_1$.

For model C, as shown in Figure 4.3, the pyrochlore phase can exist in a certain temperature range, while the amorphous phase cannot. In this example, the pyrochlore phase has started forming before the metalorganic compounds are completely transformed to the amorphous phase. In other words, as can be seen in Figure 4.3, the entire phase transformation route is a combination of the first three steps of the model B and the last four steps of the model A.

4.3 Structure Development in MOD PZT Thin Films

4.3.1 X-ray Diffraction Study

As mentioned in the previous section, the structure development of MOD PZT thin films involves four different phases. Among these four phases, the pyrochlore phase and the perovskite phase are the crystalline phases. Therefore, the temperatures at which the perovskite phase is initiated ($T_1^{Pe}$) and completed ($T_c^{Pe}$) can be determined by an x-ray diffraction study.

Figure 4.4 shows the selected XRD patterns of the Pb(Zr$_{0.5}$Ti$_{0.5}$)O$_3$ thin film in the temperature range from 460°C to 620°C. The major XRD peaks of pyrochlore (222) and perovskite (111) are at $2\theta = 29.5^0$ and $31^0$, respectively. As can be seen in Figure 4.4, the $T_1^{Pe}$ can be determined in the temperature range from 520°C to 540°C, whereas the $T_c^{Pe}$ is in the temperature range from 600°C to 620°C. The $T_1^{Pe}$s and $T_c^{Pe}$s of the entire PZT solid solution are summarized in Figure 4.5. Both $T_1^{Pe}$ and $T_c^{Pe}$ increase with increasing Zr concentration in the film. For
Figure 4.4 XRD patterns of the MOD Pb(Zr$_{0.5}$Ti$_{0.5}$)O$_3$ film for the annealing temperatures ranging from 460°C to 620°C for 30 min at each temperature.
Figure 4.5 Initiation and completion temperature of the perovskite phase as a function of composition in the Pb(Zr$_x$Ti$_{1-x}$)O$_3$ films.
example, the temperatures where the formation of the perovskite phase is completed are around 460°C and 650°C for PbTiO$_3$ and PbZrO$_3$, respectively. In addition, the higher the Zr concentration, the wider the phase transformation temperature range, as can be seen in Figure 4.5. In other words, the pyrochlore–perovskite transformation is initiated at lower temperature and completed faster for the films on the titanium rich side than those on the zirconium rich side.

4.3.2 Optical Method

The optical properties and thickness of the films were derived by using the envelope method as described in Chapter 3 from the transmission spectra only. For the structure development study, only the envelope values ($T_{\text{max}}$ and $T_{\text{min}}$) at extremes and $\lambda = 632.8$ nm were used.

The refractive index (at $\lambda = 632.8$ nm) and film thickness as a function of annealing temperature for MOD Pb(Zr$_x$Ti$_{1-x}$)O$_3$ films across the entire solid solution, i.e., from $x = 0.0$ to $x = 1.0$, are shown in Figures 4.6 - 4.12. The refractive indices are represented as open circles, while the thickness values are the filled circles. Based on the shape of the refractive index curve, these PZT films are classified into two groups: (1) $x = 0.0$ and 0.2 and (2) $x = 0.4$ - 1.0.

At a first glance (Figures 4.6 and 4.7), the refractive indices of the first group have the lowest value of 2.04 for PbTiO$_3$ and 2.08 for Pb(Zr$_{0.2}$Ti$_{0.8}$)O$_3$ in the temperature range from 150°C to 250°C, the highest value of 2.29 for PbTiO$_3$ and 2.47 for Pb(Zr$_{0.2}$Ti$_{0.8}$)O$_3$ in the temperature range from around 520°C to 700°C, and intermediate values at temperatures between these two ranges. For the second group, the refractive index curves behave much different than those in the first
Figure 4.6 Refractive index (at \( \lambda = 632.8 \text{ nm} \)) and film thickness as a function of annealing temperature for MOD PbTiO\(_3\) film.
Figure 4.7 Refractive index (at $\lambda = 632.8$ nm) and film thickness as a function of annealing temperature for MOD Pb(Zr$_{0.2}$Ti$_{0.8}$)O$_3$ film.
Figure 4.8 Refractive index (at $\lambda = 632.8$ nm) and film thickness as a function of annealing temperature for MOD Pb(Zr$_{0.4}$Ti$_{0.6}$)O$_3$ film.
Figure 4.9 Refractive index (at $\lambda = 632.8$ nm) and film thickness as a function of annealing temperature for MOD Pb(Zr$_{0.5}$Ti$_{0.5}$)O$_3$ film.
Figure 4.10 Refractive index (at $\lambda = 632.8$ nm) and film thickness as a function of annealing temperature for MOD Pb(Zr$_{0.6}$Ti$_{0.4}$)O$_3$ film.
Figure 4.11 Refractive index (at $\lambda = 632.8$ nm) and film thickness as a function of annealing temperature for MOD Pb(Zr$_{0.8}$Ti$_{0.2}$)O$_3$ film.
Figure 4.12 Refractive index (at $\lambda = 632.8$ nm) and film thickness as a function of annealing temperature for MOD PbZrO$_3$ film.
As can be seen in Figures 4.8 – 4.12, the refractive index curves display a "flat top", which is not shown in the first group, at temperatures around 500°C. The "flat tops" are not quite flat. This may be due to an increase in the packing density of the film as the temperature is increased which causes an increase in the refractive index according to the effective medium approximation (EMA).

For the convenience of discussion, start from the group 2 and take the case of Pb(Zr₀.₄Ti₀.₆)O₃ as an example. As can be seen from Figure 4.8, the refractive index curve can be divided into five regions in terms of temperature range, i.e.,

1. from 150°C to 250°C: the indices have a minimum and constant value of 2.06
2. from 250°C to 480°C: the indices increase to a maximum value of 2.39 at 480°C
3. from 480°C to 520°C: the indices show a "flat top"
4. from 520°C to 580°C: the indices drop steeply to a value of 2.25 at 580°C
5. from 580°C to 700°C: the indices increase slightly to a value of 2.29 at 700°C

From the results of the XRD study as discussed in section 4.3.1, it is known the perovskite phase is initiated at around 520°C and completed at the temperature range from 560°C to 580°C for the Pb(Zr₀.₄Ti₀.₆)O₃ thin film. In addition, Kwok [58] has observed a pure pyrochlore phase at a temperature around 500°C by XRD study. From the above observation, along with the XRD results, four characteristic temperatures can be easily picked, i.e., 250°C, 480°C, 520°C, 580°C; They are assigned to be \( T^A_1 \), \( T^F_P \), \( T^F_1 \), and \( T^F_T \), respectively. It should noted that the characteristic temperatures: \( T^A_1 \) and \( T^F_P \) cannot be easily identified from x-ray
diffraction studies because of the involvement of amorphous phase and due to the fine grain size of the pyrochlore phase. Among these four temperatures, $T_{c}^{P_{y}}, T_{1}^{P_{e}}$, and $T_{c}^{P_{e}}$ are most important. They are tabulated in Table 4.1. It is clear that the structure development in this example is not the case of either model A or model B.

Some fine structure in the refractive index curve in Figure 4.8 may be observed in the temperature range of 250°C to 480°C. In this temperature region, it is believed that the structure development involves the phase transformations of three different phases, namely, the metalorganic compounds, the amorphous phase, and the pyrochlore phase. The $n$ values increase as the temperature is increased with two break points at 340°C and 400°C. This may be interpreted as the decomposition of the metalorganic compounds occurring in the temperature range of 250°C to 400°C. An independent study [39] of the same precursor solution, by using thermal gravimetric analysis (TGA), showed that the PZT solution decomposed slowly in the temperature range from 200°C to 400°C which agrees well with the present observation. Therefore, the structure developments which occur in the group 2 PZT films are best represented by the proposed model C.

The variation of the film thickness with the annealing temperature for Pb(Zr$_{0.4}$Ti$_{0.6}$)O$_{3}$ is also shown in Figure 4.8. The thickness variation curve shows a less complicated feature than the refractive index curve. As expected, the thickness of the as-deposited film has the thickest value of 370 nm. The most noticeable change in thickness occurs in the temperature range from 380°C to 480°C. This indicates that a significant density change takes place in this temperature range. This large thickness change is believed to be due to the phase transformation of the amorphous material to the pyrochlore phase. As the temperature was increased up to 700°C, the thickness decreased slightly from a value of 290 nm at 480°C to a
Table 4.1 The values of $T_c^{Py}$, $T_i^{Pe}$, and $T_c^{Pe}$ determined by the optical method for MOD Pb(Zr$_x$Ti$_{1-x}$)O$_3$ thin films.

<table>
<thead>
<tr>
<th>x</th>
<th>0.0</th>
<th>0.2</th>
<th>0.4</th>
<th>0.5</th>
<th>0.6</th>
<th>0.8</th>
<th>1.0</th>
</tr>
</thead>
<tbody>
<tr>
<td>$T_c^{Py}$</td>
<td>—</td>
<td>—</td>
<td>480</td>
<td>460</td>
<td>480</td>
<td>460</td>
<td>460</td>
</tr>
<tr>
<td>$T_i^{Pe}$</td>
<td>—</td>
<td>—</td>
<td>520</td>
<td>520</td>
<td>540</td>
<td>540</td>
<td>540</td>
</tr>
<tr>
<td>$T_c^{Pe}$</td>
<td>—</td>
<td>—</td>
<td>580</td>
<td>600</td>
<td>620</td>
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</table>
value of 284 nm at 700°C.

Now, coming back to the MOD PZT films in group 1, recall the refractive index and film thickness as a function of annealing temperature shown in Figures 4.6 and 4.7. From the XRD results, notice that the formation of the perovskite phase is completed at a temperature around 460°C for the PbTiO₃ film as can be seen in Figure 4.5. In addition, it was found that the pyrochlore phase has a higher refractive index than the perovskite phase for the PZT materials. However, for both PbTiO₃ and Pb(Zr₀.₂Ti₀.₈)O₃ films, the refractive indices keep increasing as the temperature is increased up to a temperature around 520°C. This increase in refractive index above the perovskite completion temperatures may be interpreted as an effect of the densification of the film. On the other hand, no "flat top" was observed which characterizes the pyrochlore phase in the intermediate temperature range. With the help of the XRD results, the lack of a visible flat top may be due to the very narrow temperature range between $T_{i}^{P}$ and $T_{c}^{P}$ which are 430°C and 460°C, respectively, for the PbTiO₃ film. By comparing the above observation with the proposed models as described in section 4.2, it is believed that the structure development in the MOD PZT films of group 1 may be described by model B. In other words, a very complicated phase transformation involving a mixture of all four different phases takes place between the temperatures $T_{i}^{P}$ and $T_{c}^{P}$.

4.3.3 Pyrochlore–Perovskite Phase Transformation

Although the above proposed optical method is an indirect method for studying the structure development in MOD PZT films, one of the advantages of this method is that the refractive index values in the temperature range from $T_{i}^{P}$ to $T_{c}^{P}$ can
be used to calculate the volume fraction of the perovskite phase by using the effective medium approximation. However, to take this advantage, one has to be able to identify $T_{iP}$ and $T_{cP}$ from the refractive index curve. Therefore, only the films in group 2 can be used and their $T_{iP}$ and $T_{cP}$ have been listed in Table 4.1.

As mentioned in Chapter 3, the porosity also needs to be considered as a separate phase in the effective medium approximation. For a single phase region, porosity can be easily obtained by comparing the experimental value of the refractive index with that of the literature value of the bulk material. Porosity values of the single phases can be included in the analysis of the two–phase region. Due to the lack of literature data for the refractive index of the pyrochlore phase, we have assumed that the porosity in these films (1) remains unchanged in the temperature range from $T_{iP}$ to $T_{cP}$ and (2) is the same as that of the perovskite phase with the same composition.

The volume fraction of the perovskite phase was plotted as a function of temperature in Figure 4.13 for the PZT films with $x = 0.4 - 1.0$. If the sample were studied as a function of time at several temperatures, the phase transformation kinetics could have been obtained.

4.3.4 Surface Morphology

The SEM micrographs of the surface morphology are shown in Figure 4.14 for the films with $x = 0.0 - 1.0$. These SEM pictures were taken from the samples which had suffered through 23 heat treatments at an annealing temperature in the range from 150°C to 700°C for 30 min at each annealing temperature. The surface morphologies of these films were similar to those shown in Figure 3.17. That is,
Figure 4.13 The volume fraction of the perovskite phase as a function of annealing temperature in MOD Pb(Zr$_x$Ti$_{1-x}$)O$_3$ films, which was derived from the refractive index by using the effective medium approximation.
Figure 4.14 SEM micrographs of the surface morphology of MOD Pb(ZrxTi1-x)O3 films which had suffered through 23 heat treatments in the temperature range from 150°C to 700°C for 30 min at each annealing temperature.
large spheroidal grains with average sizes ranging from 7 to 15 \( \mu \text{m} \) were found for the samples at the zirconium–rich side, while fine grains with average sizes ranging from 0.3 to 2 \( \mu \text{m} \) were noted for those at the titanium–rich side. The average grain size is plotted as a function of the \( x \) value in Figure 4.15. As can be seen, the grains were larger than those shown in Figure 3.17 with the exception of the sample with \( x = 1.0 \).

4.4 Summary

Models for the structure development in MOD PZT films have been proposed and have been successfully used to interpret the experimental observations. Also, an effective, versatile, nondestructive optical method was developed for the study of the structure development in MOD PZT films. Using this method, the characteristic temperatures at which perovskite phase formation is initiated and completed were identified for the composition from \( x = 0.4 \) to 1.0. In addition, the volume fraction of each phase in a two–phase mixture can be obtained. This optical method is more effective than conventional nondestructive techniques such as x–ray diffraction in studying the pyrochlore to perovskite phase transformation in PZT films. The proposed models and this optical method could be applied to other thin film systems prepared by MOD or sol–gel techniques.
Figure 4.15  Average grain size of the Pb(ZrxTi1-x)O3 films as a function of composition. The samples had suffered through 23 heat treatments in the temperature range from 150°C to 700°C for 30 min at each annealing temperature.
Chapter 5 Metalorganic Chemical Vapor Deposition of PZT Thin Films

5.1 Introduction

Chemical vapor deposition (CVD) is a material synthesis method in which the constituents of a gaseous phase chemically react to form a condensed coating on a substrate. Thus the CVD process for depositing thin films contains four basic sequential steps:

1. generation of precursor vapors
2. transportation of precursor vapors from precursor container to reaction chamber
3. reaction of precursor vapors and producing a solid film on a substrate
4. exhausting of by-products and unused precursor

In the first step, the precursor is sealed in a container, conventionally called a bubbler, and is usually thermally evaporated to generate enough vapors. If the precursors are metalorganic compounds, the CVD process is called metalorganic CVD (MOCVD).

In the second step, the precursor vapors are transported into the reaction chamber which contains the specimens to be coated, vapors are transported by the flow of a foreign gas (carrier gas) or by a vacuum or both. If a vacuum pump is
used, the CVD process is called low pressure CVD (LPCVD). On the other hand, if the entire process is performed under atmospheric pressure, the CVD process is called atmosphere pressure CVD (APCVD). During the transporting process, a pre-mixing chamber may be needed for multiple precursors, and the transporting paths need to be kept at a temperature higher than the precursor evaporation temperature but lower than the precursor decomposition temperature.

The third step is the most complicated process which involves many fundamental aspects including thermodynamics, chemical reaction processes and kinetics, nucleation and growth modes, and transport phenomena [66]. Many methods have been used to decompose and activate the precursor vapors including thermal energy, photon energy (ultraviolet light or laser), and electric or magnetic energy. If the thermal energy is used and only the substrate is heated, it is called cold-wall CVD. On the other hand, if the substrate is placed in a hot chamber, it is called hot-wall CVD. For the case of using photon energy, it is called photo-CVD or laser assisted CVD (LACVD). In the plasma assisted CVD (PACVD) process, electric or magnetic energy is used to generate the plasma of the precursor.

Finally, the by-products and unused precursor need to be exhausted and disposed of safely.

It is clear from the above brief discussion, that the complexity of the CVD process cannot be overaddressed. From the technical point of view, it requires the precise control and feedback equipment for mass flow, temperature, and pressure. From the scientific point of view, it involves the understandings of precursor chemistry, reactor modeling and design, thermodynamics, chemical reaction processes and kinetics, nucleation and growth, and transport phenomena.

At the time when this study began three years ago, there was no reported PZT
thin films deposited by MOCVD. During the past three years, five other research
groups sequentially published the results of MOCVD PZT films [33–37]. However,
the reported MOCVD PZT films were fabricated at relatively high temperatures (> 600°C) using cold wall type reactors. Cold–wall reactors are good for epitaxial films
because of less particle contamination. However, cold–wall reactors suffer from
their low throughput. In contrast, hot–wall reactors are conceptually simpler
because of the isothermal environment. In addition, they offer much higher
throughput than do cold–wall reactors. But hot–wall reactors suffer from particle
contaminations from the walls of the chamber. This may not be a severe problem
for polycrystalline films. Furthermore, low temperature deposition processes are
needed to integrate ferroelectrics into semiconductor processing.

A summary of the properties of the reported MOCVD PZT thin films is given
in Table 5.1. The results of this study are briefly included in Table 5.1 also for the
purpose of comparison. As can be seen in Table 5.1, [001] oriented PZT films were
obtained on (100) MgO and (100) Pt substrates by different investigators. The
average grain sizes of PZT films in this study were much smaller than others.
Electrical properties comparable to those of others were obtained. In addition, no
other group reported the optical properties of MOCVD PZT films. The detailed
discussion is in the sub–sections of section 5.4.

In this chapter, at first, because of the complexity of the CVD
multi–component oxides, the selection of precursors is very carefully discussed in
details in section 5.2. The hot–wall MOCVD apparatus and the deposition process
are described in section 5.3. Section 5.4 discusses the effect of the deposition
parameters on the film composition, the crystal structure and orientation study, the
surface morphology, the reproducibility, the optical properties, and the
<table>
<thead>
<tr>
<th>Group</th>
<th>Substrates</th>
<th>Crystal Orientation</th>
<th>Microstructure</th>
<th>Ave. G.S. (μm)</th>
<th>Electric Properties</th>
<th>Optical Properties</th>
</tr>
</thead>
<tbody>
<tr>
<td>a</td>
<td>Sapphire</td>
<td>Non-oriented*</td>
<td>Fine Grains</td>
<td>0.1*+</td>
<td>εᵣ=1000</td>
<td>n=2.413</td>
</tr>
<tr>
<td></td>
<td>Pt/Ti/SiO₂</td>
<td></td>
<td>Fine Grains</td>
<td>0.15</td>
<td>Pₛ=12.3μC/cm²</td>
<td>k=0.0008</td>
</tr>
<tr>
<td></td>
<td>RuOₓ/SiO₂</td>
<td>Fine Grains</td>
<td>Fine Grains</td>
<td>0.15</td>
<td>Eₛ=64.5kV/cm</td>
<td></td>
</tr>
<tr>
<td>b</td>
<td>(100)Si,(100)MgO</td>
<td>Completed</td>
<td>Tile structure</td>
<td>0.6(x=0)</td>
<td>εᵣ=100–500</td>
<td>—</td>
</tr>
<tr>
<td></td>
<td></td>
<td>[001]</td>
<td></td>
<td>2.0(x=.48)</td>
<td></td>
<td></td>
</tr>
<tr>
<td>c</td>
<td>(100)Pt/(100)MgO</td>
<td>Completed</td>
<td>Tile structure</td>
<td>1.0</td>
<td>εᵣ=200–350</td>
<td>—</td>
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<tr>
<td></td>
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<td>[001]</td>
<td></td>
<td></td>
<td>Pₛ=30–40 μC/cm²</td>
<td></td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td>Eₛ=40–65 kV/cm</td>
<td></td>
</tr>
<tr>
<td>d</td>
<td>(100)MgO</td>
<td>Completed</td>
<td>Fine Grains</td>
<td>0.8</td>
<td>—</td>
<td></td>
</tr>
<tr>
<td></td>
<td></td>
<td>[001]</td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>e</td>
<td>(100)Si,(111)Pt</td>
<td>Non-oriented</td>
<td>Fine Grains</td>
<td>0.5</td>
<td>εᵣ=1300–1700</td>
<td>—</td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td>Pₛ=18μC/cm²</td>
<td></td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td>Eₛ=55kV/cm</td>
<td></td>
</tr>
<tr>
<td>f</td>
<td>Pt/Ti/SiO₂</td>
<td>Highly Oriented</td>
<td>Fine Grains</td>
<td>0.5(x=0)</td>
<td>εᵣ=240–870</td>
<td>—</td>
</tr>
<tr>
<td></td>
<td></td>
<td>[001]</td>
<td></td>
<td>0.2(x=.57)</td>
<td>Pₛ=50–60 μC/cm²</td>
<td></td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td>Eₛ=75–170 kV/cm</td>
<td></td>
</tr>
</tbody>
</table>

a Virginia Tech, this study.
b Chubu University, Japan, Reference 33.
c Nippon Mining Co., Japan, Reference 34.
d Tokyo Institute of Technology, Japan, Reference 35.
e Mitsubishi Electric Co., Japan, Reference 36.
f Philips Research Laboratories, The Netherlands, Reference 37.
* Highly oriented [001] PZT films were occasionally obtained.
** The average grain size seemed to be independent of film thickness, composition, and substrate.
* Non-oriented PZT films were obtained when using TEL–ZIP–TIP system (see Table 5.7).
interrelationship of the composition uniformity and ferroelectric properties. PZT films were deposited using a cold-wall and a hot-wall reactor. The results of cold-wall MOCVD PZT films are demonstrated in section 5.5. Finally the conclusions are drawn in section 5.6.

5.2 Selection of Precursors

The selection of the precursors is the most critical step in CVD for successful depositions of complex oxide thin films. The first successful deposition of oxide-based ferroelectric thin films by CVD was reported by Nakagawa et al. in 1982 [67]. They deposited PbTiO$_3$ films on Pt-coated silicon wafers by using TiCl$_4$, PbCl$_2$, O$_2$, and H$_2$O as source materials. Several problems arose from their studies: (1) very high evaporation temperature (700°C) was required of PbCl$_2$, (2) poor ferroelectric properties ($P_r = 0.16 \mu$C/cm$^2$ and $E_c = 14.5$ kV/cm), (3) poor composition uniformity in the bulk of PbTiO$_3$ films, and (4) crystallographic imperfections due to water and/or chloride contamination. Obviously, chlorides are not ideal precursors for the CVD process. In general, metalorganic precursors have relatively high vapor pressures at lower temperatures. By carefully selecting the organic compounds, the undesirable contaminations in the films can be completely excluded. Metalorganic compounds are now used almost exclusively for the deposition of oxide thin films.

5.2.1 General Consideration

The ideal precursors for MOCVD have to meet the following requirements:
(1) High vapor pressure at low vaporization temperature.
(2) Low decomposition temperature.
(3) Large enough temperature "window" between vaporization and decomposition temperatures.
(4) No contaminations from the organic constituents of the precursors
(5) Stable under ambient conditions.
(6) Nontoxic.

It is one of the goals in this study to identify the ideal precursors for MOCVD PZT films.

Several types of metalorganic compounds have been commonly used as precursors to grow metal oxide thin films including metal alkyls, metal alkoxides, and metal $\beta$-diketonates. Metal alkyls have the general formula $M^{n+}R_n$ where $R=C_mH_{2m+1}$, metal alkoxides have the general formula $M^{n+}(OR)_n$, and metal $\beta$-diketonates have the general formula

![Metal $\beta$-diketonate](image)

Most of the metalorganic precursors have reasonable vapor pressures at relative low temperatures. Although metal alkoxides and metal $\beta$-diketonates tend to be less volatile than their alkyl equivalents, they are easier to handle and are much less toxic. One of the assets of metalorganic precursors is that their physical and chemical properties can be tailored by making small changes in their chemical
structure. For example, the volatility of a metal \( \beta \)-diketonate can be increased by varying the R-group on the chelating ring. In general, increased bulkiness of the R-group or increased fluorine substitution on the R-group increases volatility. This trend is demonstrated for lead \( \beta \)-diketonates in Table 5.2 [68]. The increased volatility is apparent with chelates of increased fluorination: \( \text{Pb(acac)}_2 < \text{Pb(tfa)}_2 < \text{Pb(hfa)}_2 \) and increased bulkiness: \( \text{Pb(acac)}_2 < \text{Pb(dhd)}_2 < \text{Pb(thd)}_2 \). Increasing the size of the ligand increases the metal chelate volatility by shielding the metal center from molecular interactions. Fluorination has the same effect because fluorine atoms are somewhat larger than the hydrogen atoms for which they substitute. The thermal and ambient stabilities of the metal \( \beta \)-diketonate are also sensitive to variation in the R-substituent and metal ion size. Effective shielding of the metal ion due to either small ion size or bulkiness of the ligand results in increased thermal and ambient stability. This effect can be explained in the same manner in which the increased volatility of the \( \beta \)-diketonate is explained. Increased shielding of the metal center renders the compound less prone to intermolecular reactions which form oligomers, and also less prone to reactions with water or oxygen to increase the coordination number.

In the case of metal alkoxides, their vapor pressures strongly depend on the nature of the organic group, R. In general, the vapor pressure increases as the molecular mass of R decreases. However, if R is too small, the alkoxide groups no longer shield the incompletely coordinated central metal ion and the molecule tends to oligomerise. This leads to an increased molecular weight and thus to a reduction of the vapor pressure. For the alkoxides, the vapor pressure also depends on the branching of R. The higher the branching, the more effective the shielding of the metal ion. In the case of the butoxides of Ti and Zr, this leads to a substantial
<table>
<thead>
<tr>
<th>Name</th>
<th>R₁, R₂</th>
<th>Abbr.</th>
<th>T(°C) for 1 torr vapor pressure</th>
</tr>
</thead>
<tbody>
<tr>
<td>Lead bis–acetylacetonate</td>
<td>CH₃,CH₃</td>
<td>Pb(acac)₂</td>
<td>95</td>
</tr>
<tr>
<td>Lead bis–trifluoroacetylacetonate</td>
<td>CF₃,CH₃</td>
<td>Pb(tfa)₂</td>
<td>72</td>
</tr>
<tr>
<td>Lead bis–hexafluoroacetylacetonate</td>
<td>CF₃,CF₃</td>
<td>Pb(hfa)₂</td>
<td>67</td>
</tr>
<tr>
<td>Lead bis–dimethylheptadione</td>
<td>CH₃,C(CH₃)₃</td>
<td>Pb(dhd)₂</td>
<td>76</td>
</tr>
<tr>
<td>Lead bis–tetramethylheptadione</td>
<td>C(CH₃)₂,C(CH₃)₃</td>
<td>Pb(thd)₂</td>
<td>60</td>
</tr>
<tr>
<td>Lead bis–heptafluoroheptadione</td>
<td>CH₃,C₅F₇</td>
<td>Pb(fhd)₂</td>
<td>95</td>
</tr>
<tr>
<td>Lead bis–heptafluorodimethyloctadione</td>
<td>C(CH₃)₃,C₅F₇</td>
<td>Pb(fod)₂</td>
<td>68</td>
</tr>
</tbody>
</table>
increase of the vapor pressure going from the n—butoxide, to iso—butoxide to tertiary—butoxide. The volatility of metal alkoxides is described by Bradley, Mehrotra, and Gauer [69].

5.2.2 Properties of Precursors

This section discusses the metalorganic precursors reported in the literature for Pb(ZrxTi1-x)O3 thin film deposition. The precursors for the Pb—component and their selected properties are listed in Table 5.3 [33–38,70–74]. Use of Pb(hfa)2 and Pb(fod)2 resulted in fluorine contamination in the films [75]. In addition, PbO formation from thermal decomposition of Pb(fod)2 is initiated at 300°C, but PbF2 becomes the dominant phase above 300°C [70]. On the other hand, although good quality PbO films were obtained from tetraethyl lead (TEL), the extremely toxic nature of this precursor may prevent its use in large scale applications. Additionally, lead alkyls are photosensitive, and decompose by free radical decay. Lead alkoxides, for example Pb(OBut)3, are also liquids at room temperature, and possess significant vapor pressures which creates toxicity problems. In addition, the large Pb(II) ion suffers the hydrolysis problem which is typical of metal alkoxides. In summary, Pb(thd)2 was found to be the most suitable precursor for lead—based ferroelectric thin film deposition.

The possible selection of metalorganic precursors for the Zr—component and their selected properties in PZT thin film deposition are listed in Table 5.4 [33–38,70,76,77]. Several difficulties were encountered in using Zr(acac)4 and Zr(tfa)4 precursors. For example, Zr(acac)4 resulted in cubic ZrO2 films with carbon contamination up to 15 atom% [76]. Changes in the gas composition when
Table 5.3 Possible selection of metalorganic precursors and their selected properties for PbO films

<table>
<thead>
<tr>
<th>Name</th>
<th>Formula</th>
<th>Abbreviation</th>
</tr>
</thead>
<tbody>
<tr>
<td>Tetraethyl lead</td>
<td>Pb(C₂H₅)₄</td>
<td>TEL</td>
</tr>
<tr>
<td>Lead t-butoxide</td>
<td>Pb(OᵗC₄H₉)₂</td>
<td>Pb(OBut)₂</td>
</tr>
<tr>
<td>Lead bis-hexafluoroacetylacetone</td>
<td>Pb(C₅HF₆O₂)₂</td>
<td>Pb(hfa)₂</td>
</tr>
<tr>
<td>Lead bis-heptafluorodimethyloctadione</td>
<td>Pb(C₁₀F₇H₁₀O₂)₂</td>
<td>Pb(fod)₂</td>
</tr>
<tr>
<td>Lead tetramethylheptadione</td>
<td>Pb(C₁₁H₁₉O₂)₂</td>
<td>Pb(dpm)₂ or Pb(thd)₂</td>
</tr>
</tbody>
</table>

<table>
<thead>
<tr>
<th>Precursor</th>
<th>Appearance at RT</th>
<th>Air Stability</th>
<th>Melting Point</th>
<th>Boiling Point</th>
<th>Vaporization Temperature</th>
<th>Decomposition Temperature</th>
</tr>
</thead>
<tbody>
<tr>
<td>TEL</td>
<td>Lq.</td>
<td>Sensitive</td>
<td>—</td>
<td>—</td>
<td>-20°C - 50°C</td>
<td>—</td>
</tr>
<tr>
<td>Pb(OBut)₂</td>
<td>Lq.</td>
<td>Sensitive</td>
<td>—</td>
<td>—</td>
<td>120°C</td>
<td>—</td>
</tr>
<tr>
<td>Pb(hfa)₂</td>
<td>White Powder</td>
<td>Stable</td>
<td>158°C</td>
<td>210°C</td>
<td>130°C</td>
<td>—</td>
</tr>
<tr>
<td>Pb(fod)₂</td>
<td>White Powder</td>
<td>Stable</td>
<td>76°C</td>
<td>—</td>
<td>100°C - 130°C</td>
<td>300°C</td>
</tr>
<tr>
<td>Pb(thd)₂</td>
<td>White Powder</td>
<td>Stable</td>
<td>128°C</td>
<td>320°C</td>
<td>135°C - 165°C</td>
<td>300°C</td>
</tr>
</tbody>
</table>
Table 5.4 Possible selection of metalorganic precursors and their selected properties for \( \text{ZrO}_2 \) films

<table>
<thead>
<tr>
<th>Name</th>
<th>Formula</th>
<th>Abbreviation</th>
</tr>
</thead>
<tbody>
<tr>
<td>Zirconium isopropoxide</td>
<td>( \text{Zr(OiC}_3\text{H}_7\text{)}_4 )</td>
<td>( \text{Zr(OPr)}_4 ) or ZIP</td>
</tr>
<tr>
<td>Zirconium t-butoxide</td>
<td>( \text{Zr(OtC}_4\text{H}_9\text{)}_4 )</td>
<td>( \text{Zr(OBu)}_4 ) or ZTB</td>
</tr>
<tr>
<td>Zirconium acetylacetonate</td>
<td>( \text{Zr(C}_5\text{H}_7\text{O}_2\text{)}_4 )</td>
<td>( \text{Zr(acac)}_4 )</td>
</tr>
<tr>
<td>Zirconium trifluoroacetylacetonate</td>
<td>( \text{Zr(C}_5\text{H}_4\text{F}_2\text{O}_2\text{)}_4 )</td>
<td>( \text{Zr(tfa)}_4 )</td>
</tr>
<tr>
<td>Zirconium tetramethylheptadione</td>
<td>( \text{Zr(C}_1\text{H}_1\text{H}_9\text{O}_2\text{)}_4 )</td>
<td>( \text{Zr(dpm)}_4 ) or ( \text{Zr(thd)}_4 )</td>
</tr>
</tbody>
</table>

Selected properties

<table>
<thead>
<tr>
<th>Precursor</th>
<th>Appearance at RT</th>
<th>Air Stability</th>
<th>Melting Point</th>
<th>Boiling Point</th>
<th>Vaporization Temperature</th>
<th>Decomposition Temperature</th>
</tr>
</thead>
<tbody>
<tr>
<td>ZIP</td>
<td>Lq.</td>
<td>Sensitive</td>
<td>—</td>
<td>—</td>
<td>175°C</td>
<td>—</td>
</tr>
<tr>
<td>ZTB</td>
<td>Yellow Lq.</td>
<td>Sensitive</td>
<td>—</td>
<td>95°C</td>
<td>25°C - 50°C</td>
<td>—</td>
</tr>
<tr>
<td>( \text{Zr(acac)}_4 )</td>
<td>White Powder</td>
<td>Sensitive</td>
<td>173°C</td>
<td>—</td>
<td>160°C</td>
<td>300°C</td>
</tr>
<tr>
<td>( \text{Zr(tfa)}_4 )</td>
<td>White Powder</td>
<td>Sensitive</td>
<td>128°C</td>
<td>235°C</td>
<td>160°C</td>
<td>300°C</td>
</tr>
<tr>
<td>( \text{Zr(thd)}_4 )</td>
<td>White Powder</td>
<td>Stable</td>
<td>345°C</td>
<td>—</td>
<td>180°C - 230°C</td>
<td>500 - 550°C</td>
</tr>
</tbody>
</table>
using Zr(tfa)₄ resulted in fluorine contamination in the films. The fluorine contamination problem can be solved by controlling the partial pressure of water vapor in the reactor during deposition. One of the problems in the use of the zirconium alkoxides, e.g. Zr(OPr⁴)₄ and Zr(OBu⁴)₄, is that they are very sensitive to air. Zr(thd)₄ is thermally stable over its vaporization temperature range, and is very easy to handle under ambient conditions [70]. It has been proven to be a suitable precursor for the CVD process despite its relatively high vaporization temperature (180°C – 230°C) and decomposition temperature (500°C – 550°C) [77]. Since the formation temperature of the perovskite phase of the PZT film is around 550°C, the high decomposition temperature of Zr(thd)₄ is not a severe problem.

The possible selection of metalorganic precursors for the Ti-component and their selected properties in PZT thin film deposition are listed in Table 5.5 [33-38,70-74]. Titanium alkoxides have been used as precursors for TiO₂ thin film deposition without significant disadvantages. They are reasonably stable under ambient conditions, and do not present any extreme health hazards. The difference in degree of moisture sensitivity of the titanium alkoxides and zirconium alkoxides is a function of the metal atom size. Both are d⁰ metals in the (IV) oxidation state, and are very electronegative. The smaller Ti⁴⁺ ion is somewhat shielded from atmospheric moisture by its organic ligands, but the larger Zr⁴⁺ ion is not completely shielded by its ligands, and reacts with atmospheric moisture.

Thus it is clear from the above discussion, that there is no ideal precursor combination for MOCVD PZT thin films. As mentioned before, when this study was initiated, there was no reported information available on MOCVD PZT films. After intensive studies searching for the most suitable compromise of precursors for MOCVD PZT thin films, the suggested combination is as follows:
<table>
<thead>
<tr>
<th>Name</th>
<th>Formula</th>
<th>Abbreviation</th>
</tr>
</thead>
<tbody>
<tr>
<td>Titanium ethoxide</td>
<td>Ti(OC₂H₅)₄</td>
<td>Ti(OEt)₄</td>
</tr>
<tr>
<td>Titanium isopropoxide</td>
<td>Ti(OiC₃H₇)₄</td>
<td>Ti(OPri)₄ or TIP</td>
</tr>
<tr>
<td>Titanium (di-isopropoxide)-</td>
<td>Ti(C₅H₇O₂)(OiC₃H₇)₂</td>
<td>Ti(acac)₂(OPri)₂</td>
</tr>
<tr>
<td>bis(acetylacetonate)</td>
<td></td>
<td></td>
</tr>
</tbody>
</table>

Selected Properties

<table>
<thead>
<tr>
<th>Precursor</th>
<th>Appearance at RT</th>
<th>Air Stability</th>
<th>Melting Point</th>
<th>Boiling Point</th>
<th>Vaporization Temperature</th>
<th>Decomposition Temperature</th>
</tr>
</thead>
<tbody>
<tr>
<td>Ti(OEt)₄</td>
<td>Colorless Lq</td>
<td>Stable</td>
<td>—</td>
<td>122°C</td>
<td>110°C</td>
<td>300°C</td>
</tr>
<tr>
<td>TIP</td>
<td>Colorless Lq</td>
<td></td>
<td>20°C</td>
<td>58°C</td>
<td>25°C – 106°C</td>
<td>—</td>
</tr>
<tr>
<td>Ti(acac)₂</td>
<td>Orange Lq</td>
<td></td>
<td></td>
<td></td>
<td>87°C</td>
<td>—</td>
</tr>
<tr>
<td>(OPri)₂</td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
</tbody>
</table>
(1) For PbO: Pb(thd)$_2$.

(2) For ZrO$_2$: Zr(thd)$_4$.

(3) For TiO$_2$: Ti(OEt)$_4$ or Ti(OPr)$_4$.

In our study, the precursor combination of Pb(thd)$_2$, Zr(thd)$_4$, and Ti(OEt)$_4$ is chosen based on their high vapor pressures, no contamination (the AES detection level for the impurities is less than 1%) in the resulting films, and, most importantly, easy handling (stable and nontoxic).

5.3 Experimental Procedure

A schematic diagram of the home-made hot-wall CVD apparatus is shown in Figure 5.1. The reaction chamber is a stainless steel tube having 80 mm inside diameter. The temperature is maintained by a resistively heated three-zone furnace. The temperature profile of the reaction chamber is shown in Figure 5.2 at the set points of 550°C for center zone (zone 2) and 555°C for side zones (zone 1 and 3). As can be seen in Figure 5.2, a 300 mm uniform temperature zone is defined as 550 ± 5°C. Low pressures are achieved by a mechanical pump. The pressure is monitored by an MKS BARATRON pressure sensor with a range of 12 to 10$^{-3}$ torr. A cold trap filled with liquid nitrogen is installed between the reaction chamber and the mechanical pump to condense the products and/or the unreacted reagents. The precursor material is packaged in a stainless steel bubbler which has two connectors; one is connected to the reactor by a stainless steel line with a manual valve and the other is connected to a N$_2$ gas cylinder with a mass flow controller. Aluminum housed mantle heaters with temperature controllers are used to control the temperatures of the precursors. The precursors were kept at the desired
Figure 5.1 Schematic diagram of hot-wall MOCVD apparatus for PZT films.
Figure 5.2 Temperature profile of the deposition zone of MOCVD apparatus.
temperatures within \( \pm 0.5^\circ C \) during deposition. The paths between the furnace and the precursor bubblers were heated by heating tapes to a temperature ranging from 200\(^\circ C\) to 250\(^\circ C\); this prevents the precursors from either condensing or decomposing. Typical deposition conditions are listed in Table 5.6.

The bubblers used in this study were home-designed having a cylindrical shape 1.5 inches in diameter and 6 inches high. A volume of 40 cm\(^3\) Ti(OEt)\(_4\) packaged in the bubbler can be used for more than 20 depositions. After each deposition this liquid source was kept in vacuum. In this manner, Ti(OEt)\(_4\) can last for at least one month without apparent degradation. On the other hand, 0.8 g each of fresh Pb(thd)\(_2\) and Zr(thd)\(_4\) were used for each deposition. All of these precursors are stable and safe in air at room temperature. The partial pressures of each of the precursors were in the ranges of 5 — 20 mtorr for Ti(OEt)\(_4\), 10 — 20 mtorr for Pb(thd)\(_2\), and 10 — 30 mtorr for Zr(thd)\(_4\) under the conditions listed in Table 5.6.

The measurement of the bubbler temperature was done by inserting a thermocouple in between the inner wall of the bubbler heater and the outer wall of the bubbler. Therefore, the bubbler temperature may not be the "real" precursor temperature. A summary of the deposition parameters from different investigators is given in Table 5.7. Although the same precursor was used by different investigators, the bubbler temperatures that were used had a large divergence. For example, the bubbler temperature of TEL varied within a 40\(^\circ C\) range among all authors. This may be due to the difference in the bubbler designs and/or the difference in the temperature measuring configurations.

The substrates were of three types: 1 inch diameter sapphire disks, Pt/Ti/SiO\(_2\)/Si wafers, and RuO\(_x\)/SiO\(_2\)/Si wafers. The sapphire disks were obtained from Swiss Jewel Company and had a surface orientation within a 30\(^\circ\) cone of the
Table 5.6 Typical deposition conditions for MOCVD PZT thin films

<table>
<thead>
<tr>
<th>Precursors</th>
<th>Pb(thd)$_2$</th>
<th>Zr(thd)$_4$</th>
<th>Ti(OEt)$_4$</th>
</tr>
</thead>
<tbody>
<tr>
<td>Precursor Temperature</td>
<td>145–165°C</td>
<td>210–230°C</td>
<td>90–115°C</td>
</tr>
<tr>
<td>Carrier Gas (sccm, N$_2$)</td>
<td>20–30</td>
<td>15–30</td>
<td>5</td>
</tr>
<tr>
<td>Substrate</td>
<td>sapphire, Pt/Ti/SiO$_2$/Si, and RuO$_x$/SiO$_2$/Si</td>
<td></td>
<td></td>
</tr>
<tr>
<td>Substrate Temperature</td>
<td>550°C</td>
<td></td>
<td></td>
</tr>
<tr>
<td>Dilute Gas (sccm, O$_2$)</td>
<td>500–1000</td>
<td></td>
<td></td>
</tr>
<tr>
<td>Total Pressure</td>
<td>6 torr</td>
<td></td>
<td></td>
</tr>
<tr>
<td>Deposition Rate (nm/min)</td>
<td>3.0–20.0</td>
<td></td>
<td></td>
</tr>
</tbody>
</table>
Table 5.7 Summary of deposition parameters from different investigators

<table>
<thead>
<tr>
<th>Group</th>
<th>Source materials</th>
<th>Dilute Gas (sccm)</th>
<th>Deposition Temperature (°C)</th>
<th>Total Press. (Torr)</th>
<th>Depos. Rate (nm/min)</th>
</tr>
</thead>
<tbody>
<tr>
<td>a</td>
<td>Pb(thd)$_2$, Zr(thd)$_4$, Ti(OEt)$_4$, O$_2$</td>
<td>550</td>
<td>6</td>
<td>3.0–20</td>
<td></td>
</tr>
<tr>
<td>b</td>
<td>TEL, ZIP, TIP, O$_2$</td>
<td>550</td>
<td>6</td>
<td>10–20</td>
<td></td>
</tr>
<tr>
<td></td>
<td>Ar, 40–100, Ar, 40–100, Ar, 40–100</td>
<td>120</td>
<td>—</td>
<td>—</td>
<td></td>
</tr>
<tr>
<td></td>
<td>TEL, Zr(thd)$_4$, TIP, O$_2$</td>
<td>600</td>
<td>6</td>
<td>10–20</td>
<td></td>
</tr>
<tr>
<td></td>
<td>Ar, 40–100, Ar, 40–100, Ar, 40–100</td>
<td>120</td>
<td>—</td>
<td>—</td>
<td></td>
</tr>
<tr>
<td>c</td>
<td>TEL, Zr(thd)$_4$, TIP, O$_2$</td>
<td>600–650</td>
<td>5</td>
<td>8.5–12</td>
<td></td>
</tr>
<tr>
<td></td>
<td>Ar, 30–100, Ar, 30–100, Ar, 30–100</td>
<td>200</td>
<td>—</td>
<td>—</td>
<td></td>
</tr>
<tr>
<td>d</td>
<td>Pb(thd)$_2$, ZTB, TIP, O$_2$</td>
<td>700</td>
<td>20</td>
<td>20–30</td>
<td></td>
</tr>
<tr>
<td></td>
<td>N$_2$, 165, N$_2$, 180, N$_2$, 50</td>
<td>40</td>
<td>—</td>
<td>—</td>
<td></td>
</tr>
<tr>
<td>e</td>
<td>Pb(thd)$_2$, ZTB, TIP, O$_2$</td>
<td>600–700</td>
<td>1–2</td>
<td>5–20</td>
<td></td>
</tr>
<tr>
<td></td>
<td>N$_2$, 100–200, N$_2$, 80–100, N$_2$, 30</td>
<td>700</td>
<td>—</td>
<td>—</td>
<td></td>
</tr>
<tr>
<td>f</td>
<td>TEL, ZTB, TIP, O$_2$</td>
<td>700</td>
<td>3.75</td>
<td>—</td>
<td></td>
</tr>
<tr>
<td></td>
<td>N$_2$, —, N$_2$, —, N$_2$, —</td>
<td>200</td>
<td>—</td>
<td>—</td>
<td></td>
</tr>
</tbody>
</table>

*The designation of the research group can be found in Table 5.1.

Note: All the PZT films were deposited by using cold-wall type reactors, except this study.
[100] direction. The Pt layer on the Pt-coated substrate obtained from SHARP Co, Japan was a sputtered polycrystalline film. The RuO$_x$ layer on RuO$_x$-coated substrate bought from Massachusetts Thin Films was also a sputtered polycrystalline film. Samples were loaded, the reactor tube was sealed, and the system was evacuated to 0.01 torr. The pressure was maintained until the samples reached thermal equilibrium. Deposition was initiated by sending each of the three precursors and the oxygen diluent gas at the same time and subsequently adjusting the vacuum to the desired pressure using the pump valve. At the end of the run the evaporators and diluent gas were shut off, and the reactor was evacuated to base pressure before backfilling with air to atmospheric pressure. The samples were furnace-cooled below 100°C before they were removed from the reactor.

As-deposited MOCVD PZT films were specular, crack-free, uniform, and adhered well on all substrates used and were highly transparent on sapphire substrates. These films also showed very smooth surfaces as viewed using both optical microscopy and scanning electron microscopy. The deposition rates were estimated from the weight changes of each specimen before and after deposition. The film thicknesses estimated in this manner agreed very well with that calculated from the optical interference fringes. For the deposition conditions described in Table 5.6, film growth rates were in the range of 3.0 to 20.0 nm/min. A very interesting result on the film growth rate was that the rates observed on the Pt-coated substrates were about 2 – 3 times larger than on the sapphire and RuO$_x$-coated substrates. A similar substrate effect was also reported by Swartz et al [74].

5.4 Results and Discussion of MOCVD PZT Thin Films
The characterization techniques of MOCVD PZT thin films have been described in detail in Chapter 2.

5.4.1 The Effect of the Deposition Parameters on the Composition of the Film

The stoichiometry of the films can be controlled mainly by varying the individual precursor temperatures and/or the diluent gas flow rates. The variation of the Zr/Ti ratio under different deposition conditions is illustrated in Figure 5.3. As can be seen from Figure 5.3, the desired Zr/Ti ratio can be easily obtained across the entire PZT solid solution range.

One of the advantages of the hot-wall MOCVD is its high throughput. In a production line, it is common to have more than 100 wafers in one run. Therefore, it is important to examine the composition uniformity from sample to sample. The composition uniformity across the entire uniform temperature zone (550 ± 5°C) is shown in Figure 5.4. Figure 5.4 shows that the higher the diluent gas flow rate, the better the sample-to-sample composition uniformity. For example, the composition is relatively uniform in a region of up to two thirds of the size of the entire uniform temperature zone at a diluent gas flow rate of 1000 sccm, while it is less than one third of the uniform temperature zone at diluent gas flow rate of 500 sccm. Figure 5.4 also shows that zirconium content increased while the titanium content decreased when approaching the end of the uniform temperature zone. The increasing zirconium content at the end of the uniform temperature zone indicates that the Zr(thd)$_4$ is more difficult to decompose than Ti(OEt)$_4$ is. The decreasing titanium content is a consequence of the depletion of titanium precursors at the end of the uniform temperature zone.
Figure 5.3 Variation of (Zr,Ti) composition with the bubbler temperature of Zr and Ti precursors.
Figure 5.4 Sample-to-sample composition uniformity.

$T_D = 550^\circ C$

$P = 6$ torr
5.4.2 X-ray Diffraction Study

The specimens (deposited films on substrates) were directly characterized by x-ray diffraction. No further specimen preparation is required. All the as-deposited PZT films were single phase with perovskite structure, regardless of the substrate and the composition. The XRD patterns of the as-deposited PZT films on sapphire disks, Pt/Ti/SiO₂/Si wafers, and RuOₓ/SiO₂/Si wafers are shown in Figures 5.5–5.7, respectively. One very interesting observation is that both non-oriented and highly [100] oriented films were obtained on each of these three different types of substrates. Figure 5.5 shows PZT films on sapphire disks with five different Zr/Ti ratios ranging from \( x = 0.07 \) to \( x = 0.70 \) where \( x = \frac{Zr}{(Zr+Ti)} \). As expected, the films with \( x \) values larger than 0.5 have rhombohedral structure, and the films with \( x \) values smaller than 0.5 have tetragonal structure. As can be seen from Figure 5.5, the films with \( x = 0.07 \) and \( x = 0.70 \) were highly [001] oriented, while the films with \( x = 0.33, 0.51, \) and 0.62 are non-oriented. Figure 5.6 shows PZT films on Pt/Ti/SiO₂/Si substrates. Similar to the films on sapphire disks, both highly [001] oriented films [Figures 5.6(a) and 5.6(b)] and non-oriented films [Figure 5.6(c)] were observed. There are very strong XRD peaks at 2\( \theta \) around 40 degree. By carefully examining these peaks, they were found to consist of two peaks, one at 2\( \theta = 38.4^0 \) corresponding to (111) PbPt₅₋₇ [78] and the other at 2\( \theta = 40^0 \) corresponding to (111) Pt (see the insert of Figure 5.6). This is direct evidence of the interaction of PZT films and Pt substrates. The XRD patterns for four different compositions on the RuOₓ/SiO₂/Si substrates are shown in Figure 5.7. The one with \( x = 0.55 \) is highly [001] oriented, while the others are non-oriented.
Figure 5.5 XRD patterns of as-deposited MOCVD PZT films on sapphire substrates.
Figure 5.6 XRD patterns of as-deposited MOCVD PZT films on Pt/Ti/SiO₂/Si substrates
Figure 5.7 XRD patterns of as-deposited MOCVD PZT films on RuO$_x$/SiO$_2$/Si substrates.
5.4.3 Surface Morphology

The surface morphology of the typical MOCVD PZT films was investigated by SEM and is shown in Figure 5.8. Figures 5.8(a)–(c) are the as-deposited films on sapphire disk with $x = 0.4$, on Pt-coated substrate with $x = 0.6$, and on RuO$_x$-coated substrate with $x = 0.8$, respectively. Figure 5.8(d) is the same sample as in Figure 5.8(c) after annealing in air at 650°C for 30 min. The SEM micrographs show that the films were dense and smooth on all three different substrates used. The grains were very fine and uniformly distributed. The average grain size was estimated to be 0.15 $\mu$m for the film on Pt/Ti/SiO$_2$/Si and RuO$_x$/SiO$_2$/Si substrates and less than 0.1 $\mu$m for the film on the sapphire substrate.

Recall that the microstructures of MOD films presented in Chapters 3 and 4 are composition and heat treatment dependent, and the average grain size for the zirconium rich films was on the order of 10 $\mu$m which is about 100 times larger than that of MOCVD films. As can be seen in Figure 5.8, the microstructure of the MOCVD PZT films seems to be independent of the substrate used, the film composition, and the annealing temperature. In addition, the average grain sizes of MOCVD PZT films from other research groups were about 10 times larger than ours (see Table 5.1). From the view of large scale applications, it is very important to have a fine grain structure. For example, a submicro device can sit either on a single grain or on the grain boundary if the average grain size is about 1 $\mu$m. The resulting electrical properties of these two devices would be expected to be very different. On the other hand, for a film having an average grain size of 0.1 $\mu$m, all the devices will cover several tens of grains. Therefore, the performance of every
Figure 5.8 SEM micrographs of MOCVD Pb(Zr<sub>x</sub>Ti<sub>1-x</sub>)O<sub>3</sub> films: (a) as-deposited film on sapphire substrate with \( x = 0.4 \), (b) as-deposited film on Pt/Ti/SiO<sub>2</sub>/Si substrate with \( x = 0.6 \), (c) as-deposited film on RuO<sub>x</sub>/SiO<sub>2</sub>/Si substrate with \( x = 0.8 \), and (d) 650°C/30min annealed film on RuO<sub>x</sub>/SiO<sub>2</sub>/Si substrate with \( x = 0.8 \).
device is expected to be uniform.

As mentioned earlier in section 5.4.2, highly [100] oriented films were occasionally obtained on all three different types of substrates used. A surprising result is that a different microstructure was observed only for the film on sapphire disk. Figure 5.9 shows the SEM micrograph of the highly [100] oriented film on sapphire disk whose XRD pattern is shown in Figure 5.5(a). The film has faceted grains, which indicates that they are well crystallized, with an estimated average grain size of 0.5 μm. This surface morphology is similar to those reported by Sakashita et al [34].

5.4.4 Reproducibility

The reproducibility is always the most important issue from the view of mass production. Figure 5.10 shows the reproducibility of the compositions and deposition rates of MOCVD PZT films on sapphire substrates for four consecutive runs with the same deposition parameters. The samples were picked from the same position in the reactor for each run. As can be seen in Figure 5.10, the composition concentrations of Pb, Zr, and Ti were almost constant: 54 ± 2, 32 ± 1, and 14 ± 1 atomic %, respectively, for all four runs. In addition, the variation in the deposition rate was also small, 3.8 ± 0.5 nm/min.

An excellent reproducibility in surface morphology is also shown in Figure 5.11. Each of these four samples was a film on RuO$_x$/SiO$_2$/Si substrate which was also picked from the same position in the reactor for each run. As can be seen in Figure 5.11, the films were dense and smooth and had an average grain size around 0.15 μm.
Figure 5.9 SEM micrograph of highly [100] oriented MOCVD PZT film on sapphire substrate.
Figure 5.10 Reproducibility of composition and deposition rate for four consecutive runs with the same deposition condition. The films were on sapphire substrates.
Figure 5.11 Reproducibility of surface morphology for four consecutive runs with the same deposition condition. The films were on RuO$_2$/SiO$_2$/Si substrates.
5.4.5 Optical Properties

The UV–VIS–NIR transmission spectrum of the as-deposited PZT (x = 0.6) film on the sapphire substrate is shown in Figure 5.12. This spectrum illustrates that the transmittance drops down to 0% (the absorption edge) at a wavelength around 302 nm and has a value of 85% at a wavelength of 2000 nm. The envelope method (see Chapter 3) was used to calculate the film thickness as well as the refractive index and extinction coefficient of the film as a function of wavelength. This calculation procedure is mentioned in detail in Chapter 3. The film thickness calculated by this method is 510 nm. The n and k as a function of wavelength are shown in Figure 5.13. The n and k values are 2.413 and 0.0008, respectively at \( \lambda = 633 \text{ nm} \) for the film with Zr/Ti = 60/40. The high refractive index value, compared to the value of 2.281 from MOD PZT films (Figure 3.11), indicates that the MOCVD PZT film is denser than the MOD film. The very low extinction coefficient illustrates the nature of the specular and highly transparent films.

5.4.6 Interrelationship of Composition Uniformity and Ferroelectric Properties

Although the phase, the microstructure, the "average" composition, and the electrodes of a particular MOCVD PZT film may all be good, the ferroelectric properties may not be as expected. One of the possible problems is that the composition uniformity through the bulk of the film may not be acceptable. Two typical samples were presented to demonstrate the effect of the composition uniformity across the film thickness on ferroelectric properties. Figure 5.14 shows the AES depth profile and selected AES spectra of the film with the "average"
Figure 5.12 Optical transmission spectrum of as-deposited MOCVD Pb(Zr$_{0.6}$Ti$_{0.4}$)O$_3$ film on sapphire on sapphire substrate. Dashed line shows the transmittance of the uncoated sapphire substrate.
Figure 5.13 Variation of optical constants with wavelength for as-deposited MOCVD Pb(Zr0.6Ti0.4)O3 film.
Figure 5.14 AES study of MOCVD PZT film with the composition of Pb/Zr/Ti = 50/41/9: (a) depth profile, (b) AES spectrum on the sample surface, and (c) AES spectrum after 3 min Ar sputtering.
composition of Pb/Zr/Ti = 50/41/9 which was measured by the EDS. For convenience, this sample will be referred to as sample A hereafter. Figure 5.15 shows the AES depth profile and selected AES spectra of the film with the "average" composition of Pb/Zr/Ti = 52/26/22 which was also measured by the EDS, and this sample will be referred to as sample B hereafter. The D–E hysteresis loops of sample A and B are shown in Figures 5.16 and 5.17, respectively.

As can be seen in Figure 5.14(a), the composition of sample A was quite uniform through the bulk of the film for all four elements i.e., Pb, Zr, Ti, and O. Figures 5.14(b) and 5.14(c) show the AES spectra both at the sample surface and after 3 minutes of Ar sputtering, respectively. The carbon peak shown in Figure 5.14(b) was due to the carbon adsorption on the sample surface. After 3 minutes of Ar sputtering, the carbon peak was not detected as can be seen in Figure 5.14(c). This indicates that no carbon contamination was found in the bulk of the film. On the other hand, the composition of sample B was less uniform through the thickness of the film than that of sample A. As can be seen in Figure 5.15(a), the Pb content appears to be uniform through the thickness of the film. In contrast to Pb content, the Zr content decreased, while the Ti and O contents increased with an increase in the sputtering time. This poor composition uniformity through the thickness of the film may be a result of the fairly high partial pressures of precursors during the initial stage of the deposition. The AES spectra of sample B at the sample surface and after 3 minutes Ar sputtering, which are shown in Figures 5.15(b) and 5.15(c), respectively, have similar behavior as those of sample A.

Although sample B has a preferable "average" composition than sample A (52/26/22 vs. 50/41/9), the composition profile through the thickness of each of the films resulted in sample A having superior ferroelectric properties: for sample A, the
Figure 5.15 AES study of MOCVD PZT film with the composition of Pb/Zr/Ti = 52/26/22: (a) depth profile, (b) AES spectrum on the sample surface, and (c) AES spectrum after 3 min Ar sputtering.
Figure 5.16  D–E hysteresis loop of 600°C/30min annealed MOCVD film whose composition profile is shown in Figure 5.14.
Figure 5.17 D–E hysteresis loop of 600°C/30min annealed MOCVD film whose composition profile is shown in Figure 5.15.
spontaneous polarization, \( P_s = 23.3 \, \mu C/cm^2 \), the remanent polarization, \( P_r = 12.3 \, \mu C/cm^2 \), and the coercive field, \( E_c = 64.5 \, kV/cm \), see Figure 5.16. On the contrary, sample B had poor ferroelectric properties: \( P_s = 9.36 \, \mu C/cm^2 \), \( P_r = 6.0 \, \mu C/cm^2 \), and \( E_c = 90.9 \, kV/cm \), as shown in Figure 5.17.

The composition non-uniformity at the interface of the film and the bottom electrode is due to the unstable source partial pressure during the initial deposition stage. To improve this problem, the CVD reactor was modified by adding a bypass line as shown in Figure 5.18. At the beginning of the deposition, the source vapors were flowed through the bypass line; oxygen was flowed through the deposition chamber to minimize the back diffusion of source vapors into the chamber. This bypass process was continued for about 3 minutes before beginning the deposition process. The effect of the bypass line can be seen in Figure 5.19. Figure 5.19(a) shows the AES depth profile of PZT film on RuO\(_2\)/SiO\(_2\)/Si substrate without the bypass, and Figure 5.19(b) shows the AES depth profile of that with the bypass.

5.5 Cold–Wall MOCVD PZT Thin Films

A schematic diagram of the home-made cold–wall MOCVD apparatus with the bypass line is shown in Figure 5.20. The cold–wall reactor differs from the hot–wall reactor in that (1) only the substrates are heated, (2) the source vapors are vertically injected onto the substrates, and (3) the wall of the deposition chamber is kept around 250°C. A three inch diameter substrate heater was employed, which can be operated at a maximum temperature of 900°C. The temperature of the substrate heater is position insensitive within an 8°C range, and the variation in temperature with time is within 1°C. A substrate holder, which was made of
Figure 5.18 Schematic diagram of hot-wall MOCVD apparatus with bypass line.
Figure 5.19 AES depth profiles of MOCVD PZT films on RuO$_x$/SiO$_2$/Si: (a) without bypass line and (b) with bypass line.
INCONEL and was placed in direct contact with the substrate heater, was used to hold the substrates. The substrate temperature was monitored by a thermocouple which was directly placed inside the center of the substrate holder. The specimens were adhered on the substrate holder by silver paste. The silver paste was used to improve the heat conduction and the temperature uniformity of the specimens. The distance between the inlet of the source mixture and the substrates can be varied from 1.5 to 10 cm. The setup and the control of the bypass line and the bubbler heaters are similar to those of the hot-wall apparatus.

The deposition conditions of the cold-wall MOCVD PZT films were similar to those used in hot-wall apparatus except the deposition temperature was 600°C. The PZT films obtained from cold-wall MOCVD were also uniform and specular on all three different substrates, i.e. sapphire disks, Pt/Ti/SiO₂/Si, and RuOₓ/SiO₂/Si substrates. Typical XRD patterns of the as-deposited PZT films by cold-wall MOCVD are shown in Figure 5.21. The XRD patterns show that the films were single phase with perovskite structure. The film on the RuOₓ-coated substrate was highly [111] oriented, while the films on the sapphire and Pt-coated substrates were non-oriented.

A very uniform and fine grain microstructure was also obtained from the cold-wall MOCVD PZT films. Figure 5.22 shows the SEM micrograph of the surface morphology of the cold-wall MOCVD PZT film on Pt-coated substrate whose XRD pattern is shown in Figure 5.21(b). The average grain size was estimated to be about 0.1 μm.

5.6 Summary
Figure 5.21 XRD patterns of MOCVD PZT films deposited by cold–wall reactor at 600°C: (a) on RuO$_x$/SiO$_2$/Si, (b) on Pt/Ti/SiO$_2$/Si, and (c) on sapphire.
Figure 5.22 SEM micrograph of cold-wall MOCVD PZT film on Pt/Ti/SiO$_2$/Si.
(1) Smooth and specular PZT thin films with pure perovskite phase were successfully fabricated at temperatures as low as 550°C on sapphire disks and Si wafers coated with either Pt or RuOx by hot-wall MOCVD using Pb(thd)2, Zr(thd)4, Ti(OEt)4, and O2 as source materials.

(2) Highly [001] oriented films were occasionally obtained on all three different substrates.

(3) The reproducibility has been confirmed by four consecutive depositions.

(4) The stoichiometry of the films can be easily controlled either by varying the individual precursor temperature and/or the flow rate of the carrier gas.

(5) The compositions of films were uniform from sample to sample for up to two thirds of the length of the uniform temperature zone (i.e., 20 cm in this study) when 1000 sccm oxygen was used as the diluent gas.

(6) High refractive index (n = 2.413) and low extinction coefficient (k = 0.0008) were obtained for the films on the sapphire disks.

(7) The average grain sizes of the films on all three different substrates used were found to be ≈ 0.1 μm.

(8) The surface morphology of the films seems to be independent of the substrate, the film composition, and the annealing temperature.

(9) The AES spectrum showed no carbon contamination in the bulk of the film, and the AES depth profile showed an uniform composition distribution for the films deposited using the bypass.

(10) A well defined D–E hysteresis loop was observed with the ferroelectric properties of \( P_s = 23.3 \mu C/cm^2 \), \( P_r = 12.3 \mu C/cm^2 \), and \( E_c = 64.5 \) kV/cm for the film with \( Zr/Ti = 82/18 \).

(11) Smooth and specular PZT films with pure perovskite phase were also
obtained by cold-wall MOCVD.
Chapter 6 Summary

The results of this research are now summarized as follows:

1. Ferroelectric thin films of lead zirconate titanate were successfully fabricated by the metalorganic decomposition process for the entire lead–titanate and lead–zirconate solid solution range. The average grain size of the MOD PZT films was found to increase with increasing zirconium content.

2. The optical properties (the refractive index, the extinction coefficient, and the absorption coefficient near the band gap) and the thickness of the PZT thin films were studied. The envelope method, with consideration of light intensity loss from the back surface of the substrate, was shown to be a simple and convenient tool for obtaining the optical properties and the film thickness of the PZT films by using the transmission spectra alone in the medium and weak absorption regions. In the near optical band gap region, both the transmission and the reflection spectra were used to successfully calculate the optical constants of the films. The film thickness derived from the envelope method was cross checked by a computer simulation method and was found to have an accuracy better than 2%. In addition, the refractive indices were fitted to a simple Sellmeier type equation for determining the dispersion constants for both porous PZT films and bulk PZT materials. The
valid wavelength range of these dispersion relations was found to be from 350 nm to 2000 nm.

3. The refractive index of the PZT films decreased linearly with increasing zirconium content. On the other hand, the near optical band gap energy of the PZT materials increased with increasing the zirconium content.

4. An effective, versatile, and nondestructive optical method was developed for the study of the structure development in MOD PZT films. Also, the models for the structure development were proposed and were verified by this optical method. Using this method, the characteristic temperatures (i.e., the initiation and the completion temperatures) of each phase can be easily identified. The structure developments in MOD PZT films were found to involve at least three phases in a certain temperature range. In addition, the volume fraction of each phase in a two–phase mixture can be obtained.

5. For the PZT films prepared by the MOD process, the perovskite phase formed at much lower temperatures in titanium rich PZT films compared to those of zirconium rich PZT films; for example, 460°C for PbTiO$_3$ and 650°C for PbZrO$_3$.

6. The ferroelectric PZT thin films were successfully deposited at temperatures as low as 550°C on sapphire disks, Pt/Ti/SiO$_2$/Si wafers, and RuO$_x$/SiO$_2$/Si wafers by hot–wall MOCVD using safe and stable precursors, namely, lead tetramethylheptadione [Pb(thd)$_2$], zirconium tetramethylheptadione [Zr(thd)$_4$], titanium ethoxide [Ti(OEt)$_4$], and oxygen (O$_2$). The films had the pure perovskite
phase in the as-deposited state. Also, the films were smooth, specular, crack-free, uniform, and adhered well on all substrates used. The reproducibility has been confirmed by four consecutive depositions.

7. The stoichiometry of the films can be easily controlled either by varying the individual precursor temperature and/or the flow rate of the carrier gas. The sample-to-sample composition uniformity was found to be very good for up to two thirds of the length of the uniform temperature zone (i.e., 20 cm in this study) when 1000 sccm oxygen was used as the dilute gas.

8. The surface morphology of the MOCVD PZT films seems to be independent of the substrate, the film composition, and the annealing temperature. The average grain size of the films on all three different substrates used was found to be around 0.1 μm.

9. Two significant differences on the structure properties between the MOD and the MOCVD films were observed: (1) the perovskite phase of the MOCVD film was completely formed at the deposition temperature (550°C) regardless of the Zr/Ti ratio, while for the MOD film, the temperature at which the formation of the perovskite phase was completed was strongly dependent on the Zr/Ti ratio, (2) the microstructure of the MOCVD PZT film was found to be an insensitive function of the substrate, the composition, and the annealing temperature, while that of the MOD film was a strong function of the substrate, the composition, and the annealing temperature.
10. High refractive index \( n = 2.413 \) at \( \lambda = 632.8 \text{ nm} \) and low extinction coefficient \( k = 0.0008 \) at \( \lambda = 632.8 \text{ nm} \) were obtained for the \( \text{Pb}(\text{Zr}_{0.6}\text{Ti}_{0.4})\text{O}_3 \) film on the sapphire disk. The refractive index value of 2.413 at \( \lambda = 632.8 \text{ nm} \) corresponds to a packing density of 0.93. The very low extinction coefficient illustrates the nature of the specular and highly transparent films.

11. The AES spectrum showed no carbon contamination (the detection level is less than 1 at\%) in the bulk of the film, and the AES depth profile showed uniform composition distribution for the films deposited using the bypass. The composition uniformity through the thickness of the film was found to have a significant effect on the ferroelectric properties. For a film with a uniformly distributed composition with \( \text{Zr}/\text{Ti} = 82/18 \), a well defined \( D-E \) hysteresis loop was observed with the superior ferroelectric properties of \( P_s = 23.3 \text{ \mu C/cm}^2 \), \( P_r = 12.3 \text{ \mu C/cm}^2 \), and \( E_c = 64.5 \text{ kV/cm} \).

12. Highly [100] oriented films were occasionally obtained on all three different substrates by both the hot–wall MOCVD and the cold–wall MOCVD.
Chapter 7  Suggestions for Future Research

The results of this study are far from final, and in fact only touch the surface of the ferroelectric materials, especially in the MOCVD aspect. In this chapter several directions which follow from the present research will be suggested.

The film thickness measurements are very important in a thin film processing technique because they give information on the film growth rate. As mentioned in Chapter 2, the film thickness can also be measured by either an optical profilometer or a stylus profilometer, both of which require a sharp step between the film and the substrate. This sharp step may be created by either covering a small portion of the substrate during the deposition or etching away a small portion of the film after the deposition. However, either one of these methods may not work in many cases. For example, it is not easy to generate a sharp step during the chemical vapor deposition because of the high temperature process and the high penetration nature of the chemical vapors. Also, it is very difficult to find an etching solution which can isotropically etch the film away without damaging the substrate.

The film thickness measurement using the optical transmission or reflection spectrum is very attractive because it is nondestructive. Although an accurate measurement technique for the film thickness using the transmission interference fringes along with the envelope method has been demonstrated in Chapter 2, it is only good for films on a transparent substrate. For a film on an opaque substrate such as
silicon wafer or metal–coated silicon wafer, the following procedures are suggested for the film thickness calculation:

(1) measure the reflection spectrum of the sample
(2) use a simple Sellmeier type dispersion relation, for example equation 2.43, for refractive index
(3) use equation 2.10 with three unknowns, i.e., the film thickness and two dispersion constants, to fit the experimental reflection spectrum

For the case of the PZT thin films, the dispersion constants obtained in this study could be used for the initial guess in the above procedures.

The phase transformation kinetics can be easily obtained using the method developed in Chapter 3, if the refractive index of the sample is studied as a function of time at several temperatures in the pyrochlore–perovskite phase transformation region. In addition, the proposed models for the structure development in the PZT films may be confirmed by using Ramam scattering which is more direct and may be more sensitive than the method described in Chapter 3.

One of the goals of this research is to develop a reliable MOCVD process for PZT thin films. Although successful and reproducible depositions and good properties of PZT films have been achieved, many problems still need to be solved, such as

(1) Understanding of the deposition process
(2) Understanding how the deposition rate and the substrate affect the nucleation and the growth of the film
(3) Understanding the difference between the hot–wall and the cold–wall
MOCVD PZT films

Additionally, a dopant such as lanthanum can be incorporated into the PZT film by the established MOCVD PZT reactor and process.
Appendix A  Preparation of PZT Precursor Solutions

To prepare an M molar fraction solution, it follows

\[ M = \frac{W}{W_M V} \]  \hspace{1cm} (A.1)

where \( W_M \) is molecular weight of solute, \( w \) is the weight of solute, and \( V \) is the volume of the solution in liter. The molecular weight and purity of the starting precursors are listed in Table A.1. If, for example, we want to prepare a 0.5 mole 30 ml lead titanate (PT) precursor solution with 10% lead acetate excess, the detailed procedures are as follows:

1. Weigh 6.2589 g of lead acetate \((0.5 \times 379.33 \times 0.03 = 5.6899 \text{ g with } 10\% \text{ excess})\).
2. Add about 50 ml methoxyethanol into lead acetate (referred to as solution A).
3. Distill solution A at 120°C until the volume is reduced to about 30 ml (the purpose of this step is to boil off the water in lead acetate, solution B).
4. Add 4.2637 g titanium isopropoxide into solution B \((0.5 \times 284.25 \times 0.03 = 4.2637 \text{ g})\) and stir it (solution C).
5. Distill solution C at 120°C until the volume is reduced to less than 30 ml.
6. Add proper amounts of methoxyethanol to make the final solution volume of 30 ml.

The same procedure can be applied to prepare a 0.5 mole 30 ml lead zirconate (PZ) precursor solution except that at step 4, a 7.0191 g zirconium n-propoxide should be used (the purity of the precursor must be taken into account). The final PZT precursor solutions are prepared by mixing PT and PZ solutions in volume fraction according to the desired Zr/Ti composition ratio.

<table>
<thead>
<tr>
<th>Precursor</th>
<th>Formula</th>
<th>Molecular Weight</th>
<th>Purity</th>
</tr>
</thead>
<tbody>
<tr>
<td>Lead Acetate</td>
<td>Pb(OOCCH₃)₂·3H₂O</td>
<td>379.33</td>
<td>100%</td>
</tr>
<tr>
<td>Titanium Isopropoxide</td>
<td>Ti(OC₃H₇)₄</td>
<td>284.25</td>
<td>100%</td>
</tr>
<tr>
<td>Zirconium n-Propoxide</td>
<td>Zr(OC₃H₇)₄</td>
<td>327.55</td>
<td>70%</td>
</tr>
</tbody>
</table>
Appendix B

This Appendix collects figures not presented in Chapter 2 for the optical properties study of PZT thin films. They are

Figures B.1 – B.6  The reflection and the transmission spectra and their sum of Pb(ZrxTi1-x)O3

Figures B.7 – B.12  The refractive index as a function of wavelength and the dispersion curve of Pb(ZrxTi1-x)O3

Figures B.13 – B.18  Adjusted refractive index as a function of wavelength and the dispersion curve of Pb(ZrxTi1-x)O3

Figures B.19 – B.23  The extinction coefficient as a function of wavelength of Pb(ZrxTi1-x)O3

Figures B.24 – B.30  The experimental and simulated transmission spectra of Pb(ZrxTi1-x)O3
Figure B.1 The reflectance and the transmittance and their sum of PbTiO$_3$ film on sapphire in the wavelength range of 300 nm to 2000 nm. The reflection spectrum was measured without the black paint on the back surface of the substrate.
Figure B.2 The reflectance and the transmittance and their sum of Pb(Zr$_{0.2}$Ti$_{0.8}$)O$_3$ film on sapphire in the wavelength range of 300 nm to 2000 nm. The reflection spectrum was measured without the black paint on the back surface of the substrate.
Figure B.3 The reflectance and the transmittance and their sum of Pb(Zr<sub>0.4Ti<sub>0.6</sub>)O<sub>3</sub> film on sapphire in the wavelength range of 300 nm to 2000 nm. The reflection spectrum was measured without the black paint on the back surface of the substrate.
Figure B.4 The reflectance and the transmittance and their sum of Pb(Zr_{0.5}Ti_{0.5})O_3 film on sapphire in the wavelength range of 300 nm to 2000 nm. The reflection spectrum was measured without the black paint on the back surface of the substrate.
Figure B.5 The reflectance and the transmittance and their sum of Pb(Zr\textsubscript{0.8}Ti\textsubscript{0.2})O\textsubscript{3} film on sapphire in the wavelength range of 300 nm to 2000 nm. The reflection spectrum was measured without the black paint on the back surface of the substrate.
Figure B.6 The reflectance and the transmittance and their sum of PbZrO$_3$ film on sapphire in the wavelength range of 300 nm to 2000 nm. The reflection spectrum was measured without the black paint on the back surface of the substrate.
Figure B.7 The refractive index as a function of wavelength and the dispersion curve of PbTiO$_3$ film
Figure B.8 The refractive index as a function of wavelength and the dispersion curve of Pb(Zr$_{0.2}$Ti$_{0.8}$)O$_3$ film
Figure B.9 The refractive index as a function of wavelength and the dispersion curve of Pb(Zr$_{0.4}$Ti$_{0.6}$)O$_3$ film
Figure B.10 The refractive index as a function of wavelength and the dispersion curve of Pb(Zr_{0.5}Ti_{0.5})O_3 film
Figure B.11 The refractive index as a function of wavelength and the dispersion curve of \( \text{Pb(Zr}_{0.8}\text{Ti}_{0.2})\text{O}_3 \) film.
Figure B.12 The refractive index as a function of wavelength and the dispersion curve of PbZrO$_3$ film
Figure B.13  Adjusted refractive index as a function of wavelength and the dispersion curve of Pb(Zr<sub>0.2</sub>Ti<sub>0.8</sub>)O<sub>3</sub> film
Figure B.14 Adjusted refractive index as a function of wavelength and the dispersion curve of Pb(Zr_{0.4}Ti_{0.6})O_3 film
Figure B.15 Adjusted refractive index as a function of wavelength and the dispersion curve of Pb(Zr$_{0.5}$Ti$_{0.5}$)O$_3$ film
Figure B.16  Adjusted refractive index as a function of wavelength and the dispersion curve of Pb(Zr$_{0.6}$Ti$_{0.4}$)O$_3$ film
Figure B.17 Adjusted refractive index as a function of wavelength and the dispersion curve of Pb(Zr$_{0.8}$Ti$_{0.2}$)O$_3$ film
Refractive Index ($n$)

$\text{PbZrO}_3$

- : Experimental data adjusted to 100% density

--- : Dispersion relation

$$n^2 = 1 + 4.2033\lambda^2 / (\lambda^2 - 0.0501)$$

---

Figure B.18 Adjusted refractive index as a function of wavelength and the dispersion curve of PbZrO$_3$ film

185
Figure B.19 The extinction coefficient as a function of wavelength of PbTiO$_3$ film
Figure B.20 The extinction coefficient as a function of wavelength of 
\( \text{Pb(Zr}_{0.2}\text{Ti}_{0.8})\text{O}_3 \) film
Figure B.21 The extinction coefficient as a function of wavelength of Pb(Zr$_{0.4}$Ti$_{0.6}$)O$_3$ film
Figure B.22  The extinction coefficient as a function of wavelength of Pb(Zr$_{0.5}$Ti$_{0.5}$)O$_3$ film
Figure B.23  The extinction coefficient as a function of wavelength of Pb(Zr\textsubscript{0.8}Ti\textsubscript{0.2})\textsubscript{O\textsubscript{3}} film
Figure B.24 The extinction coefficient as a function of wavelength of PbZrO$_3$ film
Figure B.25 The experimental and simulated transmission spectra of PbTiO$_3$ film
Figure B.26  The experimental and simulated transmission spectra of Pb(Zr$_{0.2}$Ti$_{0.8}$)O$_3$ film
Figure B.27 The experimental and simulated transmission spectra of Pb(Zr$_{0.4}$Ti$_{0.6}$)O$_3$ film
Figure B.28 The experimental and simulated transmission spectra of $\text{Pb(Zr}_{0.5}\text{Ti}_{0.5})\text{O}_3$ film
Figure B.29 The experimental and simulated transmission spectra of Pb(Zr_{0.8}Ti_{0.2})O_3 film
Figure B.30 The experimental and simulated transmission spectra of PbZrO$_3$ film
Appendix C

All the computer programs used in the optical properties study (Chapter 3) and structure development study (Chapter 4) are collected in this Appendix. These computer programs were written in BASIC:

ENV.BAS: Calculate optical constants using the Envelope Method.
THKENV.BAS: Calculate film thickness using the Envelope Method and the interference equation: $2nd = m\lambda$.
THKSIMU.BAS: Calculate film thickness by fitting the optical constants to the experimental transmission spectrum.
T&R.BAS: Calculate the transmittance and reflectance of a multi-layer thin film system.
DRFIT.BAS: Find the dispersion relation parameters by fitting the refractive index data to a Sellmeier type equation.
ALPHA.BAS: Calculate the absorption coefficient of a film on a transparent substrate at the strong absorption region.
VF.BAS: Calculate the volume fraction of a two phase mixture by Effective Medium Approximation.
REM ENV.BAS calculates \( (\lambda n k) \) and \( (E \alpha \alpha^2 \alpha^{.5}) \) from a transmission spectrum of a 'weakly absorbing thin film -- transparency substrate' system. This is so-called "ENVELOPE METHOD".

REM Input: \( (\lambda_{\text{max}} \lambda_{\text{min}}) \) -- Hand-made envelope curves
REM The unit of \( \lambda \) is nm. Wavelength should be tabulated from short to long. \( \lambda_{\text{max}} \) and \( \lambda_{\text{min}} \) are in fraction.
REM Peaks and/or Valleys position (for thickness calculation)
REM Substrate: Sapphire or Glass
REM
REM Output: \( (\lambda n k) \) and/or \( (E \alpha \alpha^2 \alpha^{.5}) \)
REM
REM The back surface of substrate has been taken into account.
REM
REM J Opti. Soc. Am. 52, 1377 (1967) for the refractive index of sapphire.
REM == C. H. PENG 1/16/91 (6/18/92 revised) ========

DI1=3000: DI2=100:DI3=30
DIM LAMBDA(DI1) ,TMAX(DI1) , TMIN(DI1) ,NS(DI1) ,N(DI1),K(DI1) ,ALPHA(DI1)
DIM LAMBDAS (DI2) , LAMBDAF (DI2) , TMAX1(DI2) , TMIN1(DI2) ,NS1(DI2)
DIM LM(DI3) ,NM(DI3) ,DM(DI3) , LM$(DI3)
A1=1.023798
A2=1.058264
A3=5.280792
L12=3.77588E-03
L22=.0122544
L32=321.3616
PI=3.1415926#
CLS

INPUT "Enter data filename of substrate ('S' for sapphire, 'G' for glass): ",FILEN1$
IF FILEN1$="s" OR FILEN1S="S" THEN GOTO 450
IF FILEN1S="G" OR FILEN1$="g" THEN FILEN1$="AQUARTZ.DAT"
OPEN "I",#1,FILEN1$
I=0
WHILE NOT EOF(1)
I=I+1
INPUT #1,LAMBDAS(I) ,NS1(I)
WEND
NPS=I
CLOSE #1

INPUT "Enter wavelength min, max, and increment: ",LMIN, LMAX, LINC

I=0
WHILE NOT EOF(1)
I=I+1
INPUT #1,LAMBDAF(I) ,TMAX1(I),TMIN1(I)
WEND

I=0
WHILE NOT EOF(1)
I=I+1
INPUT #1,LAMBDAF(I) ,TMAX1(I),TMIN1(I)
IF TMAX1(I)<TMIN1(I) THEN SWAP TMAX1(I), TMIN1(I)
IF TMAX1(I)>1 THEN TMAX1(I)=TMAX1(I)*.01
IF TMIN1(I)>1 THEN TMIN1(I)=TMIN1(I)*.01
WEND

I=0
WHILE NOT EOF(1)
I=I+1
INPUT"Enter wavelength min, max, and increment: ",LMIN, LMAX, LINC
IF LMIN<LAMBDAF(1) OR LMAX>LAMBDAF(NPF) THEN PRINT "Wavelength has to be within the range: ",LAMBDAF(1);" - ";LAMBDAF(NPF):GOTO 570
590 NP=INT((LMAX-LMIN)/LINC)+1
600 IF FILEN$="s" OR FILEN$="S" THEN GOSUB 1730:GOTO 710
610 JJ=1
620 FOR I=1 TO NP
630 LAMBDA(I)=LMIN+(I-1)*LINC
640 FOR J=JJ TO NPS
650 IF LAMBDA(I)=LAMBDAS(J) THEN NS(I)=NS1(J):JJ=J :GOTO 700
660 IF LAMBDA(I)<LAMBDAS(J) THEN JJ=J-1: GOTO 680
670 NEXT J
680 SLOPE=(NS1(J)-NS1(J-1))/(LAMBDAS(J)-LAMBDAS(J-1))
690 NS(I)=NS1(J-1)+(LAMBDAS(I)-LAMBDAS(J-1))*SLOPE
700 NEXT I
710 JJ=1
720 FOR I=1 TO NP
730 LAMBDA(I)=LMIN+(I-1)*LINC
740 FOR J=JJ TO NPF
750 IF LAMBDA(I)=LAMBDAF(J) THEN TMAX(I)=TMAX1(J):TMIN(I)=TMIN1(J):JJ=J
:GOTO 840
760 IF LAMBDA(I)<LAMBDAF(J) THEN JJ=J-1: GOTO 780
770 NEXT J
780 DE1=LAMBDAF(J)-LAMBDAS(J-1)
790 DE2=LAMBDA(I)-LAMBDAS(J-1)
800 SLOPE=(TMAX1(J)-TMAX1(J-1))/DE1
810 TMAX(I)=TMAX1(J-1)+DE2*SLOPE
820 TMIN(I)=TMIN1(J-1)+DE2*SLOPE
830 NEXT I
840 NEXT J
850 REM Calculation refractive index of film
860 FLAG=0
870 FOR I=1 TO NP
880 IF FLAG=1 THEN 900
890 IF LAMBDA(I)>632.8 THEN L6=I-1:FLAG=1
900 DE=8*(NS(I)/(NS(I)+1))^2*(TMAX(I)-TMIN(I))/(TMAX(I)*TMIN(I))
910 NN=.5*(1+NS(I)*NS(I))+DE
920 N(I)=SQR(NN+SQR(NN*NN-NS(I)*NS(I)))
930 NEXT I
940 N6=N(L6)-(N(L6)-N(L6+1))*(632.8-LAMBDAS(L6))/(LAMBDAS(L6+1)-LAMBDAS(L6))
950 PRINT"Refractive index of film at 632.8 nm is ";N6
960 PRINT
970 PRINT"----< Calculation of film thickness >----" 
980 PRINT"Enter wavelengths which correspond to extrema, 'P'=peaks, " 
981 PRINT"'V'=valleys"
990 PRINT"--- Enter '0,0' to end entry."
1000 PRINT"For example, 361.3,P"
1010 PRINT" 413.2,V"
1020 PRINT" 573.3,P"
1030 PRINT" 883.8,V"
1040 PRINT" 0,0"
1050 PRINT
1060 I=0
1070 I=I+1
1080 PRINT I;:INPUT"",LM(I),LM$(I)
1090 IF LM(I)=0 THEN NLM=I-1 ELSE GOTO 1070
1100 FOR J=1 TO NLM
1110 IF LM(J)=LAMBDAS(I) THEN NM(J)=N(I):GOTO 1170
1120 IF LM(J)=LAMBDAS(I) THEN NM(J)=N(I): GOTO 1150
1130 IF LM(J)<LAMBDAS(I) THEN GOTO 1150
1140 NEXT I
1150 SLOPE=(N(I)-N(I-1))/(LAMBDAS(I)-LAMBDAS(I-1))
1160 NM(J)=N(I-1)+(LM(J)-LAMBDAS(I-1))*SLOPE
PRINT J;" Lambda=":LM(J);" ;"n=";NM(J)

NEXT J

NK=0;NV=0

FOR I=1 TO NLM

IF LM$(I)="p" OR LM$(I)="P" THEN NK=NK+1 ELSE NV=NV+1

NEXT I

D=0

IF NK<2 THEN 1340

L=1

FOR I=1 TO NK-1

F0=0;F3=0

FOR J=L TO NLM

IF (LM$(J)="p" OR LM$(J)="P") AND F0=1 THEN F3=J

IF (LM$(J)="p" OR LM$(J)="P") AND F0=0 THEN F2=J;F0=1

IF F3>F2 THEN L=F3:DESS$="peaks":GOSUB 1790:GOTO 1330

NEXT J

NEXT I

IF NK<2 AND NV<2 THEN PRINT"No sufficient peaks or valleys":RETURN

IF NV<2 THEN 1450

L=1

FOR I=1 TO NV-1

F0=1;F3=0

FOR J=L TO NLM

IF (LM$(J)="v" OR LM$(J)="V") AND F0=2 THEN F3=J

IF (LM$(J)="v" OR LM$(J)="V") AND F0=1 THEN F2=J;F0=2

IF F3>F2 THEN L=F3:DESS$="valleys":GOSUB 1790:GOTO 1440

NEXT J

NEXT I

D=D/ (NK+NV-2)

PRINT "Average thickness: ";D;"nm"

INPUT"Enter thickness for extinction coefficient calculation: ",D

FOR I=1 TO NP

C1=(N(I)+1)*(NS(I)+N(I))

C2=(N(I)-1)*(NS(I)-N(I))

A=(C1*(1-SQR(TMAX(I)/TMIN(I))))/(C2*(1+SQR(TMAX(I)/TMIN(I))))

K(I)=(-LAMBDA(I)/(4*PI*D)) *LOG(A)

ALPHA(I)=1E+07*4*PI*K(I)/LAMBDA(I)

NEXT I

INPUT "Enter filename to save (lambda, n, and k): ",FILEN3$

OPEN "0",#1,FILEN3$

FOR I=1 TO NP

PRINT #1,LAMBDA(I),N(I),K(I)

NEXT I

CLOSE #1

PRINT "Enter filename to save (E, alpha, alpha^2, and sqr(alpha))"

INPUT "Hit <RETURN> to skip: ",FILEN5$

IF FILEN5$="" THEN 1690

OPEN "0",#1,FILEN5$

FOR I=1 TO NP

PRINT #1,1239.85/LAMBDA(I),ALPHA(I),ALPHA(I)*ALPHA(I),SQR(ALPHA(TI))

NEXT I

CLOSE #1

INPUT "Another calculation? (Y/N) ",Z$

IF Z$="Y" OR Z$="y" THEN GOTO 320

CLS

END

FOR I=1 TO NP

LAMBDA(I)=LMIN+(I-1)*LINC

LS=LAMBDA(I)*LAMBDA(I)/1000000!

1770 NEXT I
1780 RETURN
1790 REM
1800 DM(I)=ABS((LM(F2)*LM(F3))/(2*(NM(F2)*LM(F3)-NM(F3)*LM(F2))))
1810 D=D+DM(I)
1820 PRINT "t=";DM(I);" nm from ";DES$;" at ";LM(F2);" and ";LM(F3)
1830 RETURN
REM THKENV.BAS calculates the film thickness basing on the envelope method along with the interference equation: 2nd=m*lambda.
REM Both lambda and thickness (d) are in nm.
REM
REM The algorithm is
REM 1. input the wavelengths of the interference peaks and/or valleys and the corresponding Tmax and Tmin.
REM 2. the refractive indices at these wavelengths are calculated based on the envelope method
REM 3. the thicknesses are calculated from pairs of peaks and/or valleys
REM 4. the order numbers m are then calculated from corresponding wavelength, refractive index, and film thickness.
REM 5. the order numbers m are rounded to the nearest integer or half-integer, then new thicknesses are calculated from these new m.
REM 6. the average thickness from step 5 is taken as the final answer.
REM
CLS
DIM PL(20), PN(20), VL(20), VN(20), D1(20), D2(20)
DIM LM(20), NL1(20), N2(20), M0(20), M(20)
DIM TMXP(20), TMINP(20), TMAXv(20), TMINV(20)
A1=1.023798
A2=1.058264
A3=5.280792
L12=3.77588E-03
L22=.0122544
L32=321.3616

INPUT "Enter filename to save data: ", F$
OPEN "0",#1,FS
INPUT "Description: ", DS$
PRINT #1, DS$
INPUT "Enter Tmax and Tmin at 633 nm: ", TMAX, TMIN
IF TMAX<1 THEN GOTO 360
TMAX=TMAX/18.71: TMIN=TMIN/18.71
IF TMAX<TMIN THEN SWAP TMAX, TMIN
LS=632.8*632.8/1000000!
DE=8*(NS/NS+1)^2*(TMAX-TMIN)/(TMAX*TMIN)
NN=.5*(1+NS^2)+DE
N633=SQR(NN+SQR(NN^2-NS^2))
PRINT #1, " n(633)="; N633; " Tmax="; TMAX; " Tmin="; TMIN
PRINT "Enter lambda, Tmax, and Tmin for peaks:"
I=0: PL(0)=0
I=I+1
PRINT I;
INPUT " lambda="; PL(T)
IF PL(I) > 200 THEN GOTO 500
PL(I)=CINT(PL(I)*1800/23+200)
IF PL(I)=200 THEN NP=I-1: GOTO 650
LS=PL(I)*PL(I)/1000000!
DE=8*(NS/NS+1)^2*(TMAXP(I)-TMINP(I))/(TMAXP(I)*TMINP(I))
IF TMAXP(I)<TMINP(I) THEN SWAP TMAXP(I), TMINP(I)
PRINT " Tmax="; TMAXP(I); " Tmin="; TMINP(I)
PRINT " lambda="; PL(I)
IF PL(I) > 200 THEN GOTO 500
PL(I)=CINT(PL(I)*1800/23+200)
IF PL(I)=200 THEN NP=I-1: GOTO 650
LS=PL(I)*PL(I)/1000000!
INPUT " Tmax="; TMAXP(I)
NN=.5*(1+NS^2)+DE
PN(I)=SQR(NN+SQR(NN*2-NS^2))
IF PL(I)<PL(I-1) THEN NP=I-1:VL(I)=PL(I):VN(I)=PN(I):
TMAXP(I)=TMAXP(I):TMINV(I)=TMINP(I):I=1:GOTO 670
GOTO 450
PRINT"Enter lambda(nm), Tmax, and Tmin (cm) for valleys:")
I=0
FOR I=1 TO NP
PRINT #1,USING " H#H#H#") PL(I);
NEXT I
FOR I=1 TO NV
PRINT #1,USING " HFHH") FVL(I)?
NEXT I
FOR I=1 TO NP
PRINT #1,USING " ~####") TMAXP(I);
NEXT I
FOR I=1 TO NV
PRINT #1,USING " eH H") TMAXV(I)?
NEXT I
FOR I=1 TO NP
PRINT #1,USING " #.####")3PN(I);
NEXT I
FOR I=1 TO NV
PRINT #1,USING " #.####8")5VN(I);
NEXT I
FOR I=1 TO NP-1
D1(I)=PL(I+1)*PL(I)/(2*(PL(I+1)*PN(I)-PL(I)*PN(I+1))
NEXT I
L=NP-1
FOR I=1 TO NP-1
D1(I)=PL(I+1)*PL(I)/(2*(PL(I+1)*PN(I)-PL(I)*PN(I+1)))
PRINT #1,USING " ###.#") D1(I);
NEXT I
L=NP-1
FOR I=1 TO NV-1
204
1200   L=L+1
1210   D1(L)=VL(I+1) *VL(I) / (2 * (VL(I) +1) * VN(I) - VL(I) * VN(I+1))
1220   PRINT #1, USING " #.###"; D1(L); 
1230 NEXT I
1240 PRINT #1," "
1250   D1A=0
1260 FOR I=1 TO L
1270   D1A=D1A+D1(I)
1280 NEXT I
1290   D1A=D1A/L
1300 PRINT #1," Average thickness:"; D1A
1310 FOR I=1 TO NP
1320   LM(I)=PL(I) ; N1(I)=PN(I)
1330 NEXT I
1340 LL=NP
1350 FOR I=1 TO NV
1360   LM(LL)=VL(I) ; N1(LL)=VN(TI)
1370 NEXT I
1380 NN=NP+NV
1390 D2A=0
1400 FOR I=1 TO NN
1410   M0(I)=2*N1(I) * D1A / LM(I)
1420   IF I>NP THEN M(I)=CINT(M0(I)+ .5)-.5 ELSE M(I)=CINT(M0(I))
1430   D2(I)=LM(I) * M(I) / (2*N1(I))
1440   D2A=D2A+D2(I)
1450 NEXT I
1460 FOR I=1 TO NN
1470   PRINT #1, USING " #.###"; M0(I);
1480 NEXT I
1490 PRINT #1," "
1500 PRINT #1," "
1510 FOR I=1 TO NN
1520   PRINT #1, USING " #.###"; M(I);
1530 NEXT I
1540 PRINT #1," "
1550 FOR I=1 TO NN
1560   PRINT #1, USING " #.###"; D2(I);
1570 NEXT I
1580 PRINT #1," "
1590 D2A=D2A/NN
1600 PRINT #1," Average thickness="; D2A
1610 FOR I=1 TO NN
1620   N2(I)=LM(I) * M(I) / (2*D2A)
1630 PRINT #1, USING " #.###"; N2(I);
1640 NEXT I
1650 PRINT #1," "
1660 PRINT #1," "
1670 INPUT"Another Calculation? (y/n) ", Z$ 
1680 IF Z$="N" OR Z$="n" THEN 1700 
1690 GOTO 310 
1700 CLOSE #1
1710 INPUT"Another Calculation and change new filename? (y/n) ", Z$ 
1720 IF Z$="N" OR Z$="n" THEN 1740 
1730 GOTO 290 
1740 CLS 
1750 END
REM THKSIMU.BAS calculates the film thicknesses by fitting the calculated transmission spectrum to the experimental transmission spectrum.

Input: optical constants for substrate and each film

initial thickness guess for each film

thickness increment for each film

Output: thickness for each film

fitting error (chi square)

The calculation of the transmission spectrum is based on the program T&R.BAS with the consideration of the back surface of the substrate.

The fitting process stops when the minimum fitting error is met.

The fitting error is defined as:

Error = (summation of [T(cal)^2 - T(exp)^2])/(# of data points)

C. H. PENG 5/16/92

CLS

DIM X(D1),Y(D1),K(D2,D1),D(D2), X1(D3), Y1(2,D3)

DIM G(D2),H(D2),GAMMA(D2),DI(D2)

DIM P(D2),Q(D2),R(D2),S(D2),T(D2),V(D2),W(D2)

DIM P1(D2),Q1(D2),R1(D2),S1(D2),T1(D2),U1(D2),V1(D2),W1(D2)

DIM G(D2),H(D2),GAMMA(D2),DI(D2)

INPUT "Spectral range (wavelength in nm, min, max): ", XMIN, XMAX

INPUT "Resolution (in nm): ", RSL

IF NP > 1000 THEN PRINT "Resolution too high!": BEEP: PRINT: GOTO 280

FOR I=1 TO NP
    X(I) = XMIN + RSL * (I-1)
    N(0,I) = 1 : K(0,1) = 0
NEXT I

INPUT "How many layers (do not count the substrate)? ", NL

IF NL > 5 THEN PRINT "Too many layers (max: 5)": GOTO 350

PRINT "Input optical properties for each layer and substrate ...

FOR I=1 TO NL
    PRINT "Layer # ", I
    INPUT "Thickness and increment (in nm): ", D(I), DI(I)
    INPUT "Filename for (n,k) -- ", RI$
    GOSUB 1080
NEXT I

PRINT "Substrate:

Refractive Index (n) (Enter 'S' for sapphire, 'G' for glass, a file name for other materials, or digits for constants): ", RIS

IF RIS = "S" OR RIS = "s" THEN GOSUB 1800: GOTO 510

IF RIS = "g" OR RIS = "G" THEN GOSUB 1940: GOTO 510

IF ASC(RIS) > 45 AND ASC(RIS) < 58 THEN RI = VAL(RIS)

INPUT "Enter experiment data filename for T -- ", FILENS

OPEN "I", #1, FILENS

J=0

WHILE NOT EOF(1)
    J = J + 1
    INPUT #1, X1(J), Y1(1,J)
WEND
K(I,J)=Y1(2,J1-1)+(Y1(2,J1)-Y1(2,J1-1))*SLOPE
GOTO 1200
NEXT J
NEXT I
RETURN

REM Multi-layer transmittance and reflectance calculation
REM See O. S. Heavens, "Optical Properties of Thin Solid Films"
REM (Academic, New York, 1955), pp.76-79

CHISQ1=0
FOR I=1 TO NP
FOR I=1 TO NL+1
H(I)=(2*(N(I-1,L)*K(I,L)-N(I,L)*K(I-1,L)))/NN
NEXT I
FOR I=1 TO NL
ALPHA(I)=6.28318534*K(I,L)*D(I)/X(L)
GAMMA(I)=6.28318534*N(I,L)*D(I)/X(L)
NEXT I
FOR I=2 TO NL+1
P(I)=EA*CG
Q(I)=EA*SG
T(I)=EMA*(G(I)*CG+H(I)*SG)
U(I)=EMA*(H(I)*CG-G(I)*SG)
IF I=NL+1 THEN 1550
R(I)=EA*(G(I)*CG-H(I)*SG)
S(I)=EA*(H(I)*CG+G(I)*SG)
V(I)=EMA*CG
W(I)=-EMA*SG
NEXT I
FOR I=1 TO NL
P(I+1)=P(I)*P(I+1)-Q(I)*Q(I+1)+R(I)*T(I+1)-S(I)*U(I+1)
Q(I+1)=Q(I)*P(I+1)+P(I)*Q(I+1)+S(I)*T(I+1)-R(I)*U(I+1)
T(I+1)=T(I)*P(I+1)-U(I)*Q(I+1)+V(I)*T(I+1)-W(I)*U(I+1)
U(I+1)=U(I)*P(I+1)+T(I)*Q(I+1)-V(I)*T(I+1)+W(I)*U(I+1)
IF I=NL THEN 1660
R(I+1)=P(I )*R(I+1) -Q(I)*S(I+1)+R(I)*V(I+1) -S(I)*W(I+1)
S(I+1)=Q(I)*R(I+1)+P(I)*S(I+1)+S(I)*V(I+1)+R(I)*W(I+1)
V(I+1)=T(I)*R(I+1)-U(I)*S(I+1)+V(I)*V(I+1)-W(I)*W(I+1)
W(I+1)=U(I)*R(I+1)+T(I)*S(I+1)+W(I)*V(I+1)+V(I)*W(I+1)
NEXT I
YRP=(T1(NL+1)*2+U1(NL+1)*2)/(P1(NL+1)*2+Q1(NL+1)*2)
NUMER=1
FOR I=1 TO NL+1
NUMER=NUMER*( (1+G(I))*2+H(I)*2)
NEXT I
DENOM=P1(NL+1)*2+Q1(NL+1)*2
YTP=(N(NL+1,L)*NUMER)/(N(0,L)*DENOM)
C1=((-N(NL+1,L)-N(NL+1,L)))/((N(NL+1,L)+N(NL+1,L)))*2
C2=((1-N(NL+1,L))/(1+N(NL+1,L)))*2
YT=YTP*(1-C2)/(1-C1*C2)
CHISQ1=CHISQ1+(YT-Y(L))*2
REM Calculate n of sapphire or read n of fused quartz.
A1=1.023798
A2=1.058264
A3=5.280792
L12=3.77588E-03
L22=.0122544
L32=321.3616
FOR J=1 TO NP
  LS=X(J)*X(J)*.000001
NEXT J
GOTO 2120
REM read n of fused quartz
OPEN "I",#1,"AQUARTZ.DAT"
J=0
WHILE NOT EOF(1)
  J=J+1
  INPUT #1,X1(J),¥1(1,T)
WEND
CLOSE #1
NPS=J
JJ=1
FOR I=1 TO NP
  FOR J=JJ TO NPS
    IF X(I)=X1(J) THEN N(NL+1,1)=¥1(1,J):JJ=J:GOTO 2110
    IF X(I)<X1(J) THEN JJ=J-1:GOTO 2090
  NEXT J
SLOPE=(¥1(1,J)-¥1(1,J-1))/(X1(J)-X1(J-1))
N(NL+1,I)=¥1(1,J-1)+(X(I)-X1(J-1))*SLOPE
NEXT I
REM Set k of substrate equal to 0.
FOR K=1 TO NP
  K(NL+1,K)=0
NEXT K
RETURN
REM T&R.BAS calculates the transmittance and reflectance of a multi-
layer thin films system.

REM Input: optical constants for substrate and each film

REM The refractive index (n) and extinction coefficient (k) can be non-
dispersive or dispersive. The dispersive n and k have to be pre-
saved in a data file which has the following format:
1st line: lambda(1) n(1) k(1)
2nd line: lambda(2) n(2) k(2)
. . .
where lambda(i) is in nm and is tabulated from short to long.

REM The result will be saved in a data file with the following format:
1st line: lambda(1) T(1) or R(1)
2nd line: lambda(2) T(2) or R(2)
. . .

REM The back surface of substrate has been taken into account during
REM calculation as follows:
T = T' (1-r(m+2))/(1-r(m+1) r(m+2))
R = R' + (T/-T) (R'+T')
where T = transmittance with the back surface of substrate
R = reflectance with the back surface of substrate
T' = transmittance without the back surface of substrate
R' = reflectance without the back surface of substrate
r(m+1) = reflectivity of the interface of film and substrate
r(m+2) = reflectivity of the interface of substrate and air

REM Maximum # of layers: 5
REM Maximum # of data points: 1000

CLS
D1=1000 :D2=5 :D3=1000
DIM X(D1),YT(D1),YR(D1) ,N(D2,D1) ,K(D2,D1) ,D(D2), X1(D3),¥1(2,D3)
DIM G(D2) ,H(D2) ,GAMMA(D2) ,ALPHA(D2)
DIM P(D2) ,Q(D2) ,R(D2),S(D2) ,T(D2),U(D2),V(D2),W(D2)
DIM P1(D2) ,Q1(D2) ,R1(D2) ,S1(D2) ,T1(D2) ,U1(D2) ,V1(D2) ,W1(D2)
INPUT "Spectral range (wavelength in nm, min, max): ",XMIN, XMAX
INPUT "Resolution (in nm): ",RSL
NP=INT ( (XMAX-XMIN) /RSL) +1
IF NP > 1000 THEN PRINT "Resolution too high!":BEEP:PRINT: GOTO 410
FOR I=1 TO NP
   X(I) =XMIN+RSL* (I-1)
   N(0,I)=1 :K(0,I)=0
NEXT I
PRINT
INPUT "How many layers (do not count the substrate)? ",NL
IF NL>5 THEN PRINT "Too many layers (max: 5)":GOTO 480
PRINT "Input the thickness and optical properties for each layer";
PRINT "or substrate."
PRINT "For refractive index (n) and extinction coefficient (k), entering":
"digits means constant value independent on wavelength or an ";
"existed filename means (n,k) value dependent on wavelength or an ";
FOR I=1 TO NL
   PRINT :PRINT "Layer ":I
   INPUT "Thickness (in nm): ",D(I)
   INPUT "Refractive Index (n): ",RI$
   IF ASC(RI$)>45 AND ASC(RI$)<58 THEN RI$=VAL(RI$)
ELSE GOSUB 1300: GOTO 660

FOR J = 1 TO NP
    N(I,J) = RI
NEXT J

INPUT "Extinction coefficient (k): ", EC
FOR J = 1 TO NP
    K(I,J) = EC
NEXT J
NEXT I

PRINT: PRINT "Substrate:"
PRINT "Refractive Index (n) (Enter 'S' for sapphire, 'G' for glass, a""
" file name for other materials, or digits for constants):";

INPUT " ", RIS
IF RIS = "S" OR RIS = "G" THEN GOSUB 2010: GOTO 800
IF ASC(RI$) > 45 AND ASC(RI$) < 58 THEN RI = VAL(RIS)
ELSE GOSUB 1300: GOTO 800

FOR J = 1 TO NP
    N(NL + 1, J) = RI
NEXT J

INPUT "Extinction coefficient (k): ", EC
FOR J = 1 TO NP
    K(NL + 1, J) = EC
NEXT J
GOSUB 1190
GOSUB 1440
GOSUB 870
PRINT
INPUT "Another calculation? (Y/N) ", Y$
IF Y$ = "Y" OR Y$ = "y" THEN CLS: GOTO 400
END

REM Save data (X,Y)
REM The data are saved in (x,y) array.
REM
INPUT "Save T? (¥/N) ", YY$
IF YY$ = "N" OR YY$ = "n" THEN 990
INPUT "Enter data file name to save T: ", FILENS$
OPEN "O", #1, FILENS$
FOR I = 1 TO NP
    PRINT #1, X(I), YT(I)
NEXT I
CLOSE #1

INPUT "Save R? (Y/N) ", YY$
IF YY$ = "N" OR YY$ = "n" THEN 1070
INPUT "Enter data file name to save R: ", FILENS$
OPEN "O", #1, FILENS$
FOR I = 1 TO NP
    PRINT #1, X(I), YR(I)
NEXT I
CLOSE #1
RETURN

REM Get data (X,Y1,Y2)
REM
OPEN "I", #1, FILENS$
J = 0
WHILE NOT EOF(1)
    J = J + 1
    INPUT #1, X1(J), Y1(1,J), Y1(2, J)
WEND
CLOSE #1
RETURN
REM  Display a wait message
REM  CLS
FOR I=1 TO 8
PRINT
NEXT I
PRINT CHR$(7)
PRINT 
REM  Please wait for calculation ...... (";NP:"pts ")
RETURN
REM  Read n & k and convert them to (x,y) arrays.
REM File=$ : GOSUB 1080
JJ=J
FOR J=1 TO NP
IF X(J)=X1(J1) THEN N(I,J)=Y1(1,J1):K(I,J)=Y1(2,J1) : GOTO 1420
IF X(J)<X1(J1) THEN SLOPE=(X(J)-X1(J1-1))/(X1(J1)-X1(J1-1))
ELSE GOTO 1410
N(I,J)=Y1(1,J1-1)+(Y1(1,J1)-Y1(1,J1-1))*SLOPE
K(I,J)=Y1(2,J1-1)+(Y1(2,J1)-Y1(2,J1-1))*SLOPE
GOTO 1420
NEXT J1
NEXT J
RETURN
REM  Multi-layer transmittance and reflectance calculation
REM See O. S. Heavens, "Optical Properties of Thin Solid Films"
REM  FOR L=1 TO NP
FOR I=1 TO NL+1
NN=(N(I-1,L)+N(I,L))^2+(K(I-1,L)+K(I,L))^2
G(I)=(N(I-1,L)^2+K(I-1,L)^2-N(I,L)^2-K(I,L)^2)/NN
H(I)=(2*(N(I-1,L)*K(I,L)-N(I,L)*K(I-1,L)))/NN
NEXT I
P1(1)=1!:Q1(1)=0!:R1(1)=G(1):S1(1)=H(1)
T1(1)=G(1):U1(1)=H(1):V1(1)=1!:W1(1)=0!
FOR I=1 TO NL
ALPHA(I)=6.2831853*K(I,L)*D(I)/X(L)
GAMMA(I)=6.2831853*N(I,L)*D(I)/X(L)
NEXT I
FOR I=2 TO NL+1
EA=EXP(ALPHA(I-1))
CG=COS(GAMMA(I-1))
SG=SIN(GAMMA(I-1))
EMA=EXP(-ALPHA(I-1))
P(I)=EA*CG
Q(I)=EA*SG
T(I)=EMA*(G(I)*CG+H(I)*SG)
U(I)=EMA*(H(I)*CG-G(I)*SG)
IF I=NL+1 THEN 1760
R(I)=EA*(G(I)*CG-H(I)*SG)
S(I)=EA*(H(I)*CG+G(I)*SG)
V(I)=EMA*CG
W(I)=EMA*SG
NEXT I
FOR I=2 TO NL+1
EA=EXP(ALPHA(I-1))
CG=COS(GAMMA(I-1))
SG=SIN(GAMMA(I-1))
EMA=EXP(-ALPHA(I-1))
P(I)=EA*CG
Q(I)=EA*SG
T(I)=EMA*(G(I)*CG+H(I)*SG)
U(I)=EMA*(H(I)*CG-G(I)*SG)
IF I=NL+1 THEN 1760
R(I)=EA*(G(I)*CG-H(I)*SG)
S(I)=EA*(H(I)*CG+G(I)*SG)
V(I)=EMA*CG
W(I)=EMA*SG
NEXT I
FOR I=1 TO NL+1
FOR I=1 TO NL
P1(I+1)=P1(I)*P(I+1)-Q1(I)*Q(I+1)+R1(I)*T(I+1)-S1(I)*U(I+1)
Q1(I+1)=Q1(I)*P(I+1)+P1(I)*Q(I+1)+S1(I)*T(I+1)+R1(I)*U(I+1)
T1(I+1)=T1(I)*P(I+1)-U1(I)*Q(I+1)-V1(I)*T(I+1)-W1(I)*U(I+1)
U1(I+1)=U1(I)*P(I+1)+T1(I)*Q(I+1)+V1(I)*T(I+1)+W1(I)*U(I+1)
IF I=NL THEN 1870
R1(I+1)=P1(I)*R(I+1)-Q1(I)*S(I+1)+R1(I)*V(I+1)-S1(I)*W(I+1)
S1(I+1)=Q1(I)*R(I+1)+P1(I)*S(I+1)+S1(I)*V(I+1)+R1(I)*W(I+1)
V1(I+1)=T1(I)*R(I+1)-U1(I)*S(I+1)+V1(I)*V(I+1)-W1(I)*W(I+1)
W1(I+1)=T1(I)*R(I+1)+U1(I)*S(I+1)+W1(I)*V(I+1)+V1(I)*W(I+1)
NEXT I
YRP=(T1(NL+1)*2+U1(NL+1)*2)/(P1(NL+1)*2+Q1(NL+1)*2)
NUMER=1
FOR I=1 TO NL+1
NUMER=NUMER**((1+G(I))*2+H(I)*2)
NEXT I
DENOM=P1(NL+1)*2+Q1(NL+1)**2
YP=(N(NL+1,L)*NUMER)/(N(0,L)*DENOM)
YR(L)=YRP+(YP-YR(L))*(YRP+YP)
LOCATE 15,35 :PRINT L
NEXT L
RETURN

A1=1.02798
A2=1.058264
A3=5.280792
L12=3.77588E-03
L22=.0122544
L32=321.3616
FOR J=1 TO NP
LS=X(J)*X(J)*.000001
NEXT J
GOTO 2330
REM read n of fused quartz
OPEN "I",#1,"AQUARTZ.DAT"
J=0
WHILE NOT EOF (1)
J=I+1
INPUT #1,X1(J),Y1(J)
WEND
CLOSE #1
NPS=J
FOR I=1 TO NP
FOR J=1 TO NPS
IF X(I)=X1(J) THEN N(NL+1,I)=Y1(1,J):JJ=J:GOTO 2320
IF X(I)<X1(J) THEN JJ=J-1:GOTO 2300
NEXT J
SLOPE=(Y1(J)-Y1(J-1))/(X1(J)-X1(J-1))
Y(NL+1,I)=Y1(1,J-1)+(X(I)-X1(J-1))*SLOPE
NEXT I
FOR K=1 TO NP :K(NL+1,K)=0 :NEXT K:REM Set ks=0
RETURN
REM DRFIT.BAS finds the dispersion relation parameters by fitting the
REM refractive index data to a Sellmeier type equation:
REM \[ n^2 = 1 + \frac{A \lambda^2}{\lambda^2 - B} \]
REM where A and B are the parameters to be determined and \( \lambda \) is in um.
REM
REM input: refractive index data file (\( \lambda \) in nm)
REM lower and upper bounds for A and B
REM output: fitting error and parameter A and B
REM
REM =======s=== = C. H. PENG 7/15/92 =======
DIM X(100), N(100)
CLS
INPUT "Enter data filename: ", FS$
INPUT "Enter adjusted value for n: ", ADJ
OPEN "I", #1, F$
REM Skip the first few "bad" data point
INPUT "Enter number of data to be skipped: ", SK
I=0: L=0
WHILE NOT EOF(1)
I=I+1
INPUT #1, X1, X2, X3
IF I<(SK+1) THEN 250
L=L+1: N(L)=X2+ADJ: X(L)=X1
WEND
NP=L
CLOSE #1
INPUT "Enter lower and upper limit for A (0,0 to quit): ", AL, AU
IF AL=0 AND AU=0 THEN 510
AI=(AU-AL)/9
INPUT "Enter lower and upper limit for B: ", BL, BU
BI=(BU-BL)/9
CHISQO=1
FOR K=1 TO 10
A=AL+AI*(K-1)
FOR J=1 TO 10
B=BL+BI*(J-1)
CHISQ1=0
FOR I=1 TO NP
C=(X(I)/1000)^2
Y=N(I)
F=SQR(1+A*C/(C-B))
CHISQ1=CHISQ1+(Y-F)^2
NEXT I
CHISQ1=CHISQ1/NP
IF CHISQ1<CHISQ THEN CHISQ=CHISQ1: AA=A: BB=B
NEXT J
NEXT K
PRINT CHISQ, AA, BB
GOTO 280
INPUT "Another calculation? (Y/N) ", Z$
IF Z$="Y" OR Z$="y" THEN 130
CLS
END
REM SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS SSS
FOR I=1 TO NP
  T(I)=T(I)*.01
NEXT I
PRINT
PRINT "Select Substrate:" :PRINT
PRINT " 1 ... Sapphire"
PRINT " 2 ... Fused Quartz": PRINT
INPUT "Enter your selection: ", S
IF S=1 THEN GOTO 800
IF S=2 THEN FILEN1$="AQUARTZ.DAT"
IF S>2 OR S<1 THEN GOTO 230
OPEN "I", #1,FILEN1$
INPUT #1, DESC$
I=0
WHILE NOT EOF(1)
  I=I+1
  INPUT #1, LAMBDAS(I), NS1(T)
WEND
NPS=I
CLOSE #1
IF S=1 THEN GOSUB 1080
IF S=2 THEN GOSUB 980
PRINT
INPUT "Enter file name to save (E(eV),A(cm-1),A^2,SQR(A)): ", FA$
OPEN "O", #1, FA$
FOR I=1 TO NP
  NF=(1+SQR(R(I)))/(1-SQR(R(I)))
  R2=(NF-NS(I))^2/(NF+NS(I))^2
  R3=(1-NS(I))^2/(1+NS(I))^2
  ALPHA=(1E+07/D) *LOG((1-R(I))*(1-R2)*(1-R3)/T(T))
  IF ALPHA<O THEN 930
  PRINT #1, 1239.85/LAMBDA(I), ALPHA, ALPHA^2, SQR(ALPHA)
NEXT I
CLOSE #1
PRINT: INPUT "Another calculation? (Y/N) ", Z$
IF Z$="Y" OR Z$="y" THEN GOTO 230
CLS
END

FOR I=1 TO NP
  FOR J=JJ TO NPS
    IF LAMBDAS(I)=LAMBDAS(J) THEN NS(I)=NS1(J): JJ=J: GOTO 1060
    IF LAMBDAS(I)<LAMBDAS(J) THEN JJ=J-1: GOTO 1040
  NEXT J
SLOPE=(NS1(J)-NS1(J-1))/(LAMBDAS(J)-LAMBDAS(J-1))
NS(I)=NS1(J-1)+(LAMBDAS(I)-LAMBDAS(J-1))*SLOPE
NEXT I
RETURN

FOR I=1 TO NP
  LS=LAMBDAS(I)*LAMBDAS(I)/1000000!
NEXT I
RETURN
REM
OPEN "I", #1, FT$
1200 IF X1<=LMIN THEN 1220
1210 WEND
1220 CLOSE #1
1230 NP=I+1
1240 FOR I=NP TO 1 STEP -1
1250 LAMBDA(NP-I+1)=TEMP1(I)
1260 T(NP-I+1)=TEMP2(I)
1270 NEXT I
1280 RETURN
1290 REM
1300 OPEN "I",#1,FR$
1310 I=0
1320 WHILE NOT EOF(1)
1330 I=I+1
1340 INPUT #1,X1,Y\$1
1350 IF X1<=LMAX AND X1=LAMBDA(1) THEN TEMP1(I)=X1;TEMP2(I)=Y\$1
1360 IF X1<=LAMBDA(1) THEN 1380
1370 WEND
1380 CLOSE #1
1390 FOR I=NP TO 1 STEP -1
1400 LAMBDA(NP-I+1)=TEMP1(I)
1410 T(NP-I+1)=TEMP2(I)
1420 NEXT I
1430 RETURN
REM VF.BAS calculates (1) the pyrochlore volume fraction of amorphous-
REM pyrochlore mixture PZT film and (2) the perovskite volume fraction
REM of pyrochlore-perovskite mixture PZT film by using effective medium
REM approximation.

REM n(PT,bulk)=2.668 n(PZ,bulk)=2.42
REM Ref: Philip D. Thacher, Applied Optics, 16(12), 3210-3213 (1977)

REM Step 1: Calculation packing density
REM Step 2: Calculation bulk n of pyrochlore
REM Step 3: Calculation bulk n of amorphous
REM Step 4: Calculation volume fraction of pyrochlore of amorphous-
REM Step 5: Calculation volume fraction of perovskite of pyrochlore-

CLS

DIM TP(2,20),NP(20),V(2,20)

PRINT
PRINT "Step 1: Calculation packing density"
INPUT " Enter Zr content=",X
INPUT " Dopant? (Description) ",XS
IF X>1 THEN X=X*.01
NPE =2.668-.248%*X

PRINT "Enter measured n of perovskite phase:",NPEM
A= (NPE*2-NPEM*2) / (NPE*2+2*NPEM*2)
B= (PD=1-NPEM*2) /(1+2*NPEM*2)

PRINT " Packing density=";PD

PRINT "Step 2: Calculation bulk n of pyrochlore"
INPUT " Enter measured n of pyrochlore phase:",NPYM
A=(1-PD) * (NPYM*2-1) / (PD* (1+2*NPYM^2) )
NPY=SQR((2*A+1)/(1-A) ) *NPYM

PRINT " bulk n of pyrochlore: ";NPY

PRINT "Step 3: Calculation bulk n of amorphous (Hit <RETURN> to"
" skip this step)"

INPUT " Enter measured n of amorphous phase:",NAM
A=(1-PD) * (NAM*2-1) /(1+2*NAM*2)
NA=SQR((2*A+1)/(1-A) )*NAM

PRINT " bulk n of amorphous: ";NA

PRINT "Step 4: Calculation volume fraction of pyrochlore of amorphous-
REM pyrochlore mixture (Hit <RETURN> to skip this step)"
INPUT " Enter measured n of pyrochlore (in Celsius) ":,TIPY
IF TIPY=0 THEN 620
INPUT " Enter completion temperature of pyrochlore (in Celsius) ":,TCPY
INPUT " Enter T(C) and measured n between":,TIPY;"and";TCPY;"C"

PRINT " Enter (0,0) to end entry"
I=0

IF I=I+1 THEN 490
PRINT " ;I;
INPUT ",TP(1,I),NP(I)
IF TP(1,I)=0 THEN 530
GOTO 480

PRINT "T(C)" TAB(10) "1/T(K)" TAB(22) "vol frc of py (alpha)" TAB(46)
"normalized alpha" TAB(65) "In(alpha)"

FOR I=1 TO NY

N2=NP(I)^2;NA2=NA^2;NPY2=NPY^2
A=(1-PD)* (N2-1) /(1+2*N2)+PD* (N2-NA2) /(NA2+2*N2)
B=(NPY2-N2) /(NPY2+2*N2)-(NA2-N2) /(NA2+2*N2)
V(1,I)=A/B
PRINT TP(1,I) TAB(7) 1/(TP(1,I)+273) TAB(25) V(1,I) TAB(47)
V(1,I)/PD TAB(65) LOG(V(1,I)/PD)

NEXT I

PRINT"Step 5: calculation volume fraction of perovskite of pyrochlore-"
PRINT" perovskite mixture (Hit <RETURN> to skip this step)"
PRINT" Enter initiation temperature of perovskite (in Celsius):";TIPE
IF TIPE=0 THEN 840
PRINT" Enter completion temperature of perovskite (in Celsius):";TCPE
PRINT" Enter T(C) and measured n between";TIPE;"and";TCPE;"C"
PRINT" Enter (0,0) to end entry"
I=0
I=I+1
PRINT" ;I;
PRINT" TP(2,I),NP(I)
IF TP(2,I)=0 THEN 750
GOTO 700
NE=I-1
PRINT"T(C)" TAB(10) "1/T(K)" TAB(22) "vol fra of pero (alpha)" TAB(46)
"normalized alpha" TAB(65) "ln(alpha)"
FOR I=1 TO NE
N2=NP(I)^2:NPE2=NPE^2:NPY2=NPY^2
A=(1-PD) * (N2-1)/(1+2*N2) +PD*(N2-NPY2)/(NPY2+2*N2)
B=(NPE2-N2)/(NPE2+2*N2) -(NPY2-N2)/(NPY2+2*N2)
V(2,I)=A/B
PRINT TP(2,I) TAB(7) 1/(TP(2,I)+273) TAB(25) V(2,I) TAB(47)
V(2,I)/PD TAB(65) LOG(V(2,I)/PD)
NEXT I

PRINT"Save all results into a file? (Y/N) ",ZS$
IF ZS="n" OR Z$="N" THEN 1090
PRINT"Enter file name to save results: ",F$ OPEN "O",#1,F$
PRINT #1,"Zr content = ";X$;Dopant = ";X$;
PRINT #1," Measured n of perovskite = ";NPEM
PRINT #1," Measured n of pyrochlore = ";NPYM
PRINT #1," Measured n of amorphous = ";NAM
PRINT #1," Packing density = ";PD
PRINT #1," Calculated bulk n of pyrochlore = ";NPY
PRINT #1," Calculated bulk n of amorphous = ";NA
PRINT #1," Initiation temperature of pyrochlore = ";TIPY
PRINT #1," Completion temperature of pyrochlore = ";TCPY
PRINT #1," Initiation temperature of perovskite = ";TIPE
PRINT #1," Completion temperature of perovskite = ";TCPY
PRINT #1,"T(C)" TAB(10) "1/T(K)" TAB(22) "vol fra of py (alpha)"
"normalized alpha" TAB(65) "ln(alpha)"
FOR I=1 TO NY
PRINT #1,TP(1,I) TAB(7) 1/(TP(1,I)+273) TAB(25) V(1,I) TAB(47)
V(1,I)/PD TAB(65) LOG(V(1,I)/PD)
NEXT I
FOR I=1 TO NE
PRINT #1,"T(C)" TAB(10) "1/T(K)" TAB(22) "vol fra of pero (alpha)"
"normalized alpha" TAB(65) "ln(alpha)"
CLOSE #1
PRINT "Another calculation? (Y/N) ",ZS$
IF ZS="y" OR Z$="Y" THEN 190
CLS:END

219
Bibliography


38. C. H. Peng and S. B. Desu, "Low–Temperature Metalorganic Chemical Vapor


78. Powder Diffraction File, Card No. 6–0547, Joint Committee on Powder Diffraction Standards (JCPDS), Swarthmore, PA.
VITA

Chien-Hsiung Peng was born on June 19, 1958 in Tainan, Taiwan. He received his undergraduate training at National Tsing Hua University, Hsinchu, Taiwan, where he earned a Bachelor of Science degree in Physics in 1980. He then completed his Master of Science degree in Materials Science and Engineering at National Tsing Hua University in 1982. He enrolled in the Materials Engineering Science Program at Virginia Tech to pursue his PhD in 1985. From Fall 1985 to Summer 1989, he worked with Profs. R. Zallen and D. Hoffman in the Physics Department. Later he worked with Prof. S. B. Desu in Materials Science Engineering Department. After receiving his PhD from Virginia Tech in August 1992, he will work for Ceram Incorporated in the field of electronic and optical thin films.

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